

# STIC Search Report

## STIC Database Tracking Number: 103832

TO: Sin J Lee

Location: CP3 9B05

Art Unit: 1752

September 23, 2003

Case Serial Number: 10/080507

From: Barba Koroma Location: EIC 1700

CP3/4-3D62

Phone: 305-3542

barba.koroma@uspto.gov

### Search Notes

Please find attached results of the search you requested. The list of hits have been printed out to help you look through rapidly, followed by a detailed printout of records. Let me know if you have any questions. Thanks.



## SEARCH REQUEST FORM

## Scientific and Technical Information Center

Art Unit: 1759 Phone Number 3 Mail Box and Bldg/Room Location: 98	05-0504 65 Results Fo	Serial Number: rmat Preferred (	60 Date: 9 10/080, circle) PAPER D	50'!	. ·
If more than one search is submitted, pl  ***********************************	ease prioritize sea ***************  pic, and describe as spec synonyms, acronyms, a have a special meaning.	arches in order  *********  ifically as possible  nd registry number  Give examples or	of need.  ***********  the subject matter to s, and combine with t relevant citations, au	t**********  be searched.  he concept or  thors, etc, if	<b>:</b>
Jung, Min Ho; Lea	22-02	Barky			-Same
*For Sequence Searches Only* Please include all perappropriate serial number.  — Please search for the make from the Shown in Cl.	ne copolym monomer	er (a) & V	nonomer	(b)	Constitution (Constitution Constitution Cons
Searcher:         NA           Searcher Phone #:         AA           Searcher Location:         Str           Date Searcher Picked Up:         Bil           Date Completed:         Lit           Searcher Prep & Review Time:         Fu           Clerical Prep Time:         Pa	pe of Search Sequence (#) Sequence (#) Uncture (#) Sequence (#) Sequen	Vendors  STN  Dialog  Questel/Orbit  Dr.Link  Lexis/Nexis  Sequence Systems  WWW/Internet		icable	

Page 1Lee507

1

=> file reg FILE 'REGISTRY' ENTERED AT 13:07:27 ON 23 SEP 2003 USE IS SUBJECT TO THE TERMS OF YOUR STN CUSTOMER AGREEMENT. PLEASE SEE "HELP USAGETERMS" FOR DETAILS. COPYRIGHT (C) 2003 American Chemical Society (ACS)

Property values tagged with IC are from the ZIC/VINITI data file

STRUCTURE FILE UPDATES: DICTIONARY FILE UPDATES: 22 SEP 2003 HIGHEST RN 591204-55-6 22 SEP 2003 HIGHEST RN 591204-55-6

TSCA INFORMATION NOW CURRENT THROUGH JULY 14, 2003

Please note that search-term pricing does apply when conducting SmartSELECT searches.

Crossover limits have been increased. See HELP CROSSOVER for details.

Experimental and calculated property data are now available. See HELP PROPERTIES for more information. See STNote 27, Searching Properties in the CAS Registry File, for complete details: http://www.cas.org/ONLINE/STN/STNOTES/stnotes27.pdf

=> file caplus FILE 'CAPLUS' ENTERED AT 13:07:33 ON 23 SEP 2003 USE IS SUBJECT TO THE TERMS OF YOUR STN CUSTOMER AGREEMENT. PLEASE SEE "HELP USAGETERMS" FOR DETAILS. COPYRIGHT (C) 2003 AMERICAN CHEMICAL SOCIETY (ACS)

Copyright of the articles to which records in this database refer is held by the publishers listed in the PUBLISHER (PB) field (available for records published or updated in Chemical Abstracts after December 26, 1996), unless otherwise indicated in the original publications. The CA Lexicon is the copyrighted intellectual property of the American Chemical Society and is provided to assist you in searching databases on STN. Any dissemination, distribution, copying, or storing of this information, without the prior written consent of CAS, is

FILE COVERS 1907 - 23 Sep 2003 VOL 139 ISS 13 FILE LAST UPDATED: 22 Sep 2003 (20030922/ED)

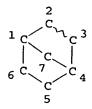
This file contains CAS Registry Numbers for easy and accurate

=> d que

Ll

STR

#### Page 2Lee507

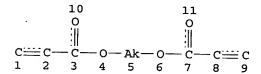


NODE ATTRIBUTES:
DEFAULT MLEVEL IS ATOM
DEFAULT ECLEVEL IS LIMITED

GRAPH ATTRIBUTES:

RING(S) ARE ISOLATED OR EMBEDDED NUMBER OF NODES IS 7

STEREO ATTRIBUTES: NONE L8 STR



NODE ATTRIBUTES:

DEFAULT MLEVEL IS ATOM

DEFAULT ECLEVEL IS LIMITED

ECOUNT IS M1-X10 C AT 5

GRAPH ATTRIBUTES:

RING(S) ARE ISOLATED OR EMBEDDED

NUMBER OF NODES IS 11

STEREO ATTRIBUTES: NONE

L10 1421 SEA FILE=REGISTRY SSS FUL L1 AND L8

L11 792 SEA FILE=CAPLUS ABB=ON PLU=ON L10

L12 34 SEA FILE=CAPLUS ABB=ON PLU=ON L11 AND (PHOTORESIS OR RESIST

OR PHOTOLITHOGRAPHY)

#### => d ti 1-34

- L12 ANSWER 1 OF 34 CAPLUS COPYRIGHT 2003 ACS on STN
- TI Fluorine-containing norbornene polymers and their uses for antireflective films, photosensitive coatings, and **resists**
- L12 ANSWER 2 OF 34 CAPLUS COPYRIGHT 2003 ACS on STN
- Fluorine-containing norbornene polymers and their uses for antireflective films, photosensitive coatings, and resists

- L12 ANSWER 3 OF 34 CAPLUS COPYRIGHT 2003 ACS on STN
- TI Surface functionalization of thermoplastic polymers for the fabrication of microfluidic devices by photoinitiated grafting
- L12 ANSWER 4 OF 34 CAPLUS COPYRIGHT 2003 ACS on STN
- TI A study of high accuracy screen printing method (HADOP) a HADOP system and optimization of the materials
- L12 ANSWER 5 OF 34 CAPLUS COPYRIGHT 2003 ACS on STN
- TI Alkali-developable water-based solder photoresist compositions with good screen printability, and their cured films with no pinhole
- L12 ANSWER 6 OF 34 CAPLUS COPYRIGHT 2003 ACS on STN
- TI Cross-linking monomers for photoresists and preparation of photoresist polymers
- L12 ANSWER 7 OF 34 CAPLUS COPYRIGHT 2003 ACS on STN
- TI Flame retardant photosolder resist composition and cured solder resist coating for printed circuit board
- L12 ANSWER 8 OF 34 CAPLUS COPYRIGHT 2003 ACS on STN
- TI Alkaline-developable photosolder resist composition and cured solder resist coating for printed circuit board
- L12 ANSWER 9 OF 34 CAPLUS COPYRIGHT 2003 ACS on STN
- TI Water-soluble photosolder resist composition and cured solder resist coating for printed circuit board
- L12 ANSWER 10 OF 34 CAPLUS COPYRIGHT 2003 ACS on STN
- TI Radiation-curable epoxy resin compositions with good storage stability at high temperatures
- L12 ANSWER 11 OF 34 CAPLUS COPYRIGHT 2003 ACS on STN
- Curable resins and their compositions for alkali-developable solder resists with good dielectric properties
- L12 ANSWER 12 OF 34 CAPLUS COPYRIGHT 2003 ACS on STN
- TI Acrylic photoresist polymers bearing cyclotetrasiloxanyl groups, their preparation, composition, and photolithography thereof
- L12 ANSWER 13 OF 34 CAPLUS COPYRIGHT 2003 ACS on STN
- TI Light-sensitive photoresist polyurethane oligomer composition and method for pattern formation using same
- L12 ANSWER 14 OF 34 CAPLUS COPYRIGHT 2003 ACS on STN
- TI Photoresist monomer, photoresist polymer, manufacture of the polymer, photoresist composition, patterning of photoresist, and semiconductor device manufactured by using the photoresist pattern
- L12 ANSWER 15 OF 34 CAPLUS COPYRIGHT 2003 ACS on STN -
- TI Radiation-sensitive chemically amplified resist composition

Page 4Lee507

#### containing specific copolymer

- L12 ANSWER 16 OF 34 CAPLUS COPYRIGHT 2003 ACS on STN
- TI Radiation-sensitive resin composition as chemically-amplified photoresist with superior dry etching resistance and resolution for deep UV lithography
- L12 ANSWER 17 OF 34 CAPLUS COPYRIGHT 2003 ACS on STN
- TI Crosslinking monomer containing double bond and photoresist copolymer containing the same
- L12 ANSWER 18 OF 34 CAPLUS COPYRIGHT 2003 ACS on STN
- TI Radiation-sensitive polymer composition for photoresist
- L12 ANSWER 19 OF 34 CAPLUS COPYRIGHT 2003 ACS on STN
- TI Radiation sensitive resin composition
- L12 ANSWER 20 OF 34 CAPLUS COPYRIGHT 2003 ACS on STN
- TI Radiation-sensitive resin composition
- L12 ANSWER 21 OF 34 CAPLUS COPYRIGHT 2003 ACS on STN
- TI Radiation-sensitive resin composition
- L12 ANSWER 22 OF 34 CAPLUS COPYRIGHT 2003 ACS on STN
- TI Fabrication of shadow mask using UV-curable acrylic back coating with excellent pore sealability
- L12 ANSWER 23 OF 34 CAPLUS COPYRIGHT 2003 ACS on STN
- TI Resist composition and its use for forming patterns
- L12 ANSWER 24 OF 34 CAPLUS COPYRIGHT 2003 ACS on STN
- TI Acrylic or methacrylic acid derivatives and polymers therefrom useful for resist compositions used in production of semiconductor devices
- L12 ANSWER 25 OF 34 CAPLUS COPYRIGHT 2003 ACS on STN
- TI Novel (meth)acrylic acid derivatives and curable compositions therefrom with good heat resistance, water resistance, electric insulation properties and adhesion to substrates
- L12 ANSWER 26 OF 34 CAPLUS COPYRIGHT 2003 ACS on STN
- TI Color filter materials having high transparency and low reflectance and high-definition color filters for liquid crystal displays
- L12 ANSWER 27 OF 34 CAPLUS COPYRIGHT 2003 ACS on STN
- TI Manufacture of phenolic resins and epoxy resins for laminates, sealants, and solder resists and photocurable compositions
- L12 ANSWER 28 OF 34 CAPLUS COPYRIGHT 2003 ACS on STN
- TI Photopolymerization initiators for photocurable compositions
- L12 ANSWER 29 OF 34 CAPLUS COPYRIGHT 2003 ACS on STN
- TI UV-curable resin compositions for electrically insulating coatings and

#### Page 5Lee507

colorant compositions containing them

L12 ANSWER 30 OF 34 CAPLUS COPYRIGHT 2003 ACS on STN

Patterning of gold film TI

L12 ANSWER 31 OF 34 CAPLUS COPYRIGHT 2003 ACS on STN

Light-transmitting material and its manufacture, and resin compositions for claddings for light-transmitting materials

L12 ANSWER 32 OF 34 CAPLUS COPYRIGHT 2003 ACS on STN

Curable polyene-polythiol resin compositions

L12 ANSWER 33 OF 34 CAPLUS COPYRIGHT 2003 ACS on STN

Polymerizable (meth)allylnorbornene dicarboximide-(meth)acrylate ester compositions

L12 ANSWER 34 OF 34 CAPLUS COPYRIGHT 2003 ACS on STN

Photocurable flexible inks

#### => d ibib abs hitstr ind total

L12 ANSWER 1 OF 34 CAPLUS COPYRIGHT 2003 ACS on STN

ACCESSION NUMBER:

2003:368925 CAPLUS

DOCUMENT NUMBER:

138:386269

TITLE:

Fluorine-containing norbornene polymers and their uses for antireflective films, photosensitive coatings, and

resists

INVENTOR(S):

Koga, Tadashi; Maeda, Kazuhiko Central Glass Co., Ltd., Japan Jpn. Kokai Tokkyo Koho, 13 pp.

SOURCE:

CODEN: JKXXAF

DOCUMENT TYPE:

Patent Japanese LANGUAGE:

FAMILY ACC. NUM. COUNT:

PATENT INFORMATION:

PATENT ASSIGNEE(S):

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
JP 2003137939	A2	20030514	JP 2001-339981 JP 2001-339981	20011105
PRIORITY APPLN. INFO.	:		JP 2001-339981	20011103
GI.				

The polymers comprise .gtoreq.60 mol% norbornene repeating units I (R1-R4 = H, halo, C1-20 alkyl, CO2H, OH, cyano, etc.; .gtoreq.1 of R1-R4 = F-contg. group) and .gtoreq.0.1 mol% repeating units (CH2CR5)R6(CR7CH2) [R5, R7 = H, F, alkyl, fluoroalkyl; R6 = (ether- or ester-contg.) (fluoro)hydrocarbylene] and are manufd. by polymn. using peroxides at .gtoreq.100.degree.. Thus, 19.27 g 3-(5-bicyclo[2.2.1]hepten-2-yl)-1,1,1-trifluoro-2-(trifluoromethyl)-2-propanol was polymd. with 0.73 g divinyl adipate to give copolymer, which was made into a film showing 650-nm light reflectance 0.98% and good weather resistance.

IT 521947-52-4P

RL: IMF (Industrial manufacture); PRP (Properties); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses) (manuf. of F-contg. norbornene polymers for antireflective films, photosensitive coatings, and resists)

RN 521947-52-4 CAPLUS

CN Bicyclo[2.2.1]hept-5-ene-2-carboxylic acid, 2-(trifluoromethyl)-, polymer with 1,4-butanediyl bis[2-(trifluoromethyl)-2-propenoate] (9CI) (CA INDEX NAME)

CM 1

CRN 521947-47-7 CMF C12 H12 F6 O4

CM 2

CRN 370102-78-6 CMF C9 H9 F3 O2

IC ICM C08F232-04

ICS C07C033-44; C07C061-40; C07C069-653; C08F220-10; C08F220-20; C08F220-22; C08F222-06; C08F232-08; G03F007-039

CC 37-3 (Plastics Manufacture and Processing) Section cross-reference(s): 38, 74

ST fluoro norbornene polymer antireflective film resist; photosensitive coating fluoro norbornene polymer; vinyl adipate

IT Coating materials (light-sensitive; manuf. of F-contg. norbornene polymers for antireflective films, photosensitive coatings, and resists) IT Antireflective films Photoresists (manuf. of F-contg. norbornene polymers for antireflective films, photosensitive coatings, and resists) ITFluoropolymers, preparation RL: IMF (Industrial manufacture); PRP (Properties); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses) (manuf. of F-contq. norbornene polymers for antireflective films, photosensitive coatings, and resists) IT Polymerization catalysts (peroxides; manuf. of F-contg. norbornene polymers for antireflective films, photosensitive coatings, and resists) IT Peroxides, uses RL: CAT (Catalyst use); USES (Uses) (polymn. initiators; manuf. of F-contg. norbornene polymers for antireflective films, photosensitive coatings, and resists) 105935-24-8P 521947-47-7P IT 80830-27-9P RL: IMF (Industrial manufacture); RCT (Reactant); PREP (Preparation); RACT (Reactant or reagent) (comonomer; manuf. of F-contg. norbornene polymers for antireflective films, photosensitive coatings, and resists) IT 1992-15-0 RL: RCT (Reactant); RACT (Reactant or reagent) (intermediate for comonomer; manuf. of F-contg. norbornene polymers for antireflective films, photosensitive coatings, and resists) IT 521947-49-9P 521947-50-2P 521947-51-3P **521947-52-4P** 521947-54-6P 521947-55-7P 521947-53-5P 521947-56-8P RL: IMF (Industrial manufacture); PRP (Properties); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses) (manuf. of F-contg. norbornene polymers for antireflective films, photosensitive coatings, and resists) IT 196314-61-1P 365568-55-4P 370102-78-6P RL: IMF (Industrial manufacture); RCT (Reactant); PREP (Preparation); RACT (Reactant or reagent) (monomer; manuf. of F-contg. norbornene polymers for antireflective films, photosensitive coatings, and resists) 110-05-4, Di-tert-butyl peroxide 614-45-9, tert-Butyl peroxybenzoate IT 27073-06-9, Di-tert-hexyl peroxide 3457-61-2, tert-Butyl cumyl peroxide RL: CAT (Catalyst use); USES (Uses) (polymn. initiator; manuf. of F-contg. norbornene polymers for antireflective films, photosensitive coatings, and resists) IT 110-63-4, Butylene glycol, reactions RL: RCT (Reactant); RACT (Reactant or reagent) (reactant for comonomer; manuf. of F-contg. norbornene polymers for antireflective films, photosensitive coatings, and resists) 77-73-6, Dicyclopentadiene 115-11-7, Isobutene, reactions IT 2-Trifluoromethylacrylic acid 542-92-7, Cyclopentadiene, reactions 646-97-9, 1,1,1-Trifluoro-2-(trifluoromethyl)pent-4-en-2-ol

fluoronorbornene copolymer antireflective film

#### Page 8Lee507

RL: RCT (Reactant); RACT (Reactant or reagent)
 (reactant for monomer; manuf. of F-contg. norbornene polymers for
 antireflective films, photosensitive coatings, and resists)

L12 ANSWER 2 OF 34 CAPLUS COPYRIGHT 2003 ACS on STN

ACCESSION NUMBER:

2003:366812 CAPLUS

DOCUMENT NUMBER:

138:369658

TITLE:

Fluorine-containing norbornene polymers and their uses for antireflective films, photosensitive coatings, and

resists

INVENTOR(S):
PATENT ASSIGNEE(S):

Koga, Tadashi; Maeda, Kazuhiko Central Glass Co., Ltd., Japan Jpn. Kokai Tokkyo Koho, 11 pp.

SOURCE:

CODEN: JKXXAF

DOCUMENT TYPE:

Patent

LANGUAGE:

Japanese

FAMILY ACC. NUM. COUNT: 1

PATENT INFORMATION:

PATENT NO. KIND DATE APPLICATION NO. DATE

JP 2003137940 A2 20030514 JP 2001-339982 20011105

PRIORITY APPLN. INFO.: JP 2001-339982 20011105

$$\begin{array}{c|c}
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\
 & & \\$$

AB The polymers comprise norbornene repeating units I (R1-R4 = H, halo, C1-20 alkyl, CO2H, OH, cyano, etc.; .gtoreq.1 of R1-R4 = F-contg. group) and repeating units CR5R6R7 (R5, R6 = alkyl, fluoroalkyl; R5 and/or R6 = fluoroalkyl; R7 = O, CH2). Thus, 39.70 g 3-(5-bicyclo[2.2.1]hepten-2-yl)-1,1,1-trifluoro-2-trifluoromethyl-2-propanol was polymd. with 10.30 g (F3C)2CO to give copolymer, which was made into a film showing 650-nm light reflectance 0.98% and good weather resistance.

IT 521949-37-1P

RL: IMF (Industrial manufacture); PRP (Properties); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses) (manuf. of F-contg. norbornene polymers for antireflective films, photosensitive coatings, and resists)

521949-37-1 CAPLUS

т

CN Bicyclo[2.2.1]hept-5-ene-2-carboxylic acid, 2-(trifluoromethyl)-, 1,1-dimethylethyl ester, polymer with .alpha.,.alpha.-bis(trifluoromethyl)bicyclo[2.2.1]hept-5-ene-2-ethanol, 1,4-butanediyl

RN

Page 9Lee507

bis[2-(trifluoromethyl)-2-propenoate] and 1,1,1,3,3,3-hexafluoro-2propanone (9CI) (CA INDEX NAME)

CM 1

CRN 521947-47-7 CMF C12 H12 F6 O4

CM 2

CRN 365568-55-4 CMF C13 H17 F3 O2

CM 3

CRN 196314-61-1 CMF C11 H12 F6 O

CM 4

CRN 684-16-2 CMF C3 F6 O

```
F3C-C-CF3
IC
     ICM C08F232-08
     ICS C09D127-12; C09D145-00
CC
     37-3 (Plastics Manufacture and Processing)
     Section cross-reference(s): 38, 74
ST
     fluoro norbornene polymer antireflective film resist;
     photosensitive coating fluoro norbornene polymer; fluoroacetone
     fluoronorbornene copolymer antireflective film
IT
     Polyethers, preparation
     RL: IMF (Industrial manufacture); PRP (Properties); TEM (Technical or
     engineered material use); PREP (Preparation); USES (Uses)
        (fluorine-contg.; manuf. of F-contg. norbornene polymers for
        antireflective films, photosensitive coatings, and resists)
TT
     Coating materials
        (light-sensitive; manuf. of F-contg. norbornene polymers for
        antireflective films, photosensitive coatings, and resists)
     Antireflective films
IT
     Photoresists
        (manuf. of F-contg. norbornene polymers for antireflective films,
        photosensitive coatings, and resists)
TT
     Fluoropolymers, preparation
     RL: IMF (Industrial manufacture); PRP (Properties); TEM (Technical or
     engineered material use); PREP (Preparation); USES (Uses)
        (manuf. of F-contg. norbornene polymers for antireflective films,
        photosensitive coatings, and resists)
     Fluoropolymers, preparation
IT
     RL: IMF (Industrial manufacture); PRP (Properties); TEM (Technical or
     engineered material use); PREP (Preparation); USES (Uses)
        (polyether-; manuf. of F-contq. norbornene polymers for antireflective
        films, photosensitive coatings, and resists)
     521947-47-7P
TT
     RL: IMF (Industrial manufacture); RCT (Reactant); PREP (Preparation); RACT
     (Reactant or reagent)
        (comonomer; manuf. of F-contg. norbornene polymers for antireflective
        films, photosensitive coatings, and resists)
IT
     105935-24-8P
     RL: IMF (Industrial manufacture); RCT (Reactant); PREP (Preparation); RACT
     (Reactant or reagent)
        (intermediate for monomer; manuf. of F-contg. norbornene polymers for
        antireflective films, photosensitive coatings, and resists)
     521949-34-8P
                    521949-35-9P
                                   521949-36-0P 521949-37-1P
IT
     521949-38-2P
                    521949-39-3P
     RL: IMF (Industrial manufacture); PRP (Properties); TEM (Technical or
     engineered material use); PREP (Preparation); USES (Uses)
        (manuf. of F-contg. norbornene polymers for antireflective films,
        photosensitive coatings, and resists)
IT
     196314-61-1P
                   365568-55-4P
```

#### Page 11Lee507

RL: IMF (Industrial manufacture); RCT (Reactant); PREP (Preparation); RACT (Reactant or reagent)

(monomer; manuf. of F-contq. norbornene polymers for antireflective films, photosensitive coatings, and resists)

110-63-4, Butylene glycol, reactions IT

RL: RCT (Reactant); RACT (Reactant or reagent)

(reactant for comonomer; manuf. of F-contg. norbornene polymers for antireflective films, photosensitive coatings, and resists)

77-73-6, Dicyclopentadiene 115-11-7, Isobutene, reactions ΙT 542-92-7, Cyclopentadiene, reactions 2-Trifluoromethylacrylic acid 646-97-9, 1,1,1-Trifluoro-2-(trifluoromethyl)pent-4-en-2-ol

RL: RCT (Reactant); RACT (Reactant or reagent)

(reactant for monomer; manuf. of F-contg. norbornene polymers for antireflective films, photosensitive coatings, and resists)

L12 ANSWER 3 OF 34 CAPLUS COPYRIGHT 2003 ACS on STN

2003:346136 CAPLUS ACCESSION NUMBER:

DOCUMENT NUMBER: 139:150057

Surface functionalization of thermoplastic polymers TITLE:

for the fabrication of microfluidic devices by

photoinitiated grafting

Rohr, Thomas; Ogletree, D. Frank; Svec, Frantisek; AUTHOR (S):

Frechet, Jean M. J.

Materials Sciences Division, E.O. Lawrence Berkeley CORPORATE SOURCE:

National Laboratory, Berkeley, CA, 94720, USA

Advanced Functional Materials (2003), 13(4), 264-270 SOURCE:

CODEN: AFMDC6; ISSN: 1616-301X

PUBLISHER: Wiley-VCH Verlag GmbH & Co. KGaA

Journal DOCUMENT TYPE: English LANGUAGE:

Photografting has been used for the surface modification of a wide range AΒ of com. commodity polymers such as polystyrene, poly(Me methacrylate), poly(di-Me siloxane), polycarbonate, Parylene C, polypropylene, cyclic olefin copolymer, and hydrogenated polystyrene that are useful substrate materials for the fabrication of microfluidic chips. Since the chain propagation is initiated after UV light-activated abstraction of a hydrogen atom from the surface of channels within the materials, their permeability for UV light was tested and polyolefins were found to be the best candidates. A no. of monomers with a variety of functional groups such as perfluorinated, hydrophobic, hydrophilic, reactive, acidic, basic, and zwitterionic have been successfully grafted from the surface of selected substrates, and the grafting efficiency detd. using X-ray photoemission spectroscopy. Layered surface structures were prepd. by consecutive grafting of different monomers. Our approach also enables photolithog. patterning of surfaces and specific functionalization of confined areas within the microchannel.

572923-55-8P 572923-56-9P TT

> RL: SPN (Synthetic preparation); PREP (Preparation) (surface functionalization of thermoplastic polymers for fabrication of microfluidic devices by photoinitiated grafting)

RN 572923-55-8 CAPLUS

2-Propenoic acid, 1,2-ethanediyl ester, polymer with bicyclo[2.2.1]hept-2-CN

```
Page 12Lee507
```

ene and ethene, graft (9CI) (CA INDEX NAME)

CM 1

CRN 2274-11-5 CMF C8 H10 O4

$$\begin{array}{c} {}^{\mathsf{O}} & {}^{\mathsf{O}} \\ \| \\ {}^{\mathsf{H}_2\mathsf{C}} = {}^{\mathsf{CH}_{-}} {}^{\mathsf{C}_{-}} {}^{\mathsf{O}_{-}} {}^{\mathsf{CH}_2} - {}^{\mathsf{C}_{+2}} - {}^{\mathsf{O}_{-}} {}^{\mathsf{C}_{-}} {}^{\mathsf{C}_{+2}} = {}^{\mathsf{C}_{+2}} \\ \end{array}$$

CM 2

CRN 498-66-8 CMF C7 H10



CM 3

CRN 74-85-1 CMF C2 H4

 $H_2C = CH_2$ 

RN 572923-56-9 CAPLUS

CN 2-Propenoic acid, 2-methyl-, 1,2-ethanediyl ester, polymer with bicyclo[2.2.1]hept-2-ene and ethene, graft (9CI) (CA INDEX NAME)

CM 1

CRN 498-66-8 CMF C7 H10 Page 13Lee507



CM 2

CRN 97-90-5 CMF C10 H14 O4

CM 3

CRN 74-85-1 CMF C2 H4

 $H_2C = CH_2$ 

CC 35-8 (Chemistry of Synthetic High Polymers)

ST thermoplastic polymer surface functionalization photoinitiated grafting

IT Borosilicate glasses Polycarbonates, uses

Polysiloxanes, uses

RL: TEM (Technical or engineered material use); USES (Uses) (filter; surface functionalization of thermoplastic polymers for fabrication of microfluidic devices by photoinitiated grafting)

IT Polymerization

(graft, photochem.; surface functionalization of thermoplastic polymers for fabrication of microfluidic devices by photoinitiated grafting)

IT Contact angle

(surface functionalization of thermoplastic polymers for fabrication of microfluidic devices by photoinitiated grafting)

IT Fluoropolymers, preparation

RL: SPN (Synthetic preparation); PREP (Preparation)

(surface functionalization of thermoplastic polymers for fabrication of microfluidic devices by photoinitiated grafting)

IT 9003-07-0, Polypropylene 9003-53-6, Polystyrene 9003-53-6D,
 Polystyrene, hydrogenated 9003-63-8, Poly(butyl methacrylate)
 9011-14-7, PMMA 9016-00-6, PDMS 9052-19-1, Parylene C 14808-60-7,
 Quartz, uses 31900-57-9, PDMS

```
RL: TEM (Technical or engineered material use); USES (Uses)
        (filter; surface functionalization of thermoplastic polymers for
        fabrication of microfluidic devices by photoinitiated grafting)
IT
     109997-76-4P
                    113408-85-8P
                                   133097-40-2P
                                                  135142-55-1P
                                                                 180678-83-5P
     572923-71-8P
     RL: PRP (Properties); SPN (Synthetic preparation); PREP (Preparation)
        (surface functionalization of thermoplastic polymers for fabrication of
        microfluidic devices by photoinitiated grafting)
ΙT
     160678-98-8P
                   160679-00-5P
                                   519142-54-2P
                                                  572923-47-8P
                                                                 572923-48-9P
     572923-49-0P
                    572923-50-3P
                                   572923-51-4P
                                                  572923-52-5P
                                                                 572923-53-6P
     572923-54-7P 572923-55-8P 572923-56-9P
                                            572923-57-0P
     572923-58-1P 572923-59-2P 572923-60-5P 572923-61-6P
                                                                 572923-62-7P
     572923-63-8P
                    572923-64-9P 572923-65-0P
                                                  572923-66-1P
                                                                 572923-67-2P
                    572923-69-4P 572923-70-7P 572923-72-9P
     572923-68-3P
                                                                 573673-61-7P
     573673-62-8P
     RL: SPN (Synthetic preparation); PREP (Preparation)
        (surface functionalization of thermoplastic polymers for fabrication of
        microfluidic devices by photoinitiated grafting)
REFERENCE COUNT:
                         32
                               THERE ARE 32 CITED REFERENCES AVAILABLE FOR THIS
                               RECORD. ALL CITATIONS AVAILABLE IN THE RE FORMAT
L12 ANSWER 4 OF 34 CAPLUS COPYRIGHT 2003 ACS on STN
ACCESSION NUMBER:
                         2003:340471 CAPLUS
DOCUMENT NUMBER:
                         139:171210
TITLE:
                         A study of high accuracy screen printing method
                         (HADOP) - a HADOP system and optimization of the
                         materials
AUTHOR (S):
                         Higuchi, Youichi
CORPORATE SOURCE:
                        Display Components Lab., Dai Nippon Printing Co.,
                        Ltd., Kitasaitama-gun, Saitama, 349-1148, Japan
                        Nippon Insatsu Gakkaishi (2003), 40(1), 33-41
SOURCE:
                         CODEN: NIGAEV; ISSN: 0914-3319
PUBLISHER:
                        Nippon Insatsu Gakkai
DOCUMENT TYPE:
                         Journal
LANGUAGE:
                         Japanese
    The invention relates to a new high accuracy screen printing method
AB
     (HADOP: High accuracy and dry on-demand printing) was designed and high
     resoln. printing was achieved. HADOP printing plate and neg.
    resist ink materials were optimized. Neg. resist
    materials for the high resoln. plate and an ink of a certain viscosity
    characteristic were selected, and high accuracy screen printing was
    obtained. The screen plate for HADOP was particularly improved by
    optimization of diam. and mesh angle of the wire, an ink of a high state
    of thixotropy was used because of great important i flatness property of
          As a result, the thixotropic ink could be fixed on a base side of
    plate after passing through the small patterning holes. The sharp imaging
    was performed by increasing the transferring ratio of ink. Thus, isolated
    lines of 40 .mu.m levels were completed by the HADOP method. A superior
    color filter of good color reprodn. was developed by high transparency and
    high transmission factor of the ink constituents.
    123535-77-3, Dipentaerythritol hexaacrylate-R 684 copolymer
IT
    RL: TEM (Technical or engineered material use); USES (Uses)
```

#### Page 15Lee507

(high accuracy screen printing method)

RN 123535-77-3 CAPLUS

CN 2-Propenoic acid, (octahydro-4,7-methano-1H-indene-5,?-diyl)bis(methylene)
 ester, polymer with 2-[[3-[(1-oxo-2-propenyl)oxy]-2,2-bis[[(1-oxo-2-propenyl)oxy]methyl]propoxy]methyl]-2-[[(1-oxo-2-propenyl)oxy]methyl]-1,3 propanediyl di-2-propenoate (9CI) (CA INDEX NAME)

CM 1

CRN 42594-17-2 CMF C18 H24 O4 CCI IDS

$$\begin{bmatrix}
0 & & & \\
0 & & & \\
D1-CH_2-O-C-CH-CH_2 & & \\
\end{bmatrix}$$

CM 2

CRN 29570-58-9 CMF C28 H34 O13

CC 74-13 (Radiation Chemistry, Photochemistry, and Photographic and Other Reprographic Processes)

ST accuracy screen printing color filter display

IT Color

Gel permeation chromatography IR spectra Viscosity

```
(high accuracy screen printing method)
IT
     Optical filters
     Optical imaging devices
     Screen printing
         (high accuracy screen printing method (HADOP) - a HADOP system and
        optimization of materials)
IT
     Inks
         (silk-screen, EG-Red; resist ink for high accuracy screen
        printing method)
IT
     Strain
         (sweep; high accuracy screen printing method)
IT
     1310-58-3, Potassium hydroxide, processes
     RL: CPS (Chemical process); PEP (Physical, engineering or chemical
     process); PROC (Process)
         (developer for high accuracy screen printing method)
IT
     1344-28-1, Alumina, processes
                                    2530-85-0, .gamma.-
     Methacryloxypropyltrimethoxysilane 29570-58-9, Dipentaerythritol
     hexaacrylate
     RL: CPS (Chemical process); PEP (Physical, engineering or chemical
     process); PROC (Process)
        (high accuracy screen printing method)
IT
     4491-03-6, Bisphenol A diacrylate 64401-02-1, Bisphenol A-ethylene oxide
     adduct diacrylate 101232-56-8, Dipentaerythritol hexaacrylate-R 128H
     copolymer 123535-77-3, Dipentaerythritol hexaacrylate-R 684
     copolymer
                 179490-75-6, Dipentaerythritol hexaacrylate-ethoxylated
     bisphenol A copolymer 577749-25-8, Dipentaerythritol hexaacrylate-MANDA
     copolymer
     RL: TEM (Technical or engineered material use); USES (Uses)
        (high accuracy screen printing method)
ΙT
     7473-98-5
                 69432-40-2, TAZ 106
     RL: CAT (Catalyst use); USES (Uses)
        (photopolymn. initiator for high accuracy screen printing method)
IT
     78-67-1, AIBN
     RL: CAT (Catalyst use); USES (Uses)
        (polymer for high accuracy screen printing method)
IT
     4435-53-4, 3-Methoxybutyl acetate
     RL: NUU (Other use, unclassified); USES (Uses)
        (polymer for high accuracy screen printing method)
IT
     209689-00-9P
     RL: SPN (Synthetic preparation); TEM (Technical or engineered material
     use); PREP (Preparation); USES (Uses)
        (polymer for high accuracy screen printing method)
IT
     193363-36-9, ACA 200
    RL: TEM (Technical or engineered material use); USES (Uses)
        (polymer for high accuracy screen printing method)
IT
    147-14-8, C.I. Pigment Blue 15:3
                                        4051-63-2, C.I. Pigment Red 177
    14302-13-7, C.I. Pigment Green 36
    RL: NUU (Other use, unclassified); USES (Uses)
        (resist ink for high accuracy screen printing method)
IT
    154213-94-2, Disperbyk 161
    RL: PEP (Physical, engineering or chemical process); PYP (Physical
    process); PROC (Process)
```

L12 ANSWER 5 OF 34 CAPLUS COPYRIGHT 2003 ACS on STN

ACCESSION NUMBER: 2003:259907 CAPLUS

DOCUMENT NUMBER: 138:294911

TITLE: Alkali-developable water-based solder photoresist

compositions with good screen printability, and their

cured films with no pinhole

INVENTOR(S): Yabuuchi, Naoya; Yamada, Atsushi; Nanba, Osamu

PATENT ASSIGNEE(S): Nippon Paint Co., Ltd., Japan SOURCE: Jpn. Kokai Tokkyo Koho, 8 pp.

CODEN: JKXXAF

DOCUMENT TYPE: Patent LANGUAGE: Japanese

FAMILY ACC. NUM. COUNT: 1

PATENT INFORMATION:

PATENT NO. KIND DATE APPLICATION NO. DATE

JP 2003098668 A2 20030404 JP 2001-288690 20010921

PRIORITY APPLN. INFO.: JP 2001-288690 20010921

- The compns. comprise (A) aq. solns. of resins having radically polymerizable groups and carboxyl groups that are neutralized by bases, (B) inorg. fillers, (C) photocurable mixts. contg. polyfunctional acrylic monomers, cyclic ether compds., and photoinitiators, and (D) org. solvents with b.p. 180-290.degree.. Screen clogging by quick drying in screen printing is prevented with this invention.
- IT 504423-24-9P, Isobornyl methacrylate-methacrylic acid-methyl methacrylate copolymer glycidyl methacrylate ester, triethylamine salt, polymer with GT 401, pentaerythritol tetraacrylate, and trimethylolpropane trimethacrylate

RL: IMF (Industrial manufacture); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

(alkali-developable aq. solder photoresists with good screen printability and no pinhole)

RN 504423-24-9 CAPLUS

CN 2-Propenoic acid, 2-methyl-, polymer with methyl 2-methyl-2-propenoate and rel-(1R,2R,4R)-1,7,7-trimethylbicyclo[2.2.1]hept-2-yl 2-methyl-2-propenoate, 2-hydroxy-3-[(2-methyl-1-oxo-2-propenyl)oxy]propyl ester, polymer with 2,2-bis[[(1-oxo-2-propenyl)oxy]methyl]-1,3-propanediyl di-2-propenoate, Epolead GT 401 and 2-ethyl-2-[[(2-methyl-1-oxo-2-propenyl)oxy]methyl]-1,3-propanediyl bis(2-methyl-2-propenoate), compd. with N,N-diethylethanamine (9CI) (CA INDEX NAME)

CM 1

CRN 121-44-8 CMF C6 H15 N Page 18Lee507

CM 2

CRN 509084-98-4

CMF (C18 H26 O6 . C17 H20 O8 . (C14 H22 O2 . C5 H8 O2 . C4 H6 O2)x . x C7 H12 O4 . Unspecified)x

CCI PMS

CM 3

CRN 149984-16-7 CMF Unspecified CCI PMS, MAN

\*\*\* STRUCTURE DIAGRAM IS NOT AVAILABLE \*\*\*

CM 4

CRN 4986-89-4 CMF C17 H20 O8

CM 5

CRN 3290-92-4 CMF C18 H26 O6 Page 19Lee507

CM 6

CRN 504423-22-7

CMF (C14 H22 O2 . C5 H8 O2 . C4 H6 O2)x . x C7 H12 O4

CM 7

CRN 5919-74-4 CMF C7 H12 O4

CM 8

CRN 154454-75-8

CMF (C14 H22 O2 . C5 H8 O2 . C4 H6 O2)  $\times$ 

CCI PMS

CM 9

CRN 7534-94-3 CMF C14 H22 O2

Relative stereochemistry.

CM 10

CRN 80-62-6 CMF C5 H8 O2

CM 11

CRN 79-41-4 CMF C4 H6 O2

 $^{\mathrm{CH_2}}_{\parallel}$  Me $^-$  C $^-$  CO $_2$ H

IC ICM G03F007-038

ICS H05K003-28

CC 74-5 (Radiation Chemistry, Photochemistry, and Photographic and Other Reprographic Processes) Section cross-reference(s): 38, 76

ST solder photoresist aq screen printing anticlogging; acrylic photoresist drying prevention solvent alkali developable

IT Epoxy resins, preparation

RL: IMF (Industrial manufacture); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

(acrylic; alkali-developable aq. solder photoresists with good screen printability and no pinhole)

IT Solvents

(org., high b.p.; alkali-developable aq. solder photoresists with good screen printability and no pinhole)

IT Solder resists

(photoresists; alkali-developable aq. solder photoresists with good screen printability and no pinhole)

IT Photoresists

(solder; alkali-developable aq. solder photoresists with good screen printability and no pinhole)

IT 504423-24-9P, Isobornyl methacrylate-methacrylic acid-methyl methacrylate copolymer glycidyl methacrylate ester, triethylamine salt, polymer with GT 401, pentaerythritol tetraacrylate, and trimethylolpropane trimethacrylate

RL: IMF (Industrial manufacture); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

(alkali-developable aq. solder photoresists with good screen printability and no pinhole)

IT 7727-43-7, B 34

RL: TEM (Technical or engineered material use); USES (Uses) (filler, photoresist compns. contg.; alkali-developable aq. solder photoresists with good screen printability and no pinhole)

IT 105-76-0, Dibutyl maleate 122-99-6, Ethylene glycol monophenyl ether 2050-25-1, Diethylene glycol monobenzyl ether 30136-13-1, Propylene glycol monopropyl ether 41593-38-8, Propylene glycol monophenyl ether 63512-36-7, Triethylene glycol dibutyl ether

RL: NUU (Other use, unclassified); USES (Uses)

(high b.p. solvent; alkali-developable aq. solder photoresists with good screen printability and no pinhole)

IT 504423-23-8P, Isobornyl methacrylate-methacrylic acid-methyl methacrylate copolymer glycidyl methacrylate ester, triethylamine salt RL: IMF (Industrial manufacture); RCT (Reactant); TEM (Technical or engineered material use); PREP (Preparation); RACT (Reactant or reagent); USES (Uses)

(photoresist compns. contg.; alkali-developable aq. solder photoresists with good screen printability and no pinhole)

IT 3290-92-4, Trimethylolpropane trimethacrylate 4986-89-4, Pentaerythritol tetraacrylate 149984-16-7, GT 401

RL: RCT (Reactant); TEM (Technical or engineered material use); RACT (Reactant or reagent); USES (Uses)

(photoresist compns. contg.; alkali-developable aq. solder photoresists with good screen printability and no pinhole)

L12 ANSWER 6 OF 34 CAPLUS COPYRIGHT 2003 ACS on STN

ACCESSION NUMBER: 2002:907050 CAPLUS

DOCUMENT NUMBER: 138:9661

TITLE: Cross-linking monomers for photoresists and

preparation of photoresist polymers

INVENTOR(S): Jung, Jae Chang; Kong, Keun Kyu; Jung, Min Ho; Lee,

Geun Su; Baik, Ki Ho

PATENT ASSIGNEE(S): Hyundai Electronics Industries Co., Ltd., S. Korea

SOURCE: U.S. Pat. Appl. Publ., 10 pp., Cont.-in-part of U.S.

Ser. No. 465,111, abandoned.

CODEN: USXXCO

DOCUMENT TYPE: Patent LANGUAGE: English

FAMILY ACC. NUM. COUNT: 2

PATENT INFORMATION:

PATENT NO. KIND DATE APPLICATION NO. DATE

US 2002177069 A1 20021128 US 2002-80507 20020222

PRIORITY APPLN. INFO.: KR 1998-63793 A 19981231
US 1999-465111 B2 19991216

GI

$$\begin{array}{c}
R' \\
C \\
C
\end{array} = O + R + O - C - C - R'$$

Ι

The present invention discloses a crosslinking monomer represented by the general formula I (R1, R2 = H, CH3; m = 1-10; R = C1-10-alkyl, C1-10-ester, C1-10-ketone, C1-10-carboxylic acid, C1-10-acetal, C1-10 alkyl) and a process for prepg. a photoresist polymer using the crosslinking monomer, and a photoresist polymer. The object of the present invention is to provide a crosslinking monomer for a photoresist polymer which can noticeably improve the polymn. yield of the photoresist polymer. Another object of the present invention is to provide a process for prepg. a photoresist polymer using said crosslinking monomer, and a photoresist polymer.

IT 282529-66-2P 282529-67-3P

RL: SPN (Synthetic preparation); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

(crosslinking monomers for photoresists and prepn. of photoresist polymers)

RN 282529-66-2 CAPLUS

CN Bicyclo[2.2.1]hept-5-ene-2-carboxylic acid, polymer with 1,1-dimethylethyl bicyclo[2.2.1]hept-5-ene-2-carboxylate, 2,5-furandione, 2-hydroxyethyl bicyclo[2.2.1]hept-5-ene-2-carboxylate and 1-methyl-1,3-propanediyl di-2-propenoate (9CI) (CA INDEX NAME)

CM 1

CRN 154970-45-3 CMF C12 H18 O2

CM 2

CRN 37503-42-7 CMF C10 H14 O3 Page 23Lee507

CM 3

CRN 19485-03-1 CMF C10 H14 O4

CM 4

CRN 120-74-1 CMF C8 H10 O2

CM 5

CRN 108-31-6 CMF C4 H2 O3

RN 282529-67-3 CAPLUS

CN Bicyclo[2.2.1]hept-5-ene-2-carboxylic acid, polymer with 1,4-butanediyl di-2-propenoate, 1,1-dimethylethyl bicyclo[2.2.1]hept-5-ene-2-carboxylate, 2,5-furandione and 2-hydroxyethyl bicyclo[2.2.1]hept-5-ene-2-carboxylate (9CI) (CA INDEX NAME)

CM 1

CRN 154970-45-3 CMF C12 H18 O2

CM 2

CRN 37503-42-7 CMF C10 H14 O3

CM 3

CRN 1070-70-8 CMF C10 H14 O4

CM 4

CRN 120-74-1 CMF C8 H10 O2

CM 5

CRN 108-31-6 CMF C4 H2 O3

IC ICM G03F007-038

ICS G03F007-38; G03F007-40; G03F007-32; G03F007-30

NCL 430270100; 430910000; 430914000; 430325000; 430326000; 430319000; 560224000; 526272000; 526281000; 526323200

CC 74-5 (Radiation Chemistry, Photochemistry, and Photographic and Other Reprographic Processes)
Section cross-reference(s): 38

ST photoresist UV crosslinking monomer copolymer prepn photolithog

IT Photolithography

Photoresists

(UV; crosslinking monomers for photoresists and prepn. of photoresist polymers)

IT 282529-66-2P 282529-67-3P

RL: SPN (Synthetic preparation); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

(crosslinking monomers for photoresists and prepn. of photoresist polymers)

IT 75-59-2, Tetramethylammonium hydroxide

RL: TEM (Technical or engineered material use); USES (Uses) (developer; crosslinking monomers for photoresists and prepn. of photoresist polymers)

IT 66003-78-9, Triphenylsulfonium triflate

RL: TEM (Technical or engineered material use); USES (Uses)
 (photoacid generator; crosslinking monomers for photoresists and prepn.
 of photoresist polymers)

IT 78-67-1, 2,2'-Azobisisobutyronitrile

RL: CAT (Catalyst use); USES (Uses)

(photoinitiator; crosslinking monomers for photoresists and prepn. of photoresist polymers)

IT 109-99-9, Tetrahydrofuran., uses

RL: NUU (Other use, unclassified); USES (Uses)

(polymn. solvent; crosslinking monomers for photoresists and prepn. of photoresist polymers)

L12 ANSWER 7 OF 34 CAPLUS COPYRIGHT 2003 ACS on STN

ACCESSION NUMBER:

2002:750932 CAPLUS

DOCUMENT NUMBER:

137:286447

TITLE:

Flame retardant photosolder resist

composition and cured solder resist coating

for printed circuit board

Page 26Lee507

INVENTOR(S): Yabuuchi, Naoya; Fujita, Minoru; Nanba, Osamu;

Okajima, Keiichi

PATENT ASSIGNEE(S): Nippon Paint Co., Ltd., Japan SOURCE: Jpn. Kokai Tokkyo Koho, 10 pp.

CODEN: JKXXAF

DOCUMENT TYPE: Patent LANGUAGE: Japanese

FAMILY ACC. NUM. COUNT: 1

PATENT INFORMATION:

PATENT NO. KIND DATE APPLICATION NO. DATE --------------JP 2002287358 A2 20021003 JP 2001-92199 20010328 PRIORITY APPLN. INFO.: JP 2001-92199 The invention relates to a flame retardant photosolder resist compn. comprising (A) a resin contg. radical polymerizable groups and carboxylic groups, (B) an inorg. filler, (C) a photocurable mixt. comprised of a polyfunctional acrylic monomer, a cycloether-contg. compd., and a photopolymn. initiator, and (D) nitrogen-contg. resin particles. The photosolder resist compn. may contain pigments. The photosolder resist compn. is coated on a substrate, dried at 50-90.degree., exposed pattenwisely to an actinic ray, developed with an alk. developer, and baked at 140-170.degree. to obtain the cured solder resist coating. The photosolder resist compn. shows excellent flame-retardance, developability, solder heat-resistance, gold plating-resistance, thermal shock-resistance, and elec. insulating property.

IT 464896-73-9P, Cyclohexyl methacrylate-glycidyl methacrylate-isobornyl methacrylate-methacrylic acid-pentaerythritol tetraacrylate-trimethylolpropane trimethacrylate copolymer 464896-74-0P, Glycidyl methacrylate-isobornyl methacrylate-methacrylic acid-methyl methacrylate-styrene-pentaerythritol tetraacrylate-trimethylolpropane trimethacrylate copolymer RL: PNU (Preparation, unclassified); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

(cured solder resist; flame retardant photosolder resist compn. for manufg. printed circuit board)

RN 464896-73-9 CAPLUS

CN 2-Propenoic acid, 2-methyl-, polymer with 2,2-bis[[(1-oxo-2-propenyl)oxy]methyl]-1,3-propanediyl di-2-propenoate, cyclohexyl 2-methyl-2-propenoate, 2-ethyl-2-[[(2-methyl-1-oxo-2-propenyl)oxy]methyl]-1,3-propanediyl bis(2-methyl-2-propenoate), oxiranylmethyl 2-methyl-2-propenoate and rel-(1R,2R,4R)-1,7,7-trimethylbicyclo[2.2.1]hept-2-yl 2-methyl-2-propenoate (9CI) (CA INDEX NAME)

CM 1

CRN 7534-94-3 CMF C14 H22 O2

Relative stereochemistry.

#### Page 27Lee507

CM 2

CRN 4986-89-4 CMF C17 H20 O8

CM 3

CRN 3290-92-4 CMF C18 H26 O6

CM 4

CRN 106-91-2 CMF C7 H10 O3 Page 28Lee507

$$\overset{\text{O}}{\underset{\text{CH}_2-\text{O-C-C-Me}}{|\hspace{-.08cm}|\hspace{-.08cm}|}}} \overset{\text{O}}{\underset{\text{CH}_2}{|\hspace{-.08cm}|\hspace{-.08cm}|}} \overset{\text{CH}_2}{\underset{\text{CH}_2-\text{O-C-C-Me}}{|\hspace{-.08cm}|\hspace{-.08cm}|}}$$

CM 5

CRN 101-43-9 CMF C10 H16 O2

CM 6

CRN 79-41-4 CMF C4 H6 O2

RN 464896-74-0 CAPLUS

2-Propenoic acid, 2-methyl-, polymer with 2,2-bis[[(1-oxo-2-propenyl)oxy]methyl]-1,3-propanediyl di-2-propenoate, ethenylbenzene, 2-ethyl-2-[[(2-methyl-1-oxo-2-propenyl)oxy]methyl]-1,3-propanediyl bis(2-methyl-2-propenoate), methyl 2-methyl-2-propenoate, oxiranylmethyl 2-methyl-2-propenoate and rel-(1R,2R,4R)-1,7,7-trimethylbicyclo[2.2.1]hept-2-yl 2-methyl-2-propenoate (9CI) (CA INDEX NAME)

CM 1

CRN 7534-94-3 CMF C14 H22 O2

Relative stereochemistry.

#### Page 29Lee507

CM 2

CRN 4986-89-4 CMF C17 H20 O8

$$\begin{array}{c} \circ \\ \circ \\ \parallel \\ H_2C = CH - C - O - CH_2 - C - CH_2 - O - C - CH = CH_2 \\ \cdot \\ H_2C = CH - C - O - CH_2 \\ \cdot \\ 0 \end{array}$$

CM 3

CRN 3290-92-4 CMF C18 H26 O6

CM 4

CRN 106-91-2 CMF C7 H10 O3 Page 30Lee507

CM 5

CRN 100-42-5 CMF C8 H8

 $H_2C = CH - Ph$ 

CM 6

CRN 80-62-6 CMF C5 H8 O2

$$^{\rm H_2C}_{\parallel}$$
  $^{\rm O}_{\parallel}$   $^{\rm Me-}$  C- C- OMe

CM 7

CRN 79-41-4 CMF C4 H6 O2

IC ICM G03F007-038

ICS C08F002-44; C08F002-50; C08F265-00; C08F290-00; C08K003-00;
C08L033-00; C08L063-00; C08L101-02; G03F007-004; G03F007-027;
G03F007-028; G03F007-032; G03F007-40; H05K003-28

CC 74-5 (Radiation Chemistry, Photochemistry, and Photographic and Other Reprographic Processes) Section cross-reference(s): 38, 76

ST flame retardant photosolder resist compn printed circuit board

IT Fire-resistant materials

Printed circuit boards

(flame retardant photosolder resist compn. and cured solder resist coating for printed circuit board)

```
IT
     Aminoplasts
     RL: TEM (Technical or engineered material use); USES (Uses)
        (flame retardant; flame retardant photosolder resist compn.
        for manufg. printed circuit board)
IT
     Solder resists
        (photoresists; flame retardant photosolder resist compn. and
        cured solder resist coating for printed circuit board)
IT
     Photoresists
        (solder; flame retardant photosolder resist compn. and cured
        solder resist coating for printed circuit board)
IT
     RL: TEM (Technical or engineered material use); USES (Uses)
        (B 34; flame retardant photosolder resist compn. for manufg.
        printed circuit board)
     244772-00-7, EHPE 3150
IT
     RL: TEM (Technical or engineered material use); USES (Uses)
        (EHPE 3150; flame retardant photosolder resist compn. for
        manufg. printed circuit board)
IT
     464891-71-2P, Glycidyl methacrylate-isobutyl methacrylate-methacrylic
     acid-methyl methacrylate-pentaerythritol tetraacrylate-trimethylolpropane
     trimethacrylate copolymer 464896-73-9P, Cyclohexyl
     methacrylate-glycidyl methacrylate-isobornyl methacrylate-methacrylic
    acid-pentaerythritol tetraacrylate-trimethylolpropane trimethacrylate
     copolymer 464896-74-0P, Glycidyl methacrylate-isobornyl
     methacrylate-methacrylic acid-methyl methacrylate-styrene-pentaerythritol
     tetraacrylate-trimethylolpropane trimethacrylate copolymer
     RL: PNU (Preparation, unclassified); TEM (Technical or engineered material
     use); PREP (Preparation); USES (Uses)
        (cured solder resist; flame retardant photosolder
        resist compn. for manufg. printed circuit board)
     428505-58-2P, Cyclohexyl methacrylate-glycidyl methacrylate-isobornyl
IT
     methacrylate-methacrylic acid copolymer 464891-69-8P, Glycidyl
     methacrylate-isobornyl methacrylate-methacrylic acid-methyl methacrylate
               464891-70-1P, Glycidyl methacrylate-isobornyl
     methacrylate-methacrylic acid-methyl methacrylate copolymer triethylamine
            464896-72-8P, Glycidyl methacrylate-isobornyl methacrylate-
     methacrylic acid-methyl methacrylate-styrene copolymer
     RL: SPN (Synthetic preparation); TEM (Technical or engineered material
     use); PREP (Preparation); USES (Uses)
        (flame retardant photosolder resist compn. for manufg.
        printed circuit board)
                                     4986-89-4, Pentaerythritol tetraacrylate
     147-14-8, Phthalocyanine blue
IT
     15625-89-5, Trimethylolpropanetriacrylate
     RL: TEM (Technical or engineered material use); USES (Uses)
        (flame retardant photosolder resist compn. for manufg.
        printed circuit board)
                              25035-72-7, Epostar M30
                                                        26160-89-4, Epostar MS
     9003-08-1, Epostar S12
IT
     RL: TEM (Technical or engineered material use); USES (Uses)
        (flame retardant; flame retardant photosolder resist compn.
        for manufg. printed circuit board)
                              100752-97-4, Diethylthioxanthone
IT
     71868-10-5, Irgacure 907
     RL: CAT (Catalyst use); USES (Uses)
```

(photopolymn. initiator; flame retardant photosolder resist compn. for manufg. printed circuit board)

L12 ANSWER 8 OF 34 CAPLUS COPYRIGHT 2003 ACS on STN

ACCESSION NUMBER: 2002:748363 CAPLUS

DOCUMENT NUMBER: 137:286359

TITLE: Alkaline-developable photosolder resist

composition and cured solder resist coating

APPLICATION NO. DATE

for printed circuit board

INVENTOR(S): Yabuuchi, Naoya; Fujita, Minoru; Nanba, Osamu;

Okajima, Keiichi

PATENT ASSIGNEE(S): Nippon Paint Co., Ltd., Japan Jpn. Kokai Tokkyo Koho, 9 pp. SOURCE:

KIND DATE

CODEN: JKXXAF

DOCUMENT TYPE: Patent LANGUAGE: Japanese

FAMILY ACC. NUM. COUNT: 1

PATENT INFORMATION:

PATENT NO.

JP 2002287356 A2 20021003 JP 2001-92197 JP 2001-92197 -----JP 2001-92197 20010328 PRIORITY APPLN. INFO.: 20010328 The invention relates to a photosolder resist compn. comprising (A) a resin comprised of isobornyl (meth)acrylate, (meth)acrylic acid, and glycidyl methacrylate, (B) an inorg. filler, and (C) a photocurable mixt. comprised of a polyfunctional acrylic monomer, a cycloether-contq. compd., an amino group-contg. polymerizable compd., and a photopolymn. initiator. The photosolder resist compn. may contain pigments. The photosolder resist compn. is coated on a substrate, dried at 50-90.degree., exposed pattenwisely to an actinic ray, developed with an alk. developer, and baked at 140-170.degree. to obtain the cured solder resist coating. The photosolder resist compn. shows excellent photosensitivity, developability, solder heat-resistance, gold plating-resistance, thermal shock-resistance, and elec. insulating property.

IT 464896-50-2P, Glycidyl methacrylate-isobornyl methacrylatemethacrylic acid-methyl methacrylate-Pentaerythritol tetraacrylate-Trimethylolpropane triacrylate-dimethylaminopropylmethacrylamide copolymer 464896-51-3P, lN, N-Bis[3-(methacryloyloxy)-2hydroxypropyl]isopropylamine-Glycidyl methacrylate-isobornyl methacrylate-methacrylic acid-methyl methacrylate-Pentaerythritol tetraacrylate-Trimethylolpropane triacrylate copolymer 464896-52-4P 464896-53-5P 464896-54-6P 464896-55-7P

RL: PNU (Preparation, unclassified); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

(cured solder resist; alk.-developable photosolder resist compn. for manufg. printed circuit board)

464896-50-2 CAPLUS RN

CN2-Propenoic acid, 2-methyl-, polymer with 2,2-bis[[(1-oxo-2propenyl)oxy]methyl]-1,3-propanediyl di-2-propenoate, N-

#### Page 33Lee507

[(dimethylamino)propyl]-2-methyl-2-propenamide, 2-ethyl-2-[[(1-oxo-2-propenyl)oxy]methyl]-1,3-propanediyl di-2-propenoate, methyl 2-methyl-2-propenoate and rel-(1R,2R,4R)-1,7,7-trimethylbicyclo[2.2.1]hept-2-yl 2-methyl-2-propenoate (9CI) (CA INDEX NAME)

CM 1

CRN 67296-21-3 CMF C9 H18 N2 O CCI IDS

CM 2

CRN 15625-89-5 CMF C15 H20 O6

CM 3

CRN 7534-94-3 CMF C14 H22 O2

Relative stereochemistry.

#### Page 34Lee507

CM 4

CRN 4986-89-4 CMF C17 H20 O8

CM 5

CRN 106-91-2 CMF C7 H10 O3

$$\begin{tabular}{c|c} O & O & CH_2 \\ \hline & & \parallel & \parallel \\ CH_2-O-C-C-Me \\ \hline \end{tabular}$$

CM 6

CRN 80-62-6 CMF C5 H8 O2

Page 35Lee507

CM 7

CRN 79-41-4 CMF C4 H6 O2

RN 464896-51-3 CAPLUS

CN 2-Propenoic acid, 2-methyl-, polymer with 2,2-bis[[(1-oxo-2-propenyl)oxy]methyl]-1,3-propanediyl di-2-propenoate, 2-ethyl-2-[[(1-oxo-2-propenyl)oxy]methyl]-1,3-propanediyl di-2-propenoate, [(1-methylethyl)imino]bis(2-hydroxy-3,1-propanediyl) bis(2-methyl-2-propenoate), methyl 2-methyl-2-propenoate, oxiranylmethyl 2-methyl-2-propenoate and rel-(1R,2R,4R)-1,7,7-trimethylbicyclo[2.2.1]hept-2-yl 2-methyl-2-propenoate (9CI) (CA INDEX NAME)

CM 1

CRN 36196-68-6 CMF C17 H29 N O6

CM 2

CRN 15625-89-5 CMF C15 H20 O6

CM 3

CRN 7534-94-3 CMF C14 H22 O2

# Page 36Lee507

Relative stereochemistry.

CM 4

CRN 4986-89-4 CMF C17 H20 O8

CM 5

CRN 106-91-2 CMF C7 H10 O3

CM 6

CRN 80-62-6 CMF C5 H8 O2

$$\begin{array}{c|c} ^{H_2C} & \text{O} \\ \parallel & \parallel \\ \text{Me-} & \text{C-} & \text{C-} & \text{OMe} \end{array}$$

CM 7

CRN 79-41-4 CMF C4 H6 O2

$$^{\mathrm{CH_2}}_{\parallel}$$
 Me-C-CO<sub>2</sub>H

RN 464896-52-4 CAPLUS

CN 2-Propenoic acid, 2-methyl-, polymer with 2,2-bis[[(1-oxo-2-propenyl)oxy]methyl]-1,3-propanediyl di-2-propenoate, 2-ethyl-2-[[(1-oxo-2-propenyl)oxy]methyl]-1,3-propanediyl di-2-propenoate, 1,6-hexanediylbis[nitrilobis(2-hydroxy-3,1-propanediyl)] tetrakis(2-methyl-2-propenoate), methyl 2-methyl-2-propenoate, oxiranylmethyl 2-methyl-2-propenoate and rel-(1R,2R,4R)-1,7,7-trimethylbicyclo[2.2.1]hept-2-yl 2-methyl-2-propenoate (9CI) (CA INDEX NAME)

CM 1

CRN 83372-16-1 CMF C34 H56 N2 O12

CM 2

CRN 15625-89-5 CMF C15 H20 O6

# Page 38Lee507

CM 3

CRN 7534-94-3 CMF C14 H22 O2

Relative stereochemistry.

CM 4

CRN 4986-89-4 CMF C17 H20 O8

CM 5

CRN 106-91-2 CMF C7 H10 O3 Page 39Lee507

CM 6

CRN 80-62-6 CMF C5 H8 O2

CM 7

79-41-4 CRN CMF C4 H6 O2

RN

464896-53-5 CAPLUS 2-Propenoic acid, 2-methyl-, polymer with 2,2-bis[[(1-oxo-2-CNpropenyl)oxy]methyl]-1,3-propanediyl di-2-propenoate, N-[(dimethylamino)propyl]-2-methyl-2-propenamide, 2-ethyl-2-[[(1-oxo-2propenyl)oxy]methyl]-1,3-propanediyl di-2-propenoate, methyl 2-methyl-2-propenoate, oxiranylmethyl 2-methyl-2-propenoate and

rel-(1R,2R,4R)-1,7,7-trimethylbicyclo[2.2.1]hept-2-yl 2-methyl-2propenoate, compd. with N,N-diethylethanamine (9CI) (CA INDEX NAME)

CM 1

CRN 121-44-8 CMF C6 H15 N

CM 2

### Page 40Lee507

CRN 464896-50-2

CMF (C17 H20 O8 . C15 H20 O6 . C14 H22 O2 . C9 H18 N2 O . C7 H10 O3 . C5 H8 O2 . C4 H6 O2)  $\times$ 

CCI PMS

CM 3

CRN 67296-21-3 CMF C9 H18 N2 O CCI IDS

CM 4

CRN 15625-89-5 CMF C15 H20 O6

CM 5

CRN 7534-94-3 CMF C14 H22 O2

Relative stereochemistry.

Page 41Lee507

CM 6

CRN 4986-89-4 CMF C17 H20 O8

CM 7

CRN 106-91-2 CMF C7 H10 O3

CM 8

CRN 80-62-6 CMF C5 H8 O2

CM 9

CRN 79-41-4 CMF C4 H6 O2

RN 464896-54-6 CAPLUS

2-Propenoic acid, 2-methyl-, polymer with 2,2-bis[[(1-oxo-2-propenyl)oxy]methyl]-1,3-propanediyl di-2-propenoate, 2-ethyl-2-[[(1-oxo-2-propenyl)oxy]methyl]-1,3-propanediyl di-2-propenoate, [(1-methylethyl)imino]bis(2-hydroxy-3,1-propanediyl) bis(2-methyl-2-propenoate), methyl 2-methyl-2-propenoate, oxiranylmethyl 2-methyl-2-propenoate and rel-(1R,2R,4R)-1,7,7-trimethylbicyclo[2.2.1]hept-2-yl 2-methyl-2-propenoate, compd. with N,N-diethylethanamine (9CI) (CA INDEX NAME)

CM 1

CRN 121-44-8 CMF C6 H15 N

CM 2

CRN 464896-51-3

CMF (C17 H29 N O6 . C17 H20 O8 . C15 H20 O6 . C14 H22 O2 . C7 H10 O3 . C5 H8 O2 . C4 H6 O2)  $\times$ 

CCI PMS

CM 3

CRN 36196-68-6 CMF C17 H29 N O6

# Page 43Lee507

CM 4

CRN 15625-89-5 CMF C15 H20 O6

CM 5

CRN 7534-94-3 CMF C14 H22 O2

Relative stereochemistry.

CM 6

CRN 4986-89-4 CMF C17 H20 O8

CM 7

#### Page 44Lee507

CRN 106-91-2 CMF C7 H10 O3

$$\begin{array}{c|c} \circ & \circ & \mathsf{CH}_2 \\ & \parallel & \parallel \\ \mathsf{CH}_2 - \mathsf{O} - \mathsf{C} - \mathsf{C} - \mathsf{Me} \end{array}$$

CM 8

CRN 80-62-6 CMF C5 H8 O2

$$\begin{array}{c|c} ^{H_2C} & \text{O} \\ \parallel & \parallel \\ \text{Me-} & \text{C-} & \text{C-} & \text{OMe} \end{array}$$

CM 9

CRN 79-41-4 CMF C4 H6 O2

$$\begin{array}{c} \text{CH}_2 \\ \parallel \\ \text{Me-C-CO}_2 \text{H} \end{array}$$

CN

RN 464896-55-7 CAPLUS

2-Propenoic acid, 2-methyl-, polymer with 2,2-bis[[(1-oxo-2-propenyl)oxy]methyl]-1,3-propanediyl di-2-propenoate, 2-ethyl-2-[[(1-oxo-2-propenyl)oxy]methyl]-1,3-propanediyl di-2-propenoate, 1,6-hexanediylbis[nitrilobis(2-hydroxy-3,1-propanediyl)] tetrakis(2-methyl-2-propenoate), methyl 2-methyl-2-propenoate, oxiranylmethyl 2-methyl-2-propenoate and rel-(1R,2R,4R)-1,7,7-trimethylbicyclo[2.2.1]hept-2-yl 2-methyl-2-propenoate, compd. with N,N-diethylethanamine (9CI) (CA INDEX NAME)

CM 1

CRN 121-44-8 CMF C6 H15 N Page 45Lee507

CM 2

CRN 464896-52-4

CMF (C34 H56 N2 O12 . C17 H20 O8 . C15 H20 O6 . C14 H22 O2 . C7 H10 O3 . C5 H8 O2 . C4 H6 O2)  $\times$ 

CCI PMS

CM 3

CRN 83372-16-1 CMF C34 H56 N2 O12

CM 4

CRN 15625-89-5 CMF C15 H20 O6

CM 5

CRN 7534-94-3

# Page 46Lee507

CMF C14 H22 O2

Relative stereochemistry.

CM 6

CRN 4986-89-4 CMF C17 H20 O8

$$\begin{array}{c} \text{O} & \text{CH}_2\text{--}\text{O}-\text{CH} = \text{CH}_2 \\ \text{H}_2\text{C} = \text{CH}-\text{C}-\text{O}-\text{CH}_2-\text{C}-\text{CH}_2-\text{O}-\text{C}-\text{CH} = \text{CH}_2 \\ \text{H}_2\text{C} = \text{CH}-\text{C}-\text{O}-\text{CH}_2 & \text{O} \\ \text{H}_2\text{C} = \text{CH}-\text{C}-\text{O}-\text{CH}_2 & \text{O} \\ \text{O} \end{array}$$

CM 7

CRN 106-91-2 CMF C7 H10 O3

CM 8

CRN 80-62-6 CMF C5 H8 O2

CM 9

CRN 79-41-4 CMF C4 H6 O2

IC ICM G03F007-038 ICS C08G059-46; H05K003-28

CC 74-3 (Radiation Chemistry, Photochemistry, and Photographic and Other Reprographic Processes)
Section cross-reference(s): 38, 76

ST photosolder resist compn photoresist solder printed circuit board

IT Printed circuit boards

(alk.-developable photosolder resist compn. and cured solder resist coating for printed circuit board)

IT Solder resists

(photoresists; alk.-developable photosolder resist compn. and cured solder resist coating for printed circuit board)

IT Photoresists

(solder; alk.-developable photosolder resist compn. and cured solder resist coating for printed circuit board)

IT 7727-43-7, B 34

RL: TEM (Technical or engineered material use); USES (Uses)
(B 34; alk.-developable photosolder resist compn. for manufg. printed circuit board)

IT 244772-00-7, EHPE 3150

RL: TEM (Technical or engineered material use); USES (Uses) (EHPE 3150; alk.-developable photosolder resist compn. for manufg. printed circuit board)

IT 464891-69-8P, Glycidyl methacrylate-isobornyl methacrylate-methacrylic acid-methyl methacrylate copolymer 464891-70-1P, Glycidyl methacrylate-isobornyl methacrylate-methacrylic acid-methyl methacrylate copolymer triethylamine salt

RL: SPN (Synthetic preparation); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

(alk.-developable photosolder resist compn. for manufg. printed circuit board)

IT 147-14-8, Phthalocyanine blue 4986-89-4, Pentaerythritol tetraacrylate 15625-89-5, Trimethylolpropanetriacrylate 36196-68-6 67296-21-3,

```
Dimethylaminopropylmethacrylamide
                                         83372-16-1
     RL: TEM (Technical or engineered material use); USES (Uses)
         (alk.-developable photosolder resist compn. for manufg.
        printed circuit board)
ΙT
     464896-50-2P, Glycidyl methacrylate-isobornyl methacrylate-
     methacrylic acid-methyl methacrylate-Pentaerythritol tetraacrylate-
     Trimethylolpropane triacrylate-dimethylaminopropylmethacrylamide copolymer
     464896-51-3P, lN, N-Bis[3-(methacryloyloxy)-2-
     hydroxypropyl]isopropylamine-Glycidyl methacrylate-isobornyl
     methacrylate-methacrylic acid-methyl methacrylate-Pentaerythritol
     tetraacrylate-Trimethylolpropane triacrylate copolymer
     464896-52-4P 464896-53-5P 464896-54-6P
     464896-55-7P
     RL: PNU (Preparation, unclassified); TEM (Technical or engineered material
     use); PREP (Preparation); USES (Uses)
        (cured solder resist; alk.-developable photosolder
        resist compn. for manufg. printed circuit board)
IT
     71868-10-5, Irgacure 907
                               100752-97-4, Diethylthioxanthone
     RL: CAT (Catalyst use); USES (Uses)
        (photopolymn. initiator; alk.-developable photosolder resist
        compn. for manufg. printed circuit board)
L12 ANSWER 9 OF 34 CAPLUS COPYRIGHT 2003 ACS on STN
ACCESSION NUMBER:
                       2002:748362 CAPLUS
DOCUMENT NUMBER:
                       137:286439
TITLE:
                        Water-soluble photosolder resist composition
                        and cured solder resist coating for printed
                        circuit board
INVENTOR (S):
                        Yabuuchi, Naoya; Fujita, Minoru; Nanba, Osamu;
                        Okajima, Keiichi
PATENT ASSIGNEE(S):
                        Nippon Paint Co., Ltd., Japan
SOURCE:
                        Jpn. Kokai Tokkyo Koho, 8 pp.
                        CODEN: JKXXAF
DOCUMENT TYPE:
                        Patent
LANGUAGE:
                        Japanese
FAMILY ACC. NUM. COUNT: 1
PATENT INFORMATION:
    PATENT NO.
                 KIND DATE
    PATENT NO. KIND DATE APPLICATION NO. DATE
                                         -----
    JP 2002287355 A2 20021003
                                      JP 2001-92196
                                                          20010328
PRIORITY APPLN. INFO.:
                                       JP 2001-92196
    The invention relates to a water-sol, photosolder resist compn.
    comprising (A) an reactive amine salt of a resin comprised of isobornyl
    (meth)acrylate, (meth)acrylic acid, and glycidyl methacrylate, (B) an
    inorg. filler, and (C) a photocurable mixt. comprised of a polyfunctional
    acrylic monomer, a cycloether-contg. compd., and a photopolymn. initiator.
    The photosolder resist compn. may contain pigments.
    photosolder resist compn. is coated on a substrate, dried at
    50-90.degree., exposed pattenwisely to an actinic ray, developed with an
    alk. developer, and baked at 140-170.degree. to obtain the cured solder
    resist coating. The photosolder resist compn. shows
```

excellent photosensitivity, developability, solder heat-resistance, gold plating-resistance, thermal shock-resistance, and elec. insulating property and contains reduced amt. of volatile org. compds. 464891-34-7P, Glycidyl methacrylate-isobornyl methacrylate-

methacrylic acid-styrene-pentaerythritol tetraacrylate-trimethylolpropane trimethacrylate copolymer dimethylaminopropyl methacrylamide salt 464891-35-8P, Glycidyl methacrylate-isobornyl methacrylate-methacrylic acid-styrene-pentaerythritol tetraacrylate-trimethylolpropane trimethacrylate copolymer diethylaminoethyl acrylate salt RL: PNU (Preparation, unclassified); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

(cured solder resist; water-sol. photosolder resist compn. for manufg. printed circuit board)

RN 464891-34-7 CAPLUS

2-Propenoic acid, 2-methyl-, polymer with 2,2-bis[[(1-oxo-2-propenyl)oxy]methyl]-1,3-propanediyl di-2-propenoate, ethenylbenzene, 2-ethyl-2-[[(2-methyl-1-oxo-2-propenyl)oxy]methyl]-1,3-propanediyl bis(2-methyl-2-propenoate), oxiranylmethyl 2-methyl-2-propenoate and rel-(1R,2R,4R)-1,7,7-trimethylbicyclo[2.2.1]hept-2-yl 2-methyl-2-propenoate, compd. with N-[3-(dimethylamino)propyl]-2-methyl-2-propenamide (9CI) (CA INDEX NAME)

CM 1

CN

CRN 5205-93-6 CMF C9 H18 N2 O

CM 2

CRN 464891-33-6

CMF (C18 H26 O6 . C17 H20 O8 . C14 H22 O2 . C8 H8 . C7 H10 O3 . C4 H6 O2)  $\times$ 

CCI PMS

CM 3

CRN 7534-94-3 CMF C14 H22 O2

Relative stereochemistry.

### Page 50Lee507

CM 4

CRN 4986-89-4 CMF C17 H20 O8

$$\begin{array}{c} O & CH_2-O-CCH-CH_2\\ || & || \\ H_2C-CH-C-O-CH_2-C-CH_2-O-C-CH-CH_2\\ || & || \\ H_2C-CH-C-O-CH_2\\ || & || \\ O \end{array}$$

CM 5

CRN 3290-92-4 CMF C18 H26 O6

CM 6

CRN 106-91-2 CMF C7 H10 O3 Page 51Lee507

CM 7

CRN 100-42-5 CMF C8 H8

 $H_2C = CH - Ph$ 

CM 8

CRN 79-41-4 CMF C4 H6 O2

$$\begin{array}{c} \text{CH}_2 \\ \parallel \\ \text{Me-C-CO}_2\text{H} \end{array}$$

RN 464891-35-8 CAPLUS

2-Propenoic acid, 2-methyl-, polymer with 2,2-bis[[(1-oxo-2-propenyl)oxy]methyl]-1,3-propanediyl di-2-propenoate, ethenylbenzene, 2-ethyl-2-[[(2-methyl-1-oxo-2-propenyl)oxy]methyl]-1,3-propanediyl bis(2-methyl-2-propenoate), oxiranylmethyl 2-methyl-2-propenoate and rel-(1R,2R,4R)-1,7,7-trimethylbicyclo[2.2.1]hept-2-yl 2-methyl-2-propenoate, compd. with 2-(diethylamino)ethyl 2-propenoate (9CI) (CA INDEX NAME)

CM 1

CRN 2426-54-2 CMF C9 H17 N O2

$$\begin{array}{c} \text{O} \\ \parallel \\ \text{Et}_2 \text{N} - \text{CH}_2 - \text{CH}_2 - \text{O} - \text{C} - \text{CH} \longrightarrow \text{CH}_2 \end{array}$$

CM 2

CRN 464891-33-6

#### Page 52Lee507

CMF (C18 H26 O6 . C17 H20 O8 . C14 H22 O2 . C8 H8 . C7 H10 O3 . C4 H6 O2)x

CCI PMS

CM 3

CRN 7534-94-3 CMF C14 H22 O2

# Relative stereochemistry.

CM 4

CRN 4986-89-4 CMF C17 H20 O8

$$\begin{array}{c} O & CH_2-O-C-CH \longrightarrow CH_2 \\ H_2C \longrightarrow CH-C-O-CH_2-C-CH_2-O-C-CH \longrightarrow CH_2 \\ H_2C \longrightarrow CH-C-O-CH_2 & O \\ & & & & & & & \\ & & & & & \\ & & & & & \\ & & & & & \\ & & & & & \\ & & & & & \\ & & & & & \\ & & & & & \\ & & & & & \\ & & & & & \\ & & & & & \\ & & & & \\ & & & & & \\ & & & & \\ & & & & \\ & & & & \\ & & & & \\ & & & & \\ & & & & \\ & & & \\ & & & & \\ & & \\ & & & \\ & & \\ & & & \\ & & \\ & & & \\ & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ &$$

CM 5

CRN 3290-92-4 CMF C18 H26 O6

CM

CRN 106-91-2 CMF C7 H10 O3

CM 7

CRN 100-42-5 CMF C8 H8

 $H_2C = CH - Ph$ 

CM 8

CRN 79-41-4 CMF C4 H6 O2

$$\begin{array}{c} \text{CH}_2 \\ || \\ \text{Me-C-CO}_2 \text{H} \end{array}$$

IC ICM G03F007-038

ICS C08G059-42; C08K003-00; C08K005-103; C08L063-00; G03F007-004

74-5 (Radiation Chemistry, Photochemistry, and Photographic and Other CC Reprographic Processes) Section cross-reference(s): 38, 76

water soluble photosolder resist compn printed circuit board ST

IT

(photoresists; water-sol. photosolder resist compn. and cured solder resist coating for printed circuit board)

IT Photoresists

> (solder; water-sol. photosolder resist compn. and cured solder resist coating for printed circuit board)

ΙT Printed circuit boards

(water-sol. photosolder resist compn. and cured solder resist coating for printed circuit board)

IT 7727-43-7, B 34

RL: TEM (Technical or engineered material use); USES (Uses)

```
(B 34; water-sol. photosolder resist compn. for manufg.
         printed circuit board)
 IT
      244772-00-7, EHPE 3150
      RL: TEM (Technical or engineered material use); USES (Uses)
         (EHPE 3150; water-sol. photosolder resist compn. for manufg.
         printed circuit board)
      464891-34-7P, Glycidyl methacrylate-isobornyl methacrylate-
 TТ
      methacrylic acid-styrene-pentaerythritol tetraacrylate-trimethylolpropane
      trimethacrylate copolymer dimethylaminopropyl methacrylamide salt
      464891-35-8P, Glycidyl methacrylate-isobornyl methacrylate-
     methacrylic acid-styrene-pentaerythritol tetraacrylate-trimethylolpropane
     trimethacrylate copolymer diethylaminoethyl acrylate salt
     RL: PNU (Preparation, unclassified); TEM (Technical or engineered material
      use); PREP (Preparation); USES (Uses)
         (cured solder resist; water-sol. photosolder resist
         compn. for manufg. printed circuit board)
     71868-10-5, Irgacure 907 100752-97-4, Diethylthioxanthone
 IT
     RL: CAT (Catalyst use); USES (Uses)
         (photopolymn. initiator; water-sol. photosolder resist compn.
         for manufg. printed circuit board)
     464891-30-3P, Glycidyl methacrylate-isobornyl methacrylate-methacrylic
ΙT
     acid-styrene copolymer
                              464891-31-4P 464891-32-5P, Glycidyl
     methacrylate-isobornyl methacrylate-methacrylic acid-styrene copolymer
     (diethylamino)ethyl acrylate salt
     RL: SPN (Synthetic preparation); TEM (Technical or engineered material
     use); PREP (Preparation); USES (Uses)
         (water-sol. photosolder resist compn. for manufg. printed
        circuit board)
     147-14-8, Phthalocyanine blue 4986-89-4, Pentaerythritol tetraacrylate
ΙT
     15625-89-5, Trimethylolpropanetriacrylate
     RL: TEM (Technical or engineered material use); USES (Uses)
        (water-sol. photosolder resist compn. for manufg. printed
        circuit board)
L12 ANSWER 10 OF 34 CAPLUS COPYRIGHT 2003 ACS on STN
ACCESSION NUMBER: 2002:688185 CAPLUS
DOCUMENT NUMBER:
                        137:218079
TITLE:
                        Radiation-curable epoxy resin compositions with good
                        storage stability at high temperatures
INVENTOR(S):
                       Hagiwara, Tsuneo
PATENT ASSIGNEE(S): Ragiward, Tsuneo

Patent Assignee(S): Teijin Seiki Co., Ltd., Japan
SOURCE:
                         Jpn. Kokai Tokkyo Koho, 13 pp.
                         CODEN: JKXXAF
DOCUMENT TYPE:
                        Patent
LANGUAGE:
                         Japanese
FAMILY ACC. NUM. COUNT: 1
PATENT INFORMATION:
     PATENT NO. KIND DATE
     PATENT NO. KIND DATE
                                        APPLICATION NO. DATE
    JP 2002256062 A2 20020911 JP 2001-56834 20010301
PTTV APPIN INFO.: JP 2001-56834 20010301
PRIORITY APPLN. INFO.:
```

The compns., useful for stereophotolithog., contain cationically AB polymerizable compds. contg. G-CH2(OCHR2CH2)mOC6H4CR12C6H4O(CH2HR3O)nCH2G (R1-R3 = H, Me; G = glycidyl; m, n = 1-15), radically polymerizable org. compds., radiation-sensitive cationic initiators, and radiation-sensitive radical initiators. Thus, a compn. contg. 3300 parts mixt. comprising 3,4-epoxycyclohexylmethyl-3,4-epoxycyclohexanecarboxylate 1570, Rikaresin HBE 100 [bisphenol A bis(propylene glycol glycidyl ether) ether] 300, Rikaresin HBE 100 (hydrogenated bisphenol A diglycidyl ether) 200, NK Ester A-BPE 4 [2,2-bis[4-(acryloxydiethoxy)phenyl]propane] 500, ATM 4P (propoxylated trimethylolpropane) 400, A-DCP (dicyclopentadienyl diacrylate) 400, and 3-methyl-3-hydroxymethyloxetane 30 parts, Irgacure 104 (1-hydroxycyclohexyl Ph ketone) 45, and bis[4-(diphenylsulfonio)phenyl]sulfidobishexafluoroantimonate 60 parts showed no apparent viscosity increase at 80.degree. for 17 days.

IT 455935-80-5P

RL: IMF (Industrial manufacture); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

(radiation-curable epoxy resin photolithog. compns. with good storage stability at high temps.)

RN 455935-80-5 CAPLUS

7-Oxabicyclo[4.1.0]heptane-3-carboxylic acid, 7-oxabicyclo[4.1.0]hept-3ylmethyl ester, polymer with 2,2'-[1,4-butanediylbis(oxymethylene)]bis[oxi rane], .alpha.,.alpha.'-[(1-methylethylidene)di-4,1-phenylene]bis[.omega.-(oxiranylmethoxy)poly[oxy(methyl-1,2-ethanediyl)]], 3-methyl-3oxetanemethanol, octahydro-4,7-methano-1H-indene-5,?-diyl di-2-propenoate and 2-[[3-[(1-oxo-2-propenyl)oxy]-2,2-bis[[(1-oxo-2propenyl)oxy]methyl]propoxy]methyl]-2-[[(1-oxo-2-propenyl)oxy]methyl]-1,3propanediyl di-2-propenoate (9CI) (CA INDEX NAME)

CM 1

CN

CRN 91433-85-1 CMF C16 H20 O4 CCI IDS

CM 2

### Page 56Lee507

CRN 55236-42-5 CMF (C3 H6 O)n (C3 H6 O)n C21 H24 O4 CCI IDS, PMS

PAGE 1-A

$$CH_2-O$$
  $CH_2-O$   $CH_3H_6)-O$   $n$   $Me$   $Me$   $O$ 

PAGE 1-B

CM 3

CRN 29570-58-9 CMF C28 H34 O13

CM 4

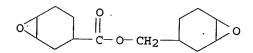
CRN 3143-02-0 CMF C5 H10 O2 Page 57Lee507

CM 5

CRN 2425-79-8 CMF C10 H18 O4

CM 6

CRN 2386-87-0 CMF C14 H20 O4



IC ICM C08G059-68

ICS G03C003-00

CC 38-3 (Plastics Fabrication and Uses)
Section cross-reference(s): 37, 74

ST radiation curable acrylic polyoxyalkylene epoxy resin; stereophotolithog radiation curable epoxy resin storage stability

IT Polyoxyalkylenes, uses

RL: IMF (Industrial manufacture); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

(acrylic-epoxy; radiation-curable epoxy resin **photolithog**. compns. with good storage stability at high temps.)

IT Epoxy resins, uses

RL: IMF (Industrial manufacture); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

(acrylic-polyoxyalkylene-; radiation-curable epoxy resin photolithog. compns. with good storage stability at high temps.)

IT Photolithography

Stereolithography

(stereophotolithog.; radiation-curable epoxy resin photolithog. compns. with good storage stability at high temps.)

IT 455935-79-2P 455935-80-5P 457067-79-7P

RL: IMF (Industrial manufacture); TEM (Technical or engineered material

use); PREP (Preparation); USES (Uses) (radiation-curable epoxy resin photolithog. compns. with good storage stability at high temps.)

L12 ANSWER 11 OF 34 CAPLUS COPYRIGHT 2003 ACS on STN

ACCESSION NUMBER:

2002:606427 CAPLUS

DOCUMENT NUMBER:

137:177099

TITLE:

Curable resins and their compositions for alkali-developable solder resists with good

dielectric properties

INVENTOR(S):

Takagi, Toru; Otani, Kazuo

PATENT ASSIGNEE(S):

Showa Highpolymer Co., Ltd., Japan

SOURCE:

Jpn. Kokai Tokkyo Koho, 7 pp.

CODEN: JKXXAF

DOCUMENT TYPE:

Patent

LANGUAGE:

Japanese

FAMILY ACC. NUM. COUNT: 1

PATENT INFORMATION:

PATENT NO. KIND DATE APPLICATION NO. DATE --------------JP 2002226560 A2 20020814 JP 2001-22894 20010131 PRIORITY APPLN. INFO.: JP 2001-22894 20010131

The resins are manufd. by reacting (A) (un)satd. polybasic anhydride and (B) reaction products prepd. from epoxy-contg. ethylenically unsatd. compds. and phenol-modified polybutadiene or polymers of phenols and dicyclopentadiene. The compns. may contain photoinitiators.

446294-08-2P, DPP-M ester with glycidyl methacrylate and IT tetrahydrophthalic anhydride, polymer with Light Acrylate TMP-A and 1,3,5-triglycidylisocyanurate

RL: IMF (Industrial manufacture); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

(alkali-developable permanent solder resists having phenol-contg. polymers and epoxy resins with good dielec. properties)

RN 446294-08-2 CAPLUS CN

2-Propenoic acid, 2-ethyl-2-[[(1-oxo-2-propenyl)oxy]methyl]-1,3propanediyl ester, polymer with (chloromethyl)oxirane polymer with phenol and 3a,4,7,7a-tetrahydro-4,7-methano-1H-indene hydrogen 4-cyclohexene-1,2-dicarboxylate 2-hydroxy-3-[(2-methyl-1-oxo-2propenyl)oxy]propyl ester, and 1,3,5-tris(oxiranylmethyl)-1,3,5-triazine-2,4,6(1H,3H,5H)-trione (9CI) (CA INDEX NAME)

CM 1

CRN 15625-89-5 CMF C15 H20 O6 Page 59Lee507

CM 2

CRN 2451-62-9 CMF C12 H15 N3 O6

$$CH_2$$
 $N$ 
 $CH_2$ 
 $CH_2$ 
 $CH_2$ 

CM 3

CRN 446294-05-9

CMF (C10 H12 . C6 H6 O . C3 H5 Cl O)x . x C8 H10 O4 . x C7 H12 O4

CM 4

CRN 5919-74-4 CMF C7 H12 O4

CM 5

CRN 88-98-2 CMF C8 H10 O4 Page 60Lee507

CM 6

CRN 30420-32-7

CMF (C10 H12 . C6 H6 O . C3 H5 Cl O) x

CCI PMS

CM 7

CRN 108-95-2 CMF C6 H6 O

CM 8

CRN 106-89-8 CMF C3 H5 Cl O

CM 9

CRN 77-73-6 CMF C10 H12

IC ICM C08G061-02 ICS C08G059-42

KOROMA EIC1700

CC 74-5 (Radiation Chemistry, Photochemistry, and Photographic and Other Reprographic Processes) Section cross-reference(s): 38, 76

ST solder resist phenolic polybutadiene epoxy dielec; permanent photoresist alkali developable acrylic epoxy dicyclopentadiene

IT Phenolic resins, preparation

RL: IMF (Industrial manufacture); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

(acrylic-epoxy; alkali-developable permanent solder resists having phenol-contg. polymers and epoxy resins with good dielec. properties)

IT Epoxy resins, preparation

RL: IMF (Industrial manufacture); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

(acrylic-phenolic; alkali-developable permanent solder resists having phenol-contg. polymers and epoxy resins with good dielec. properties)

IT Electric insulators

(alkali-developable permanent solder resists having phenol-contg. polymers and epoxy resins with good dielec. properties)

IT Solder resists

(photoresists; alkali-developable permanent solder resists having phenol-contg. polymers and epoxy resins with good dielec. properties)

IT Photoresists

(solder; alkali-developable permanent solder resists having phenol-contg. polymers and epoxy resins with good dielec. properties)

77-73-6DP, Dicyclopentadiene, epoxy resins, polymers with phenol-modified IΤ polybutadiene ester with glycidyl methacrylate and tetrahydrophthalic 9003-17-2DP, Polybutadiene, reaction products with phenols, glycidyl methacrylate, tetrahydrophthalic anhydride, polymer with epoxy 446294-04-8P, PP 700-300 ester with glycidyl methacrylate and resins tetrahydrophthalic anhydride, polymer with HP 7200H 446294-06-0P, DPP-M ester with glycidyl methacrylate and tetrahydrophthalic anhydride, polymer 446294-07-1P, PP 700-300 ester with glycidyl methacrylate with HP 7200H and tetrahydrophthalic anhydride, polymer with Light Acrylate TMP-A and 1,3,5-triglycidyl isocyanurate 446294-08-2P, DPP-M ester with glycidyl methacrylate and tetrahydrophthalic anhydride, polymer with Light Acrylate TMP-A and 1,3,5-triglycidylisocyanurate RL: IMF (Industrial manufacture); TEM (Technical or engineered material

use); PREP (Preparation); USES (Uses)
(alkali-developable permanent solder resists having

(alkali-developable permanent solder resists having phenol-contg. polymers and epoxy resins with good dielec. properties)

L12 ANSWER 12 OF 34 CAPLUS COPYRIGHT 2003 ACS on STN

ACCESSION NUMBER: DOCUMENT NUMBER: 2002:129153 CAPLUS

TITLE:

136:191690 Acrylic photoresist polymers bearing

cyclotetrasiloxanyl groups, their preparation,

composition, and photolithography thereof

INVENTOR (S):

Lee, Geun Su; Koh, Cha Won; Jung, Jae Chang; Jung, Min

Ho; Baik, Ki Ho

#### Page 62Lee507

PATENT ASSIGNEE(S):

Hynix Semiconductor Co., Ltd., S. Korea

SOURCE:

Jpn. Kokai Tokkyo Koho, 22 pp.

DOCUMENT TYPE:

CODEN: JKXXAF

LANGUAGE:

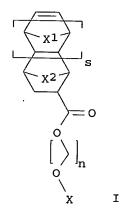
Patent

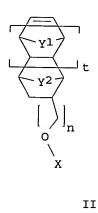
Japanese

FAMILY ACC. NUM. COUNT:

PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
JP 2002053623 US 2002028406 US 6569599	A2 A1 B2	20020219 20020307 20030527	JP 2001-188341 US 2001-852371	20010621 20010510
PRIORITY APPLN. INFO.	:		KR 2000-34102 A	20000621





The polymers with mol. wt. 3000-50,000 are prepd. by polymn. of (i) AΒ monomers represented by R5C(:CH2)CO2(CH2)nOX [R1-4 (in X definition) = H, C1-10 alkyl; R5 = H, Me], I (X1, X2 = CH2, CH2CH2; s = 0, 1, 2), and/or II (Y1, Y2 = CH2, CH2CH2; t = 0, 1, 2), (ii) R6C(:CH2)(CH2)mCO2R7 (R6 = H, CH2)mCO2R7)Me; R7 = acid-labile protective group; m = 0.5 integer), and (iii) (meth)acrylic acid and may contain crosslinking agents R9C(:CH2)CO2CR11R12YCR13R14OCOC(:CH2)R10 and/or maleic anhydride. polymers are prepd. by catalyst-assisted polymn. Chem.-amplified pos. photoresists comprising the polymers are also claimed. A bilayer resist process employing the photoresists and underlayers which are chosen from bottom antireflective coatings or i- or g-line photosensitizer coatings, is further claimed. The photoresists keep pattern sharpness during plasma etching for the underlayer patterning. 399557-23-4P 399557-24-5P IT

RL: IMF (Industrial manufacture); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

(Si-rich acrylic polymers bearing acid-labile cyclosiloxanyl groups for photoresists with superior etching resistance)

RN 399557-23-4 CAPLUS CN Bicyclo[2.2.1]hept-5-ene-2-carboxylic acid, 2-[(1,3,5,7-tetramethyl-1,3,5,7-tetrasilacyclooct-1-yl)oxy]ethyl ester, polymer with 1,1-dimethylethyl 2-methyl-2-propenoate, 2,5-furandione, 2-methyl-2-propenoic acid and 1,1,4,4-tetramethyl-1,4-butanediyl di-2-propenoate (9CI) (CA INDEX NAME)

CM 1

CRN 356043-16-8 CMF C18 H36 O3 Si4

CM 2

CRN 188837-15-2 CMF C14 H22 O4

CM 3

CRN 585-07-9 CMF C8 H14 O2

$$\begin{array}{c|c} & \text{O} & \text{CH}_2 \\ \parallel & \parallel \\ \text{t-BuO-C-C-Me} \end{array}$$

CM 4

Page 64Lee507

CRN 108-31-6 CMF C4 H2 O3

CM 5

CRN 79-41-4 CMF C4 H6 O2

$$\begin{array}{c} \text{CH}_2 \\ \parallel \\ \text{Me-C-CO}_2 \text{H} \end{array}$$

RN 399557-24-5 CAPLUS

CN 2-Propenoic acid, 2-methyl-, polymer with 1-(bicyclo[2.2.1]hept-5-en-2-ylmethoxy)-1,3,5,7-tetramethyl-1,3,5,7-tetrasilacyclooctane,
1,1-dimethylethyl 2-methyl-2-propenoate, 2,5-furandione and
1,1,4,4-tetramethyl-1,4-butanediyl di-2-propenoate (9CI) (CA INDEX NAME)

CM 1

CRN 356043-17-9 CMF C16 H34 O Si4

CM 2

CRN 188837-15-2 CMF C14 H22 O4 Page 65Lee507

CM 3

CRN 585-07-9 CMF C8 H14 O2

CM 4

CRN 108-31-6 CMF C4 H2 O3

CM 5

CRN 79-41-4 CMF C4 H6 O2

IC ICM C08F230-08

ICS C08F220-28; C08K005-00; C08L101-02; G03F007-004; G03F007-039; G03F007-075; G03F007-11; G03F007-26; H01L021-027.

CC 74-5 (Radiation Chemistry, Photochemistry, and Photographic and Other Reprographic Processes)
Section cross-reference(s): 38, 76

ST silicon rich acrylic photoresist cyclosiloxanyl protected; amplified photoresist acrylic cyclosiloxanyl protective group; semiconductor bilayer

Page 66Lee507 resist photolithog acrylic photoresist ΙT Semiconductor device fabrication (Si-rich acrylic polymers bearing acid-labile cyclosiloxanyl groups for photoresists with superior etching resistance) IT Positive photoresists (UV, deep-UV, chem. amplified; Si-rich acrylic polymers bearing acid-labile cyclosiloxanyl groups for photoresists with superior etching resistance) IT Protective groups (acid-labile, cyclotetrasiloxanyl; Si-rich acrylic polymers bearing acid-labile cyclosiloxanyl groups for photoresists with superior etching resistance) Photolithography IT (bilayer resist process; Si-rich acrylic polymers bearing acid-labile cyclosiloxanyl groups for photoresists with superior etching resistance) IT Resists (etching, plasma etching; Si-rich acrylic polymers bearing acid-labile cyclosiloxanyl groups for photoresists with superior etching IT Resists (radiation-sensitive, polymers; Si-rich acrylic polymers bearing acid-labile cyclosiloxanyl groups for photoresists with superior etching resistance) TT 399557-22-3P 399557-23-4P 399557-24-5P RL: IMF (Industrial manufacture); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses) (Si-rich acrylic polymers bearing acid-labile cyclosiloxanyl groups for photoresists with superior etching resistance) IT 356043-15-7P 356043-16-8P 356043-17-9P RL: PNU (Preparation, unclassified); RCT (Reactant); PREP (Preparation); RACT (Reactant or reagent) (Si-rich acrylic polymers bearing acid-labile cyclosiloxanyl groups for photoresists with superior etching resistance) 95-12-5, 5-Norbornene-2-methanol 818-61-1, 2-Hydroxyethyl acrylate 2370-88-9, 2,4,6,8-Tetramethylcyclotetrasiloxane 37503-42-7, 2-Hydroxyethyl 5-norbornene-2-carboxylate RL: RCT (Reactant); RACT (Reactant or reagent) (Si-rich acrylic polymers bearing acid-labile cyclosiloxanyl groups for photoresists with superior etching resistance)

L12 ANSWER 13 OF 34 CAPLUS COPYRIGHT 2003 ACS on STN

ACCESSION NUMBER:

2002:26264 CAPLUS

DOCUMENT NUMBER:

136:93494

TITLE:

Light-sensitive photoresist polyurethane oligomer composition and method for pattern formation using

same

INVENTOR(S):

In, Akira; Kamimo, Masayoshi; Shiota, Makoto

PATENT ASSIGNEE(S): SOURCE:

Hitachi Chemical Co., Ltd., Japan Jpn. Kokai Tokkyo Koho, 11 pp.

CODEN: JKXXAF

DOCUMENT TYPE:

Patent

LANGUAGE:

Japanese

FAMILY ACC. NUM. COUNT: 1

PATENT INFORMATION:

PATENT NO. KIND DATE APPLICATION NO. DATE

JP 2002006485 A2 20020109 JP 2000-192883 20000627

PRIORITY APPLN. INFO.:

JP 2000-192883 20000627

AB The title compn. contains a dispersed polyurethane oligomer and a dispersed resin having carboxylic groups in an aq. soln., wherein the polyurethane oligomer has a hydrophilic anionic groups and a ethylenic unsat. groups. The compn., which contain the polyurethane oligomer and the resin having carboxylic groups, provide resist of little tack and suitable for contact exposure.

IT 386273-09-2P, PTG 850SN-Dimethylolbutyric acid-2-Hydroxyethyl acrylate-Tripentaerythritol acrylate-Norbornane diisocyanate-Tripropylene glycol diacrylate copolymer

RL: SPN (Synthetic preparation); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

(polyurethane oligomer in photoresist compn.)

RN 386273-09-2 CAPLUS

CN Butanoic acid, bis(hydroxymethyl)-, polymer with 2,5(or 2,6)-diisocyanatobicyclo[2.2.1]heptane, .alpha.-hydro-.omega.-hydroxypoly(oxy-1,4-butanediyl), 2-hydroxyethyl 2-propenoate, 2-(hydroxymethyl)-2-[[(1-oxo-2-propenyl)oxy]methyl]-1,3-propanediyl di-2-propenoate and (1-methyl-1,2-ethanediyl)bis[oxy(methyl-2,1-ethanediyl)] di-2-propenoate (9CI) (CA INDEX NAME)

CM 1

CRN 216224-39-4 CMF C9 H10 N2 O2 CCI IDS

D1-NCO

CM 2

CRN 56743-27-2 CMF C6 H12 O4

CCI IDS

Page 68Lee507

CM 3

CRN 42978-66-5 CMF C15 H24 O6

CCI IDS

$$\begin{array}{c} \circ \\ \parallel \\ \text{H}_2\text{C} = \text{CH} - \text{C} - \text{O} - \text{CH}_2 - \text{CH}_2 - \text{O} - \text{CH}_2 - \text{CH}_2 - \text{O} - \text{CH}_2 - \text{CH}_2 - \text{O} - \text{C} + \text{CH}_2 - \text{CH}_2 - \text{C} + \text{C}$$

CM 4

CRN 25190-06-1 CMF (C4 H8 O)n H2 O CCI PMS

HO (CH<sub>2</sub>)<sub>4</sub> - O 
$$\frac{1}{n}$$
 H

CM 5

CRN 3524-68-3 CMF C14 H18 O7 Page 69Lee507

CM 6

CRN 818-61-1 CMF C5 H8 O3

$$\begin{array}{c} \text{O} \\ || \\ \text{HO-} \ \text{CH}_2 - \text{CH}_2 - \text{O-} \ \text{C-} \ \text{CH} \longrightarrow \ \text{CH}_2 \\ \end{array}$$

IC ICM G03F007-027

ICS C08F002-44; C08F002-50; C08F299-06; C08L033-00; C08L055-00;
C08L101-08; C08L101-14; G03F007-032; G03F007-033

CC 74-5 (Radiation Chemistry, Photochemistry, and Photographic and Other Reprographic Processes)

ST light sensitive photoresist polyurethane oligomer compn

IT Polyurethanes, preparation

RL: SPN (Synthetic preparation); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

(acrylates; polyurethane oligomer in photoresist compn.)

IT Photoresists

(light-sensitive photoresist polyurethane oligomer compn. and method for pattern formation using same)

386273-08-1P, PTG 850SN-Dimethylolbutyric acid-2-Hydroxyethyl acrylate-Tripentaerythritol acrylate-Isophorone diisocyanate-Tripropylene glycol diacrylate copolymer 386273-09-2P, PTG 850SN-Dimethylolbutyric acid-2-Hydroxyethyl acrylate-Tripentaerythritol acrylate-Norbornane diisocyanate-Tripropylene glycol diacrylate copolymer RL: SPN (Synthetic preparation); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

(polyurethane oligomer in photoresist compn.)

IT 25133-97-5P, Methyl methacrylate/ethyl acrylate/methacrylic acid copolymer 26915-97-9P, Methyl methacrylate-ethyl acrylate-methacrylic acid-2-hydroxyethyl methacrylate copolymer

RL: SPN (Synthetic preparation); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

(resin having calboxylic groups in photoresist compn.)

L12 ANSWER 14 OF 34 CAPLUS COPYRIGHT 2003 ACS on STN

ACCESSION NUMBER:

2001:624179 CAPLUS

DOCUMENT NUMBER:

135:203003

Page 70Lee507

Photoresist monomer, photoresist polymer, manufacture TITLE:

of the polymer, photoresist composition, patterning of photoresist, and semiconductor device manufactured by

using the photoresist pattern

INVENTOR(S): Lee, Keun Soo; Jung, Jae Chang; Jung, Min Ho; Paek, Ki

PATENT ASSIGNEE(S): Hynix Semiconductor, S. Korea

SOURCE: Jpn. Kokai Tokkyo Koho, 24 pp.

CODEN: JKXXAF

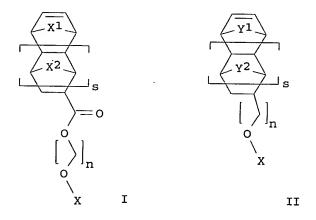
DOCUMENT TYPE: Patent

LANGUAGE: Japanese

FAMILY ACC. NUM. COUNT: PATENT INFORMATION:

GI

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
JP 2001233920	A2	20010828	JP 2001-42125	20010219
US 2001031420	A1	20011018	US 2001-788181	20010215
US 6589707	B2	20030708		
PRIORITY APPLN. INFO.	:		KR 2000-7853 A	20000218



$$Q = \begin{pmatrix} R^1 & R^2 \\ Si & SiH \\ \\ & &$$

The monomer for photoresist is CH2:CR5CO2(CH2)nOX (X = cyclic silyl group AB Q; R1-R4 = H, C1-10 linear or branched alkyl which may be inserted with

Page 71Lee507

IT

CN

O), I, or II (X1, X2, Y1, Y2 = CH2, CH2CH2; R5 = H, Me; s, t = 0-2; n = 1-5). The photoresist polymer is that involving .gtoreq.1 of the above monomers and the polymer is manufd. by mixing the monomers and polymg. in the presence of a polymn. initiator. The photoresist compn. contains the polymer, a photosensitive acid-generating agent, and an org. solvent. The compn. is applied on a substrate, exposed, and developed to give the pattern which is used in semiconductor device fabrication. The photoresist compn. is suitable for bilayer resist and the photoresist polymer involving Si shows good O2 plasma etching resistance. 356043-19-1P 356043-20-4P 356043-21-5P

RL: DEV (Device component use); IMF (Industrial manufacture); PEP (Physical, engineering or chemical process); PREP (Preparation); PROC (Process); USES (Uses)

(polymer involving cyclic silane or alicyclic group for bilayer photoresist for semiconductor device fabrication)

RN 356043-19-1 CAPLUS

Bicyclo[2.2.1]hept-5-ene-2,3-dicarboxylic acid, mono[3-(hydroxymethyl)-3-methylpentyl] ester, polymer with 1,1-dimethylethyl bicyclo[2.2.1]hept-5-ene-2-carboxylate, 2,2-dimethyl-1,3-propanediyl di-2-propenoate, 2,5-furandione and 2-[(1,3,5,7-tetramethyl-1,3,5,7-tetrasilacyclooct-1-yl)oxy]ethyl 2-propenoate (9CI) (CA INDEX NAME)

CM 1

CRN 356043-18-0 CMF C16 H24 O5

CM 2

CRN 356043-15-7 CMF C13 H30 O3 Si4 Page 72Lee507

Me 
$$O-CH_2-CH_2-O-C-CH=CH_2$$

Me  $Me$ 

Si  $Me$ 

Me  $Me$ 

CM 3

CRN 154970-45-3 CMF C12 H18 O2

CM 4

CRN 2223-82-7 CMF C11 H16 O4

CM 5

CRN 108-31-6 CMF C4 H2 O3

## Page 73Lee507

RN 356043-20-4 CAPLUS

CN Bicyclo[2.2.1]hept-5-ene-2,3-dicarboxylic acid, mono[3-(hydroxymethyl)-3-methylpentyl] ester, polymer with 1,1-dimethylethyl bicyclo[2.2.1]hept-5-ene-2-carboxylate, 2,5-furandione, 1,1,4,4-tetramethyl-1,4-butanediyl di-2-propenoate and 2-[(1,3,5,7-tetramethyl-1,3,5,7-tetrasilacyclooct-1-yl)oxy]ethyl 2-propenoate (9CI) (CA INDEX NAME)

CM 1

CRN 356043-18-0 CMF C16 H24 O5

CM 2

CRN 356043-15-7 CMF C13 H30 O3 Si4

Me 
$$O-CH_2-CH_2-O-C-CH=CH_2$$

Si  $Me$ 

Me  $SiH$ 

Me  $Me$ 

CM 3

CRN 188837-15-2 CMF C14 H22 O4 Page 74Lee507

CM 4

CRN 154970-45-3 CMF C12 H18 O2

CM 5

CRN 108-31-6 CMF C4 H2 O3

RN 356043-21-5 CAPLUS

CN Bicyclo[2.2.1]hept-5-ene-2,3-dicarboxylic acid, mono[3-(hydroxymethyl)-3-methylpentyl] ester, polymer with bicyclo[2.2.1]hept-2-ene, 1-(bicyclo[2.2.1]hept-5-en-2-ylmethoxy)-1,3,5,7-tetramethyl-1,3,5,7-tetrasilacyclooctane, 1,1-dimethylethyl bicyclo[2.2.1]hept-5-ene-2-carboxylate, 2,5-furandione and 1,1,4,4-tetramethyl-1,4-butanediyl di-2-propenoate (9CI) (CA INDEX NAME)

CM 1

CRN 356043-18-0 CMF C16 H24 O5 Page 75Lee507

$$\begin{array}{c|c} O & CH_2-OH \\ \parallel & \mid \\ C-O-CH_2-CH_2-C-Et \\ \parallel & \mid \\ CO_2H \end{array}$$

CM 2

CRN 356043-17-9 CMF C16 H34 O Si4

CM 3

CRN 188837-15-2 CMF C14 H22 O4

CM 4

CRN 154970-45-3 CMF C12 H18 O2 Page 76Lee507

CM 5

CRN 498-66-8 CMF C7 H10



CM 6

CRN 108-31-6 CMF C4 H2 O3

IC C08F230-08; C07F007-18; C08F002-48; C08F220-20; C08F222-06; C08F232-00;
C08F232-04; C08K005-00; C08L033-04; C08L035-00; C08L043-04; C08L045-00;
G03F007-039; G03F007-075; G03F007-11; G03F007-26; H01L021-027

CC 74-5 (Radiation Chemistry, Photochemistry, and Photographic and Other Reprographic Processes)
Section cross-reference(s): 38, 76

ST photoresist cyclic silyl monomer polymer; alicyclic monomer polymer photoresist; bilayer photoresist semiconductor device fabrication; etching resistance photoresist polymer

IT Photolithography

(of polymer involving cyclic silane or alicyclic group for bilayer photoresist for semiconductor device fabrication)

IT Etching

(plasma, resistance; of polymer involving cyclic silane or alicyclic group for bilayer photoresist for semiconductor device fabrication)

IT Photoresists

Semiconductor device fabrication

(polymer involving cyclic silane or alicyclic group for bilayer

```
photoresist for semiconductor device fabrication)
 IT
      RL: NUU (Other use, unclassified); USES (Uses)
         (solvent; for prepn. of photoresist compn. contg. polymer involving
         cyclic silane or alicyclic group)
      52754-92-4, Diphenyliodonium hexafluoroantimonate 57835-99-1,
      Triphenylsulfonium hexafluorophosphate
                                             57840-38-7, Triphenylsulfonium
      hexafluoroantimonate
                            57900-42-2, Triphenylsulfonium hexafluoroarsenate
      58109-40-3, Diphenyliodonium hexafluorophosphate
                                                        62613-15-4,
     Diphenyliodonium hexafluoroarsenate 66003-78-9, Triphenylsulfonium
                             116808-67-4, Diphenyl-p-methoxyphenylsulfonium
      triflate
                81416-37-7
     triflate
                 145612-66-4
                              195245-87-5
                                            255056-42-9
     RL: CAT (Catalyst use); USES (Uses)
         (acid-generating agent; polymer involving cyclic silane or alicyclic
        group for bilayer photoresist for semiconductor device fabrication)
 IT
     818-61-1, 2-Hydroxyethyl acrylate 2370-88-9, 2,4,6,8-
     Tetramethylcyclotetrasiloxane
                                    37503-42-7, 2-Hydroxyethyl
     5-norbornene-2-carboxylate
     RL: RCT (Reactant); RACT (Reactant or reagent)
        (monomer from; polymer involving cyclic silane or alicyclic group for
        bilayer photoresist for semiconductor device fabrication)
IT
     356043-15-7P
                    356043-16-8P
                                   356043-17-9P
     RL: IMF (Industrial manufacture); RCT (Reactant); PREP (Preparation); RACT
     (Reactant or reagent)
        (monomer; polymer involving cyclic silane or alicyclic group for
        bilayer photoresist for semiconductor device fabrication)
     78-67-1, AIBN 94-36-0, Benzoyl peroxide, uses
IT
                                                       110-05-4, tert-Butyl
     peroxide
                110-22-5, Acetyl peroxide 2895-03-6, Lauryl peroxide
     RL: CAT (Catalyst use); USES (Uses)
        (photopolymn. initiator; for prepn. of photoresist polymer involving
        cyclic silane or alicyclic group)
IT
     356043-19-1P 356043-20-4P 356043-21-5P
     RL: DEV (Device component use); IMF (Industrial manufacture); PEP
     (Physical, engineering or chemical process); PREP (Preparation); PROC
     (Process); USES (Uses)
        (polymer involving cyclic silane or alicyclic group for bilayer
        photoresist for semiconductor device fabrication)
IT
     60-29-7, Diethyl ether, uses
                                  64-17-5, Ethanol, uses
                                                           67-56-1, Methanol,
     uses 67-63-0, Isopropyl alcohol, uses 67-64-1, Acetone, uses
     67-66-3, Chloroform, uses 67-68-5, DMSO, uses 68-12-2, DMF, uses
     71-23-8, Propanol, uses 71-43-2, Benzene, uses 78-93-3, Ethyl methyl
                   108-88-3, Toluene, uses
    ketone, uses
                                            109-99-9, THF, uses
    Hexane, uses
                   110-82-7, Cyclohexane, uses
                                                123-91-1, Dioxane, uses
    141-78-6, Ethyl acetate, uses
                                   1330-20-7, Xylene, uses
    RL: NUU (Other use, unclassified); USES (Uses)
        (solvent; for prepn. of photoresist compn. contg. polymer involving
        cyclic silane or alicyclic group)
    108-94-1, Cyclohexanone, uses
IT
                                   120-92-3, Cyclopentanone
                                                               763-69-9, Ethyl
    3-ethoxypropionate 84540-57-8, Propylene glycol methyl ether acetate
    RL: NUU (Other use, unclassified); USES (Uses)
        (solvent; polymer involving cyclic silane or alicyclic group for
       bilayer photoresist for semiconductor device fabrication)
```

#### Page 78Lee507

L12 ANSWER 15 OF 34 CAPLUS COPYRIGHT 2003 ACS on STN

ACCESSION NUMBER:

2001:451196 CAPLUS

DOCUMENT NUMBER:

135:68548

TITLE:

Radiation-sensitive chemically amplified resist composition containing specific

copolymer

INVENTOR (S):

Nishimura, Yukio; Kobayashi, Eiichi; Shiotani, Takeo;

Shimokawa, Tsutomu

PATENT ASSIGNEE(S):

JSR Co., Ltd., Japan

SOURCE:

Jpn. Kokai Tokkyo Koho, 18 pp.

CODEN: JKXXAF

DOCUMENT TYPE:

Patent

LANGUAGE:

Japanese

FAMILY ACC. NUM. COUNT: 1

PATENT INFORMATION:

PATENT NO. KIND DATE APPLICATION NO. DATE

JP 2001166474 A2 20010622 JP 1999-344911 19991203

PRIORITY APPLN. INFO.: JP 1999-344911 19991203

GI

AB The title compn. contains a radiation-sensitive acid generator and a copolymer having repeating unit [-C(R1)(COOR2)-CH2-] ( R1 = H, methyl; R2 = C>10 alicyclic) and of repeating unit I ( R3 = H, methyl) with .ltoreq.50 % content. The compn., which contains the copolymer having the aforementioned repeating units, shows the decreased effect of the post exposure delay(PED) on the pattern profiles.

IT 345631-89-2P

RL: SPN (Synthetic preparation); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

(radiation active chem. amplified resist compn. contg.

specific copolymer)

RN 345631-89-2 CAPLUS

CN 2-Propenoic acid, 1,1,4,4-tetramethyl-1,4-butanediyl ester, polymer with [decahydro-6(or 7)-hydroxy-1,4:5,8-dimethanonaphthalen-2-yl]methyl 2-propenoate, 1-(1,1-dimethylethoxy)-4-ethenylbenzene and 4-ethenylphenol

## • Page 79Lee507

(9CI) (CA INDEX NAME)

CM 1

CRN 345631-87-0

CMF C16 H22 O3

CCI IDS

D1- OH

CM 2

CRN 188837-15-2 CMF C14 H22 O4

CM 3

CRN 95418-58-9 CMF C12 H16 O

CM 4

CRN 2628-17-3

CMF C8 H8 O

IC ICM G03F007-038

ICS C08L033-06; G03F007-004; H01L021-027; C08L025-18

CC 74-5 (Radiation Chemistry, Photochemistry, and Photographic and Other Reprographic Processes)

ST radiation active amplified resist compn copolymer

IT Light-sensitive materials

Photoresists

(radiation active chem. amplified resist compn. contg. specific copolymer)

IT 200808-68-0P, 4-Hydroxystyrene-styrene-tert-butyl acrylate copolymer 345348-83-6P 345348-84-7P 345348-85-8P 345631-88-1P

**345631-89-2P** 345631-90-5P 345631-91-6P

RL: SPN (Synthetic preparation); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

(radiation active chem. amplified resist compn. contg. specific copolymer)

L12 ANSWER 16 OF 34 CAPLUS COPYRIGHT 2003 ACS on STN

ACCESSION NUMBER:

2001:208019 CAPLUS

DOCUMENT NUMBER:

134:245232

TITLE:

Radiation-sensitive resin composition as

chemically-amplified photoresist with superior dry etching resistance and resolution for deep UV

lithography

INVENTOR(S): Douki, Katsuji; Murata, Kiyoshi; Ishii, Hiroyuki;

Kajita, Toru; Shimokawa, Tsutomu

PATENT ASSIGNEE(S):

JSR Corporation, Japan

SOURCE:

Eur. Pat. Appl., 52 pp.

CODEN: EPXXDW

DOCUMENT TYPE:

Patent English

LANGUAGE:

D.T. ..

FAMILY ACC. NUM. COUNT: 1

PATENT INFORMATION:

	PAT	CENT :	NO.		KI	ND	DATE			AF	PLI	CATI	ON N	Ο.	DATE			
											<b>-</b>							
	EP	1085	379		A:	1	2001	0321		EF	20	00-1	2000	0	2000	0914		
		R:	AT,	BE,	CH,	DE,	DK,	ES,	FR,	GB,	GR,	IT,	LI,	LU,	NL,	SE,	MC,	PT,
			ΙE,	SI,	LT,	LV,	FI,	RO										
	JP	2001	1091	57	A:	2	2001	0420		JP	19	99-2	9129	1	1999	1013		
	JΡ	2001	2091	81	A:	2	2001	0803		JP	200	00-2	7796	6	20000	0913		
	US	6482	568		B	1	2002	1119		US	20	00-6	6216	0	20000	914		
PRIOR	RITY	APP	LN.	INFO	. :					JP 19	99-2	2641	10	Α	19990	0917		

JP 1999-291291 A 19991013 JP 1999-325222 A 19991116

GI

- \* STRUCTURE DIAGRAM TOO LARGE FOR DISPLAY AVAILABLE VIA OFFLINE PRINT \*
- AB A radiation-sensitive resin compn. comprises (a) a resin contq. an acid-dissociable group which is insol. or scarcely sol. in alkali and becomes alkali sol. when the acid-dissociable group dissocs., comprising the following recurring unit I, recurring unit II, and at least one of the recurring units III and IV (A, B = H, C1-4-alkyl; X, Y = H, monovalent O or N contg. polar group, X joining together with Y may form dicarboxylic anhydride group; n = 0-2; R1 = H, CH3; R2 = CR33; R3 = monovalentalicyclic hydrocarbon group having 4-20 carbon atoms, its deriv., C1-4-alkyl; R4 = divalent hydrocarbon group having alicyclic skeleton contg. 3-15 carbons), (b) a photoacid generator, (c) an acid diffusion controller, and (d) alicyclic additive. The radiation-sensitive resin compn. is suitable for use as a chem.-amplified resist showing sensitivity to active radiation such as deep UV rays represented by a KrF excimer laser or ArF excimer laser, exhibiting superior dry etching resistance without being affected by types of etching gas, having high radiation transmittance, exhibiting excellent basic characteristics as a resist such as sensitivity, resoln., and pattern shape, possessing excellent storage stability as a compn., and exhibiting sufficient adhesion to substrates.
- IT 330576-39-1P

RL: PEP (Physical, engineering or chemical process); PRP (Properties); SPN (Synthetic preparation); TEM (Technical or engineered material use); PREP (Preparation); PROC (Process); USES (Uses)

(copolymer compns. as chem.-amplified photoresist with superior dry etching resistance, sensitivity and resoln. properties for deep UV lithog.)

RN 330576-39-1 CAPLUS

CN 2-Propenoic acid, 1,1,4,4-tetramethyl-1,4-butanediyl ester, polymer with 2,5-furandione, 2-methyltricyclo[3.3.1.13,7]dec-2-yl 2-propenoate and 1,2,3,4,4a,5,8,8a-octahydro-2-methyl-1,4:5,8-dimethanonaphthalene-2-methanol (9CI) (CA INDEX NAME)

CM 1

CRN 249562-06-9 CMF C14 H20 O2 Page 82Lee507

CM 2

CRN 231296-21-2. CMF C14 H20 O

CM 3

CRN 188837-15-2 CMF C14 H22 O4

CM 4

CRN 108-31-6 CMF C4 H2 O3

IC ICM G03F007-039

CC 74-5 (Radiation Chemistry, Photochemistry, and Photographic and Other Reprographic Processes)
Section cross-reference(s): 38

```
chem amplified photoresist polymer prepn compn deep UV lithog; dry etching
      resistance sensitivity resoln chem amplified photoresist polymer
 IT
      Photoresists
         (UV; copolymer compns. as chem.-amplified photoresist with superior dry
         etching resistance, sensitivity and resoln. properties for deep UV
         lithoq.)
      103-76-4, 1-(2-Hydroxyethyl)piperazine
 IT
                                              611-36-9, 4-Hydroxyquinoline
      1116-76-3, Tri-n-octylamine
                                    3033-62-3, Bis(2-dimethylaminoethyl)ether
      7560-83-0, Methyldicyclohexylamine
                                          193810-83-2
                                                         330576-56-2
     RL: PEP (Physical, engineering or chemical process); TEM (Technical or
      engineered material use); PROC (Process); USES (Uses)
         (acid diffusion controller; copolymer compns. as chem.-amplified
        photoresist with superior dry etching resistance, sensitivity and
         resoln. properties for deep UV lithog.)
 IT
                    330576-38-0P 330576-39-1P 330576-41-5P
      330576-37-9P
     330576-42-6P
                    330576-43-7P
                                   330576-44-8P 330576-46-0P
                                                                  330576-47-1P
      330576-48-2P
                    330576-49-3P
                                   330576-51-7P 330576-52-8P
                                                                 330576-54-0P
      330576-55-1P
     RL: PEP (Physical, engineering or chemical process); PRP (Properties); SPN
      (Synthetic preparation); TEM (Technical or engineered material use); PREP
     (Preparation); PROC (Process); USES (Uses)
         (copolymer compns. as chem.-amplified photoresist with superior dry
        etching resistance, sensitivity and resoln. properties for deep UV
        lithog.)
IT
     498-66-8D, Bicyclo[2.2.1]hept-2-ene, imide derivs.
                                                          66003-78-9.
     Triphenylsulfonium trifluoromethanesulfonate 144317-44-2,
     Triphenylsulfonium nonafluoro-n-butanesulfonate 194999-85-4
     209482-18-8
                   330576-58-4
     RL: PEP (Physical, engineering or chemical process); TEM (Technical or
     engineered material use); PROC (Process); USES (Uses)
        (photoacid generator; copolymer compns. as chem.-amplified photoresist
        with superior dry etching resistance, sensitivity and resoln.
        properties for deep UV lithog.)
IT
     157692-53-0, tert-Butyl deoxycholate
                                            169228-97-1
                                                          231296-44-9,
     t-Butoxycarbonylmethyl deoxycholate
     RL: TEM (Technical or engineered material use); USES (Uses)
        (resist additive; copolymer compns. as chem.-amplified
        photoresist with superior dry etching resistance, sensitivity and
        resoln. properties for deep UV lithog.)
REFERENCE COUNT:
                               THERE ARE 5 CITED REFERENCES AVAILABLE FOR THIS
                         5
                               RECORD. ALL CITATIONS AVAILABLE IN THE RE FORMAT
L12 ANSWER 17 OF 34 CAPLUS COPYRIGHT 2003 ACS on STN
ACCESSION NUMBER:
                         2001:150535 CAPLUS
DOCUMENT NUMBER:
                         134:200535
TITLE:
                         Crosslinking monomer containing double bond and
                         photoresist copolymer containing the same
INVENTOR (S):
                         Lee, Geun Su; Jung, Jae Chang; Baik, Ki Ho
PATENT ASSIGNEE(S):
                         Hyundai Electronics Industries Co., Ltd., Ichon, S.
                         Korea
SOURCE:
                         Ger. Offen., 16 pp.
```

CODEN: GWXXBX

#### Page 84Lee507

DOCUMENT TYPE:

Patent

LANGUAGE:

German

FAMILY ACC. NUM. COUNT:

PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
DE 10040963 GB 2354004 JP 2001106737 PRIORITY APPLN. INFO.	A1 A1 A2	20010301 20010314 20010417	DE 2000-10040963 GB 2000-19436 JP 2000-252762 KR 1999-35046 A	20000822 20000809 20000823 19990823

$$\begin{array}{c|c} & & & R^7 \\ & & & & \\ & & & & \\ & & & & \\ & & & & \\ & & & & \\ & & & & \\ & & & & \\ & & & & \\ & & & & \\ & & & & \\ & & & & \\ & & & & \\ & & & & \\ & & & & \\ & & & & \\ & & & & \\ & & & & \\ & & & & \\ & & & & \\ & &$$

Ι

II

The photoresist copolymer includes a crosslinking monomer represented by I or II (R1-8 = H, C1-5-alkyl; k = 0-3), and at least one another suitable photoresist monomer. The crosslinking monomer may be selected from 2,5-hexanediol diacrylate, 2,5-hexanediol dimethacrylate, 2,4-pentanediol diacrylate, 2,4-pentanediol diacrylate, neopentylglycol diacrylate, and neopentylglycol dimethacrylate. The photoresist copolymer is prepd. and the photoresist compn. is also prepd. The photoresist compn. is sensitive to ArF-, KrF-, VUV-, EUV-light-sources, electron-beam, x-ray, or ion-beam.

IT 328068-00-4P, Mono-2-ethyl-2-(hydroxymethyl)-butylbicyclo-[2.2.1]hept-5-ene-2,3-dicarboxylate-maleic acid anhydride-norbornene-tertbutylbicyclo-[2.2.1]-hept-5-ene-2-carboxylate-2,5-hexanediol diacrylate
copolymer 328068-01-5P, Mono-2-ethyl-2-(hydroxymethyl)butylbicyclo-[2.2.1]-hept-5-ene-2,3-dicarboxylate-maleic acid
anhydride-norbornene-tert-butylbicyclo-[2.2.1]-hept-5-ene-2-carboxylate2,4-pentanediol diacrylate copolymer 328068-02-6P,
Mono-2-ethyl-2-(hydroxymethyl)-butylbicyclo-[2.2.1]-hept-5-ene-2,3dicarboxylate-maleic acid anhydride-norbornene-tert-butylbicyclo-[2.2.1]-

hept-5-ene-2-carboxylate-neopentyl glycol diacrylate copolymer 328068-03-7P, Mono-2-ethyl-2-(hydroxymethyl)-butylbicyclo-[2.2.1]-hept-5-ene-2,3-dicarboxylate-maleic acid anhydride-norbornene-tert-butylbicyclo-[2.2.1]-hept-5-ene-2-carboxylate-2,5-hexanediol dimethacrylate copolymer 328068-04-8P, Mono-2-ethyl-2-(hydroxymethyl)-butylbicyclo-[2.2.1]-hept-5-ene-2,3-dicarboxylate-maleic acid anhydride-norbornene-tert-butylbicyclo-[2.2.1]-hept-5-ene-2-carboxylate-2,4-pentanediol dimethacrylate copolymer 328068-05-9P, Mono-2-ethyl-2-(hydroxymethyl)-butylbicyclo-[2.2.1]-hept-5-ene-2,3-dicarboxylate-maleic acid anhydride-norbornene-tert-butylbicyclo-[2.2.1]-hept-5-ene-2-carboxylate-neopentyl glycol dimethacrylate copolymer RL: SPN (Synthetic preparation); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

(prepn. of photoresist copolymer contg. crosslinking monomer with double bond)

RN 328068-00-4 CAPLUS

Bicyclo[2.2.1]hept-5-ene-2,3-dicarboxylic acid, mono[2-ethyl-2-(hydroxymethyl)butyl] ester, polymer with bicyclo[2.2.1]hept-2-ene, 1,4-dimethyl-1,4-butanediyl di-2-propenoate, 1,1-dimethylethyl bicyclo[2.2.1]hept-5-ene-2-carboxylate and 2,5-furandione (9CI) (CA INDEX NAME)

CM 1

CN

CRN 250583-69-8 CMF C16 H24 O5

CM 2

CRN 154970-45-3 CMF C12 H18 O2

CM 3

#### Page 86Lee507

CRN 85996-28-7 CMF C12 H18 O4

CM 4

CRN 498-66-8 CMF C7 H10



CM 5

CRN 108-31-6 CMF C4 H2 O3

RN 328068-01-5 CAPLUS

CN Bicyclo[2.2.1]hept-5-ene-2,3-dicarboxylic acid, mono[2-ethyl-2-(hydroxymethyl)butyl] ester, polymer with bicyclo[2.2.1]hept-2-ene, 1,1-dimethylethyl bicyclo[2.2.1]hept-5-ene-2-carboxylate, 1,3-dimethyl-1,3-propanediyl di-2-propenoate and 2,5-furandione (9CI) (CA INDEX NAME)

CM 1

CRN 250583-69-8 CMF C16 H24 O5 Page 87Lee507

CM 2

CRN 184223-36-7 CMF C11 H16 O4

CM 3

CRN 154970-45-3 CMF C12 H18 O2

CM 4

CRN 498-66-8 CMF C7 H10

Page 88Lee507

CM 5

CRN 108-31-6 CMF C4 H2 O3

RN 328068-02-6 CAPLUS

CN Bicyclo[2.2.1]hept-5-ene-2,3-dicarboxylic acid, mono[2-ethyl-2-(hydroxymethyl)butyl] ester, polymer with bicyclo[2.2.1]hept-2-ene, 1,1-dimethylethyl bicyclo[2.2.1]hept-5-ene-2-carboxylate, 2,2-dimethyl-1,3-propanediyl di-2-propenoate and 2,5-furandione (9CI) (CA INDEX NAME)

CM 1

CRN 250583-69-8 CMF C16 H24 O5

CM 2

CRN 154970-45-3 CMF C12 H18 O2

CM 3

CRN 2223-82-7 CMF C11 H16 O4

CM 4

CRN 498-66-8 CMF C7 H10



CM 5

CRN 108-31-6 CMF C4 H2 O3

RN 328068-03-7 CAPLUS

CN Bicyclo[2.2.1]hept-5-ene-2,3-dicarboxylic acid, mono[2-ethyl-2-(hydroxymethyl)butyl] ester, polymer with bicyclo[2.2.1]hept-2-ene, 1,4-dimethyl-1,4-butanediyl bis(2-methyl-2-propenoate), 1,1-dimethylethyl bicyclo[2.2.1]hept-5-ene-2-carboxylate and 2,5-furandione (9CI) (CA INDEX NAME)

CM 1

CRN 250583-69-8 CMF C16 H24 O5

# Page 90Lee507

CM 2

CRN 154970-45-3 CMF C12 H18 O2

CM 3

CRN 86336-50-7 CMF C14 H22 O4

CM 4

CRN 498-66-8 CMF C7 H10



Page 91Lee507

CM 5

CRN 108-31-6 CMF C4 H2 O3

RN 328068-04-8 CAPLUS
CN Bicyclo[2.2.1]hept-5-ene-2,3-dicarboxylic acid, mono[2-ethyl-2-(hydroxymethyl)butyl] ester, polymer with bicyclo[2.2.1]hept-2-ene, 1,1-dimethylethyl bicyclo[2.2.1]hept-5-ene-2-carboxylate,

1,3-dimethyl-1,3-propanediyl bis(2-methyl-2-propenoate) and 2,5-furandione (9CI) (CA INDEX NAME)

CM 1

CRN 328067-99-8 CMF C13 H20 O4

CM 2

CRN 250583-69-8 CMF C16 H24 O5

CM 3

CRN 154970-45-3 CMF C12 H18 O2

CM 4

CRN 498-66-8 CMF C7 H10



CM 5

CRN 108-31-6 CMF C4 H2 O3

RN 328068-05-9 CAPLUS

CN Bicyclo[2.2.1]hept-5-ene-2,3-dicarboxylic acid, mono[2-ethyl-2-(hydroxymethyl)butyl] ester, polymer with bicyclo[2.2.1]hept-2-ene, 1,1-dimethylethyl bicyclo[2.2.1]hept-5-ene-2-carboxylate, 2,2-dimethyl-1,3-propanediyl bis(2-methyl-2-propenoate) and 2,5-furandione (9CI) (CA INDEX NAME)

CM 1

CRN 250583-69-8 CMF C16 H24 O5 Page 93Lee507

CM 2

CRN 154970-45-3 CMF C12 H18 O2

CM 3

CRN 1985-51-9 CMF C13 H20 O4

CM 4

CRN 498-66-8 CMF C7 H10

CM 5

CRN 108-31-6 CMF C4 H2 O3

IC ICM G03F007-039 ICS C08J007-12

CC 74-5 (Radiation Chemistry, Photochemistry, and Photographic and Other Reprographic Processes) Section cross-reference(s): 38, 76

ST crosslinking monomer photoresist polymer compn prepn

IT Crosslinking agents
Electron beam resists
Ion beam resists
Photoresists

X-ray resists

(crosslinking monomer contg. double bond and photoresist copolymer contg. the same)

IT Ligroine

RL: NUU (Other use, unclassified); USES (Uses) (prepn. of photoresist copolymer contg. crosslinking monomer with double bond)

IT 1985-51-9 2223-82-7 85996-28-7, 2,5-Hexanediol diacrylate 86336-50-7, 2,5-Hexanediol dimethacrylate 184223-36-7, 2,4-Pentanediol diacrylate 328067-99-8, 2,4-Pentanediol dimethacrylate RL: RCT (Reactant); RACT (Reactant or reagent)

(crosslinking monomer contg. double bond for photoresist copolymer)

IT 763-69-9, Ethyl-3-ethoxypropionate

RL: TEM (Technical or engineered material use); USES (Uses) (in photoresist compn. including photoresist copolymer contg. crosslinking monomer with double bond)

IT 66003-78-9, Triphenylsulfoniumtriflate

RL: TEM (Technical or engineered material use); USES (Uses) (photoacid generator in photoresist compn. including photoresist copolymer contg. crosslinking monomer with double bond)

IT 78-67-1, AIBN

RL: CAT (Catalyst use); USES (Uses)
 (prepn. of photoresist copolymer contg. crosslinking monomer with
 double bond)

IT 328068-00-4P, Mono-2-ethyl-2-(hydroxymethyl)-butylbicyclo-[2.2.1]hept-5-ene-2,3-dicarboxylate-maleic acid anhydride-norbornene-tertbutylbicyclo-[2.2.1]-hept-5-ene-2-carboxylate-2,5-hexanediol diacrylate

```
copolymer 328068-01-5P, Mono-2-ethyl-2-(hydroxymethyl)-
butylbicyclo-[2.2.1]-hept-5-ene-2,3-dicarboxylate-maleic acid
anhydride-norbornene-tert-butylbicyclo-[2.2.1]-hept-5-ene-2-carboxylate-
2,4-pentanediol diacrylate copolymer 328068-02-6P,
Mono-2-ethyl-2-(hydroxymethyl)-butylbicyclo-[2.2.1]-hept-5-ene-2,3-
dicarboxylate-maleic acid anhydride-norbornene-tert-butylbicyclo-[2.2.1]-
hept-5-ene-2-carboxylate-neopentyl glycol diacrylate copolymer
328068-03-7P, Mono-2-ethyl-2-(hydroxymethyl)-butylbicyclo-[2.2.1]-
hept-5-ene-2,3-dicarboxylate-maleic acid anhydride-norbornene-tert-
butylbicyclo-[2.2.1]-hept-5-ene-2-carboxylate-2,5-hexanediol
dimethacrylate copolymer 328068-04-8P, Mono-2-ethyl-2-
(hydroxymethyl)-butylbicyclo-[2.2.1]-hept-5-ene-2,3-dicarboxylate-maleic
acid anhydride-norbornene-tert-butylbicyclo-[2.2.1]-hept-5-ene-2-
carboxylate-2,4-pentanediol dimethacrylate copolymer 328068-05-9P
, Mono-2-ethyl-2-(hydroxymethyl)-butylbicyclo-[2.2.1]-hept-5-ene-2,3-
dicarboxylate-maleic acid anhydride-norbornene-tert-butylbicyclo-[2.2.1]-
hept-5-ene-2-carboxylate-neopentyl glycol dimethacrylate copolymer
RL: SPN (Synthetic preparation); TEM (Technical or engineered material
use); PREP (Preparation); USES (Uses)
   (prepn. of photoresist copolymer contg. crosslinking monomer with
  double bond)
```

L12 ANSWER 18 OF 34 CAPLUS COPYRIGHT 2003 ACS on STN

ACCESSION NUMBER:

2001:98659 CAPLUS .

DOCUMENT NUMBER:

134:170818

TITLE:

Radiation-sensitive polymer composition for

photoresist

INVENTOR(S):

Nishimura, Yukio; Kobayashi, Hidekazu; Shiotani, Takeo

APPLICATION NO. DATE

PATENT ASSIGNEE(S): JSR Co., Ltd., Japan

SOURCE:

Jpn. Kokai Tokkyo Koho, 23 pp.

CODEN: JKXXAF

DOCUMENT TYPE:

Patent

LANGUAGE:

Japanese

----

KIND DATE

FAMILY ACC. NUM. COUNT: 1

-----

PATENT INFORMATION:

PATENT NO.

	JP 2001033970		20010209	JP 1999-207452	19990722
PRIC	RITY APPLN. INFO.	:		JP 1999-207452	19990722
AB	The title compn.	conta	ins (A) a	copolymer contg. a rep	eating unit
	-C(CO2CMe2CH2R2)	R1CH2-	[R1 = H,	Me; R2 = (substituted)	C6-20 aliqualia on
	arom. group] and	(B) a	radiation	-sensitive acid genera	tor The comme has
	high sensitivity	to ra	diation an	d gives high-resoln. p	ottowns
	is useful as a c	hem. a	mplified n	osworking photoresis	t fam
	device fabricati	on.	prizica p	ob. Working photoresis	c for semiconductor

ΙŤ 324767-26-2

RL: PRP (Properties); TEM (Technical or engineered material use); USES

(radiation-sensitive polymer compn. for pos.-working photoresist)

RN 324767-26-2 CAPLUS

CN Bicyclo[2.2.1]hept-5-ene-2-carboxylic acid, 1,1-dimethylethyl ester,

## Page 96Lee507

polymer with 1,1-dimethyl-2-phenylethyl 2-propenoate, 2,5-furandione and 1,1,4,4-tetramethyl-1,4-butanediyl di-2-propenoate (9CI) (CA INDEX NAME)

CM 1

CRN 324767-19-3 CMF C13 H16 O2

$$\begin{array}{c} \text{O} \\ | \\ | \\ \text{O-C-CH} \\ | \\ \text{Me-C-CH}_2 - \text{Ph} \\ | \\ \text{Me} \end{array}$$

CM 2

CRN 188837-15-2 CMF C14 H22 O4

CM 3

CRN 154970-45-3 CMF C12 H18 O2

CM 4

CRN 108-31-6 CMF C4 H2 O3

IC ICM G03F007-039

ICS G03F007-004; H01L021-027

CC 74-5 (Radiation Chemistry, Photochemistry, and Photographic and Other Reprographic Processes) Section cross-reference(s): 38

radiation sensitive polyacrylate pos photoresist; resoln sensitivity ST radiation sensitive photoresist

IT Positive photoresists

(radiation-sensitive polymer compn. for pos.-working photoresist)

IT Resists

> (radiation-sensitive; radiation-sensitive polymer compn. for pos.-working photoresist)

IT66003-78-9, Triphenylsulfonium trifluoromethanesulfonate 133710-62-0, N-(Trifluoromethyl sulfonyloxy)bicyclo[2.2.1]hept-5-ene-2,3-dicarboxyimide 185195-30-6, Bis(4-tert-butylphenyl)iodonium 10-camphorsulfonate 194999-85-4

RL: PRP (Properties); TEM (Technical or engineered material use); USES (Uses)

(acid generator; radiation-sensitive polymer compn. for pos.-working photoresist)

IT 324767-20-6 324767-21-7 324767-22-8 324767-23-9 324767-24-0 324767-25-1 **324767-26-2** 324767-27-3

RL: PRP (Properties); TEM (Technical or engineered material use); USES (Uses)

(radiation-sensitive polymer compn. for pos.-working photoresist)

L12 ANSWER 19 OF 34 CAPLUS COPYRIGHT 2003 ACS on STN

ACCESSION NUMBER: 2000:774084 CAPLUS

DOCUMENT NUMBER:

133:357243

TITLE:

Radiation sensitive resin composition

INVENTOR(S):

Yamahara, Noboru; Murata, Kiyoshi; Iwanaga, Shinichiro; Ishii, Hiroyuki; Iwasawa, Haruo

PATENT ASSIGNEE(S): Jsr Corp., Japan

SOURCE:

Eur. Pat. Appl., 40 pp.

CODEN: EPXXDW

DOCUMENT TYPE:

Patent

LANGUAGE:

English

FAMILY ACC. NUM. COUNT: 1

PATENT INFORMATION:

PATENT NO. KIND DATE APPLICATION NO. DATE ---------------EP 1048983 A1 20001102 EP 2000-108941 20000427 R: AT, BE, CH, DE, DK, ES, FR, GB, GR, IT, LI, LU, NL, SE, MC, PT, IE, SI, LT, LV, FI, RO US 6403280 B1 20020611 US 2000-558067 20000426

JP 2001013688 A2 20010119 JP 2000-128516 20000427 PRIORITY APPLN. INFO.: JP 1999-122723 A 19990428 GT

The present invention provides a radiation sensitive resin compn. which AB comprises (A) a resin represented by a copolymer comprising recurring units I, II, and [CH2R1(COOR2OH)], or I, II, and [CH2R1(COOR3OH)] (X and Y = H, C1-4 alkyl; n = 0-3; R1 = H, Me methylol; R2 = divalent hydrocarbon; R3 = trivalent hydrocarbon), and (B) a radiation sensitive acid-generator. The radiation sensitive resin compn. has an excellent storage stability and the resist produced from the compn. is a chem. amplifiable type sensitive to radiations represented by artificial UV rays. resist has a high transparency to radiations and it is excellent in basic phys. properties for resist such as durability to dry etching, sensitivity, resoln., and pattern configuration.

IT305384-38-7P

RL: SPN (Synthetic preparation); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses) (radiation sensitive resin compn. from)

305384-38-7 CAPLUS RN

Bicyclo[2.2.1]hept-5-ene-2-carboxylic acid, 1,1-dimethylethyl ester, CN polymer with decahydro-6(or 7)-hydroxy-1,4:5,8-dimethanonaphthalen-2-yl 2-propenoate, 2,5-furandione and 1,1,4,4-tetramethyl-1,4-butanediyl di-2-propenoate (9CI) (CA INDEX NAME)

CM 1

CRN 259536-03-3 CMF C15 H20 O3 CCI IDS

Page 99Lee507

D1-OH

CM 2

CRN 188837-15-2 CMF C14 H22 O4

CM 3

CRN 154970-45-3 CMF C12 H18 O2

CM 4

CRN 108-31-6 CMF C4 H2 O3

IC ICM G03F007-039

KOROMA EIC1700

```
74-5 (Radiation Chemistry, Photochemistry, and Photographic and Other
  CC
       Reprographic Processes)
       Section cross-reference(s): 35, 38
       radiation sensitive resin compn photoacid photoresist
  ST
  IT
      Photoimaging materials
      Photoresists
         (radiation sensitive resin compn. for)
      66003-78-9, Triphenylsulfonium trifluoromethanesulfonate 144317-44-2,
  IT
      Triphenylsulfonium nonafluorobutanesulfonate 194999-85-4 204315-69-5
      209482-18-8
      RL: CAT (Catalyst use); USES (Uses)
         (photoacid; radiation sensitive resin compn. from)
      305379-03-7P 305379-05-9P 305379-06-0P 305379-07-1P 305379-09-3P
  TT
      305379-11-7P 305379-12-8P 305379-13-9P 305384-35-4P
                                                              305384-37-6P
      305384-38-7P
      RL: SPN (Synthetic preparation); TEM (Technical or engineered material
      use); PREP (Preparation); USES (Uses)
         (radiation sensitive resin compn. from)
      1116-76-3, Tri-n-octylamine 19293-63-1, Dicyclohexylmethylamine
 IT
      157692-53-0, tert-Butyl deoxycholate
                                         169228-97-1
      RL: TEM (Technical or engineered material use); USES (Uses)
         (radiation sensitive resin compn. from)
 REFERENCE COUNT:
                              THERE ARE 4 CITED REFERENCES AVAILABLE FOR THIS
                        4
                              RECORD. ALL CITATIONS AVAILABLE IN THE RE FORMAT
 L12 ANSWER 20 OF 34 CAPLUS COPYRIGHT 2003 ACS on STN
 ACCESSION NUMBER: 1999:460321 CAPLUS
 DOCUMENT NUMBER:
                        131:108922
 TITLE:
                       Radiation-sensitive resin composition
 INVENTOR(S):
                      Kajita, Toru; Suwa, Mitsuhito; Iwasawa, Haruo;
                      Yamamoto, Masafumi
PATENT ASSIGNEE(S): JSR Corporation, Japan
SOURCE:
                       Eur. Pat. Appl., 49 pp.
                       CODEN: EPXXDW
DOCUMENT TYPE:
                      Patent
LANGUAGE:
                       English
FAMILY ACC. NUM. COUNT: 1
PATENT INFORMATION:
                                      APPLICATION NO. DATE
     PATENT NO. KIND DATE
     -----
                                        -----
                    A1 19990721 EP 1999-100718 19990115
     EP 930541
        R: AT, BE, CH, DE, DK, ES, FR, GB, GR, IT, LI, LU, NL, SE, MC, PT,
            IE, SI, LT, LV, FI, RO
    JP 11202491 A2 19990730
                                      JP 1998-18290
                                                        19980116
    JP 11265067 A2 19990928
US 6180316 B1 20010130
    JP 11265067
                                      JP 1998-270685 19980925
                                      US 1999-231762 19990115
PRIORITY APPLN. INFO.:
                                     JP 1998-18290 A 19980116
                                     JP 1998-18291 A 19980116
                                     JP 1998-270685 A 19980925
OTHER SOURCE(S):
                     MARPAT 131:108922
```

GI

A radiation-sensitive resin compn. useful as a chem. amplified AB resist comprises (A) a polymer contg. (a) a recurring unit of the formula I (A, B = H or an acid-decomposable org. group having .ltoreq.20 C atoms which dissocs. in the presence of an acid and produces an acidic functional group provided that either one of A and B is the acid-decomposable org. group; X, Y = H or alkyl having 1-4 C atoms; n = 0or 1) or a recurring unit of the formula I and a recurring unit of the formula II and (b) a recurring unit which is derived from a monomer having at least two polymerizable carbon-carbon double bonds by cleavage of the carbon-carbon double bonds, wherein the monomer has, in addn. to said at least two polymerizable carbon-carbon double bonds, at least one acid-decomposable divalent group of the formula -CO2C(R1)(R2)- or -OCOC(R3)(R4)- (R1-4 = alkyl having 1-5 C atoms), said at least two polymerizable carbon-carbon double bonds being linked via the acid-decomposable divalent group and (B) a photoacid generator.

231296-14-3P 231296-17-6P 231296-19-8P 231296-23-4P 231296-25-6P 231296-31-4P 231296-34-7P

RL: SPN (Synthetic preparation); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

(prepn. and use in chem. amplified photoresists)

RN 231296-14-3 CAPLUS

CN 1,4:5,8-Dimethanonaphthalene-2-carboxylic acid, 1,2,3,4,4a,5,8,8a-octahydro-2-methyl-, 2-(1,1-dimethylethoxy)-2-oxoethyl ester, polymer with 2,5-furandione, 1,2,3,4,4a,5,8,8a-octahydro-1,4:5,8-dimethanonaphthalen-2-ol and 1,1,4,4-tetramethyl-1,4-butanediyl di-2-propenoate (9CI) (CA INDEX NAME)

CM 1

CRN 231296-10-9 CMF C20 H28 O4 Page 102Lee507

CM 2

CRN 188837-15-2 CMF C14 H22 O4

CM 3

CRN 7388-87-6 CMF C12 H16 O

CM 4

CRN 108-31-6 CMF C4 H2 O3

RN 231296-17-6 CAPLUS

CN 1,4:5,8-Dimethanonaphthalene-2-carboxylic acid, 1,2,3,4,4a,5,8,8a-octahydro-, 1,1-dimethylethyl ester, polymer with 2,5-furandione and

Page 103Lee507

1,1,4,4-tetramethyl-1,4-butanediyl di-2-propenoate (9CI) (CA INDEX NAME)

CM 1

CRN 195057-79-5 CMF C17 H24 O2

CM 2

CRN 188837-15-2 CMF C14 H22 O4

CM 3

CRN 108-31-6 CMF C4 H2 O3

RN 231296-19-8 CAPLUS

CN 1,4:5,8-Dimethanonaphthalene-2-carboxylic acid, 1,2,3,4,4a,5,8,8a-octahydro-, 1,1-dimethylethyl ester, polymer with 2-hydroxypropyl 2-propenoate and 1,1,4,4-tetramethyl-1,4-butanediyl di-2-propenoate (9CI) (CA INDEX NAME)

CM 1

CRN 195057-79-5 CMF C17 H24 O2 Page 104Lee507

CM 2

CRN 188837-15-2 CMF C14 H22 O4

CM 3

CRN 999-61-1 CMF C6 H10 O3

RN 231296-23-4 CAPLUS

CN Bicyclo[2.2.1]hept-5-ene-2-carboxylic acid, 1,1-dimethylethyl ester, polymer with 2,5-furandione, 1,2,3,4,4a,5,8,8a-octahydro-2-methyl-1,4:5,8-dimethanonaphthalene-2-methanol and 1,1,4,4-tetramethyl-1,4-butanediyl di-2-propenoate (9CI) (CA INDEX NAME)

CM 1

CRN 231296-21-2 CMF C14 H20 O Page 105Lee507

CM 2

CRN 188837-15-2 CMF C14 H22 O4

CM 3

CRN 154970-45-3 CMF C12 H18 O2

CM 4

CRN 108-31-6 CMF C4 H2 O3

RN 231296-25-6 CAPLUS

CN 1,4:5,8-Dimethanonaphthalene-2-carboxylic acid, 1,2,3,4,4a,5,8,8a-octahydro-, 1,1-dimethylethyl ester, polymer with 2-(acetyloxy)ethyl 2-methyl-2-propenoate, 2,5-furandione and 1,1,4,4-tetramethyl-1,4-

Page 106Lee507

butanediyl di-2-propenoate (9CI) (CA INDEX NAME)

CM 1

CRN 195057-79-5 CMF C17 H24 O2

CM 2

CRN 188837-15-2 CMF C14 H22 O4

CM 3

CRN 20166-49-8 CMF C8 H12 O4

CM 4

CRN 108-31-6 CMF C4 H2 O3

RN 231296-31-4 CAPLUS

CN 1,4:5,8-Dimethanonaphthalene-2-carboxylic acid, 1,2,3,4,4a,5,8,8a-octahydro-, tetrahydro-2-oxo-3-furanyl ester, polymer with 1,1-dimethylethyl bicyclo[2.2.1]hept-5-ene-2-carboxylate, 2,5-furandione and 1,1,4,4-tetramethyl-1,4-butanediyl di-2-propenoate (9CI) (CA INDEX NAME)

CM 1

CRN 231296-29-0 CMF C17 H20 O4

CM 2

CRN 188837-15-2 CMF C14 H22 O4

CM 3

CRN 154970-45-3 CMF C12 H18 O2 Page 108Lee507

CM 4

CRN 108-31-6 CMF C4 H2 O3

RN 231296-34-7 CAPLUS

CN Bicyclo[2.2.1]hept-5-ene-2-carboxylic acid, 1,1-dimethylethyl ester, polymer with 2,5-furandione, 1,2,3,4,4a,5,8,8a-octahydro-1,4:5,8-dimethanonaphthalene-2-methanol and 1,1,4,4-tetramethyl-1,4-butanediyl di-2-propenoate (9CI) (CA INDEX NAME)

CM 1

CRN 188837-15-2 CMF C14 H22 O4

CM 2

CRN 154970-45-3 CMF C12 H18 O2 Page 109Lee507

CM 3

CRN 7329-04-6 CMF C13 H18 O

CM

CRN 108-31-6 CMF C4 H2 O3

IC ICM G03F007-039

ICS G03F007-004

CC 74-5 (Radiation Chemistry, Photochemistry, and Photographic and Other Reprographic Processes)

STchem amplified resist norbornene copolymer

IT Photoresists

(chem. amplified; contg. norbornene copolymers)

102-60-3, N,N,N',N'-Tetrakis(2-hydroxypropyl)ethylenediamine IT1116-76-3, Trioctylamine 2842-38-8, N-Cyclohexylethanolamine 3033-62-3, Bis(2-dimethylaminoethyl) ether 66003-78-9, Triphenylsulfonium 144317-44-2, Triphenylsulfonium trifluoromethanesulfonate nonafluorobutanesulfonate 194999-85-4, Bis(4-tert-butylphenyl)iodonium nonafluorobutanesulfonate 204315-69-5 209482-18-8 231296-54-1 RL: TEM (Technical or engineered material use); USES (Uses)

(chem. amplified photoresists contg. norbornene copolymers and)

IT 231299-53-9P

> RL: RCT (Reactant); SPN (Synthetic preparation); TEM (Technical or engineered material use); PREP (Preparation); RACT (Reactant or reagent); USES (Uses)

```
(prepn. and reaction in prepg. alicyclic compd. for chem. amplified
         photoresists contg. norbornene copolymers)
 IT
      3439-94-9P
                  7329-04-6P
                              7388-87-6P 41596-02-5P 46382-54-1P
                  168898-16-6P 195057-79-5P 231296-10-9P 231296-21-2P
      58732-15-3P
      231296-29-0P
     RL: RCT (Reactant); SPN (Synthetic preparation); TEM (Technical or
      engineered material use); PREP (Preparation); RACT (Reactant or reagent);
      USES (Uses)
         (prepn. and reaction in prepg. norbornene copolymers for chem.
        amplified photoresists)
     231296-14-3P 231296-17-6P 231296-19-8P
     231296-23-4P 231296-25-6P 231296-31-4P
     231296-34-7P
     RL: SPN (Synthetic preparation); TEM (Technical or engineered material
     use); PREP (Preparation); USES (Uses)
         (prepn. and use in chem. amplified photoresists)
TΥ
     231299-51-7P
     RL: RCT (Reactant); SPN (Synthetic preparation); TEM (Technical or
     engineered material use); PREP (Preparation); RACT (Reactant or reagent);
     USES (Uses)
        (prepn. and use in chem. amplified photoresists contg. norbornene
        copolymers)
IT
     122752-67-4P
                   169228-97-1P 213901-06-5P
                                                 231296-37-0P
                                                                231296-39-2P
     231296-41-6P
                    231296-42-7P 231296-44-9P 231296-48-3P
                                                                231296-50-7P
     231296-52-9P
     RL: SPN (Synthetic preparation); TEM (Technical or engineered material
     use); PREP (Preparation); USES (Uses)
        (prepn. and use in chem. amplified photoresists contg. norbornene
        copolymers)
IT
     97-64-3, Ethyl 2-hydroxypropionate 108-94-1, Cyclohexanone, uses
     110-43-0, 2-Heptanone 1320-67-8, Propylene glycol monomethyl ether
     RL: TEM (Technical or engineered material use); USES (Uses)
        (solvent for chem. amplified photoresists contg. norbornene copolymers)
REFERENCE COUNT:
                        5
                              THERE ARE 5 CITED REFERENCES AVAILABLE FOR THIS
                              RECORD. ALL CITATIONS AVAILABLE IN THE RE FORMAT
L12 ANSWER 21 OF 34 CAPLUS COPYRIGHT 2003 ACS on STN
ACCESSION NUMBER:
                       1999:175835 CAPLUS
DOCUMENT NUMBER:
                       130:202924
TITLE:
                       Radiation-sensitive resin composition
INVENTOR(S):
                        Iwanaga, Shin-ichiro; Kobayashi, Eiichi; Tanabe,
                        Takayoshi; Kawaguchi, Kazuo
PATENT ASSIGNEE(S):
                        JSR Corporation, Japan
SOURCE:
                        Eur. Pat. Appl., 20 pp.
                        CODEN: EPXXDW
DOCUMENT TYPE:
                        Patent
LANGUAGE:
                        English
FAMILY ACC. NUM. COUNT: 1
PATENT INFORMATION:
    PATENT NO.
                   KIND DATE
                                        APPLICATION NO. DATE
     -----
                          -----
                                         -----
```

EP 901043 Al 19990310 EP 1998-115846 19980821

R: AT, BE, CH, DE, DK, ES, FR, GB, GR, IT, LI, LU, NL, SE, MC, PT,

IE, SI, LT, LV, FI, RO

JP 11143079 A2 19990528 IP 1000 B01145

JP 11143079 A2 19990528 JP 1998-221190 19980805 US 6120972 A 20000919 US 1998-136051 19980818 PRIORITY APPLN. INFO.: JP 1997-251449 A 19970902

A radiation-sensitive resin compn. comprises (A) a copolymer which comprises a repeating unit formed by cleavage of a carbon-carbon double bond of a monomer having one polymerizable carbon-carbon double bond and a repeating unit formed by cleavage of a carbon-carbon double bond of a monomer having two or more polymerizable carbon-carbon double bonds and at least one divalent group decompd. by an acid of the formula -CO2C(R1)(R2)-or -OCO2C(R3)(R4)- (R1-4 = alkyl having 1-5 carbon atoms or aryl having 6-14 carbon atoms), said monomer having a structure in which each carbon-carbon double bond combines via said divalent group, and (B) a photoacid generator. The radiation-sensitive resin compn. exhibits excellent sensitivity and resoln., reduced effect from the swing curves, excellent pattern profile, superior heat resistance, high sensitivity to UV rays, far UV rays, x-rays, and charged particles, and is useful as a chem. amplified pos. photoresist used in the manuf. of integrated circuit devices.

220767-14-6, tert-Butyl acrylate-2,5-dimethyl-2,5-hexanediol diacrylate-p-isopropenylphenol-tricyclodecanyl acrylate copolymer 220767-16-8, tert-Butyl acrylate-2,5-dimethyl-2,5-hexanediol diacrylate-p-isopropenylphenol-isobornyl acrylate copolymer RL: TEM (Technical or engineered material use); USES (Uses) (chem. amplified pos. photoresists contq.)

RN 220767-14-6 CAPLUS

CN 2-Propenoic acid, 1,1,4,4-tetramethyl-1,4-butanediyl ester, polymer with 1,1-dimethylethyl 2-propenoate, 4-(1-methylethenyl)phenol and octahydro-4,7-methano-1H-inden-5-yl 2-propenoate (9CI) (CA INDEX NAME)

CM 1

CRN 188837-15-2 CMF C14 H22 O4

CM 2

CRN 7398-56-3 CMF C13 H18 O2

CM 3

CRN 4286-23-1 CMF C9 H10 O

CM 4

CRN 1663-39-4 CMF C7 H12 O2

RN 220767-16-8 CAPLUS

CN 2-Propenoic acid, 1,1,4,4-tetramethyl-1,4-butanediyl ester, polymer with 1,1-dimethylethyl 2-propenoate, 4-(1-methylethenyl)phenol and rel-(1R,2R,4R)-1,7,7-trimethylbicyclo[2.2.1]hept-2-yl 2-propenoate (9CI) (CA INDEX NAME)

CM 1

CRN 188837-15-2 CMF C14 H22 O4 Page 113Lee507

CM 2

CRN 5888-33-5 CMF C13 H20 O2

Relative stereochemistry.

CM 3

CRN 4286-23-1 CMF C9 H10 O

CM 4

CRN 1663-39-4 CMF C7 H12 O2

Page 114Lee507

IC ICM G03F007-004 ICS G03F007-039 74-5 (Radiation Chemistry, Photochemistry, and Photographic and Other CC Reprographic Processes) ST chem amplified pos photoresist acrylic polymer IT Photoresists Resists (chem. amplified, pos.; contg. acrylic polymers) IT 220767-14-6, tert-Butyl acrylate-2,5-dimethyl-2,5-hexanediol diacrylate-p-isopropenylphenol-tricyclodecanyl acrylate copolymer 220767-16-8, tert-Butyl acrylate-2,5-dimethyl-2,5-hexanediol diacrylate-p-isopropenylphenol-isobornyl acrylate copolymer tert-Butyl acrylate-2,5-dimethyl-2,5-hexanediol diacrylate-phydroxystyrene-styrene copolymer 220767-20-4, 2,5-Dimethyl-2,5hexanediol diacrylate-p-hydroxystyrene-p-tert-butoxystyrene copolymer 220767-22-6, 2,5-Dimethyl-2,5-hexanediol diacrylate-p-hydroxystyrene-p-(1ethoxyethoxy) styrene copolymer 220767-24-8, 2,5-Dimethyl-2,5-hexanediol diacrylate-p-hydroxystyrene-p-(tert-butoxycarbonyloxy)styrene copolymer 220767-26-0, tert-Butyl acrylate-p-isopropenylphenol-tricyclodecanyl acrylate copolymer RL: TEM (Technical or engineered material use); USES (Uses) (chem. amplified pos. photoresists contg.) 1116-76-3, Trioctylamine 138529-81-4, Bis(cyclohexylsulfonyl)diazomethan IT 144317-44-2 185195-30-6, Bis(4-tert-butylphenyl)iodonium camphorsulfonate RL: TEM (Technical or engineered material use); USES (Uses) (chem. amplified pos. photoresists contg. acrylic polymers and) REFERENCE COUNT: 2 THERE ARE 2 CITED REFERENCES AVAILABLE FOR THIS RECORD. ALL CITATIONS AVAILABLE IN THE RE FORMAT L12 ANSWER 22 OF 34 CAPLUS COPYRIGHT 2003 ACS on STN ACCESSION NUMBER: 1998:742745 CAPLUS DOCUMENT NUMBER: 130:59205 TITLE: Fabrication of shadow mask using UV-curable acrylic back coating with excellent pore sealability INVENTOR (S): Otake, Yasuhisa; Nikaido, Masaru; Hirahara, Sachiko; Kurabayashi, Shigeaki; Suzuki, Nobyuki PATENT ASSIGNEE(S): Toshiba Corp., Japan; Taiyo Ink Seizo K. K. SOURCE: Jpn. Kokai Tokkyo Koho, 17 pp. CODEN: JKXXAF DOCUMENT TYPE: Patent LANGUAGE: Japanese FAMILY ACC. NUM. COUNT: 1 PATENT INFORMATION: PATENT NO. KIND DATE APPLICATION NO. DATE ----------· JP 10308172 A2 19981117 JP 1997-134414 19970508 PRIORITY APPLN. INFO.: JP 1997-134414 19970508 The process involves photolithog. using a UV-curable resin AB

compn. of surface tension 30-50  $\mathrm{mL/m}$  as a back surface-protective coating

### Page 115Lee507

which is applied on a one-side-etched metal bar from the etched side to fill the concaves. After the coating application, the bare surface of the metal bar is etched to form through holes and then removed of the coating and a photoresist. The UV-curable compn. may comprise (a) one-carboxy-and one-(meth)acryloyl-contg. compds., (b) .gtoreq.1-(meth)acryloyl-contg. compds., (c) leveling agents, and (d) photopolymn. initiators.

IT 217190-88-0P

RL: IMF (Industrial manufacture); PRP (Properties); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

(fabrication of shadow mask using UV-curable acrylic back coating with excellent pore sealability)

RN 217190-88-0 CAPLUS

CN 1,2-Benzenedicarboxylic acid, mono[2-[(1-oxo-2-propenyl)oxy]ethyl] ester, polymer with 2-ethyl-2-[[(1-oxo-2-propenyl)oxy]methyl]-1,3-propanediyl di-2-propenoate and rel-(1R,2R,4R)-1,7,7-trimethylbicyclo[2.2.1]hept-2-yl 2-propenoate (9CI) (CA INDEX NAME)

CM 1

CRN 30697-40-6 CMF C13 H12 O6

CM 2

CRN 15625-89-5 CMF C15 H20 O6

CM 3

CRN 5888-33-5 CMF C13 H20 O2 Páge 116Lee507

Relative stereochemistry.

IC ICM H01J009-14

ICS C23F001-00; G03F007-028; C09D004-02

CC 74-13 (Radiation Chemistry, Photochemistry, and Photographic and Other Reprographic Processes) Section cross-reference(s): 42

ST shadow mask photolithog acrylic back coating; pore sealability acrylic shadow mask coating; acryloyloxyethyl phthalate ethylene glycol methacrylate coating

IT Coating materials

(UV-curable; fabrication of shadow mask using UV-curable acrylic back coating with excellent pore sealability)

IT Leveling agents Shadow masks

(fabrication of shadow mask using UV-curable acrylic back coating with excellent pore sealability)

IT 160299-83-2P 217190-83-5P 217190-85-7P 217190-86-8P 217190-87-9P 217190-88-0P 217190-89-1P 217190-90-4P 217312-43-1P

RL: IMF (Industrial manufacture); PRP (Properties); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

(fabrication of shadow mask using UV-curable acrylic back coating with excellent pore sealability)

IT 155683-81-1, BYK 055

RL: MOA (Modifier or additive use); PRP (Properties); TEM (Technical or engineered material use); USES (Uses)

(leveling agent; fabrication of shadow mask using UV-curable acrylic back coating with excellent pore sealability)

IT 24650-42-8

RL: CAT (Catalyst use); USES (Uses)

(photopolymn. initiator; fabrication of shadow mask using UV-curable acrylic back coating with excellent pore sealability)

L12 ANSWER 23 OF 34 CAPLUS COPYRIGHT 2003 ACS on STN

ACCESSION NUMBER:

1998:721577 CAPLUS

DOCUMENT NUMBER:

129:349062

TITLE:

Resist composition and its use for forming

patterns

INVENTOR (S):

Sumino, Motoshige; Fukasawa, Kazuhito; Matsuo,

Takahiro

PATENT ASSIGNEE(S):

Wako Pure Chemical Industries, Ltd, Japan; Matsushita

Electric Industrial Co., Ltd.

Page 117Lee507

SOURCE:

Eur. Pat. Appl., 32 pp.

CODEN: EPXXDW

DOCUMENT TYPE:

Patent

LANGUAGE:

English

FAMILY ACC. NUM. COUNT:

PATENT INFORMATION:

R: AT, BE, CH, DE, DK, ES, FR, GB, GR, IT, LI, LU, NL, SE, MC, PT,

IE, SI, LT, LV, FI, RO

JP 11015164 A2 19990122 JP 1998-136123 19980430 PRIORITY APPLN. INFO.: JP 1997-126402 19970430

AB A resist compn. comprising (a) a polymer having repeating units of the formula -[C(R1)(R2)C(R3)ZOCOR4]- (R1-3 = hydrogen, alkyl, cyano, alkyloxycarbonyl, or carbamoyl; Z = a spacer or a direct link and R = hydroxyalkyl having protected terminal hydroxy), (b) a photoacid generator, and (c) a solvent is effective for forming patterns using an ArF excimer laser.

IT 215382-88-0P

RL: SPN (Synthetic preparation); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

(prepn. and use in photoresists effective for forming patterns using argon fluoride excimer lasers)

RN 215382-88-0 CAPLUS

CN 2-Butenoic acid, 3-methoxy-, 2-[(2-methyl-1-oxo-2-propenyl)oxy]ethyl ester, polymer with [octahydro-5-[[(2-methyl-1-oxo-2-propenyl)oxy]methyl]-4,7-methano-1H-inden-2-yl]methyl 3-methyl-2-butenoate (9CI) (CA INDEX NAME)

CM 1 ·

CRN 215382-86-8 CMF C21 H30 O4

CM 2

CRN 215051-44-8 CMF C11 H16 O5 Page 118Lee507

H<sub>2</sub>C 0  $Me-C-C-O-CH_2-CH_2-O-C-CH=C-Me$ 

IC ICM G03F007-039

74-5 (Radiation Chemistry, Photochemistry, and Photographic and Other CC Reprographic Processes)

ST argon fluoride laser photoresist vinyl polymer

66003-78-9, Triphenylsulfonium trifluoromethanesulfonate IT RL: TEM (Technical or engineered material use); USES (Uses) (photoresists effective for forming patterns using argon fluoride excimer lasers contg. vinyl resins and)

IT 215051-44-8P 215051-47-1P 128692-52-4P 215051-54-0P 215382-86-8P RL: RCT (Reactant); SPN (Synthetic preparation); TEM (Technical or engineered material use); PREP (Preparation); RACT (Reactant or reagent); USES (Uses)

(prepn. and reaction in prepg. resins for photoresists)

IT 215051-56-2P 215382-88-0P 215382-90-4P

RL: SPN (Synthetic preparation); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

(prepn. and use in photoresists effective for forming patterns using argon fluoride excimer lasers)

REFERENCE COUNT:

THERE ARE 1 CITED REFERENCES AVAILABLE FOR THIS RECORD. ALL CITATIONS AVAILABLE IN THE RE FORMAT

Li2 ANSWER 24 OF 34 CAPLUS COPYRIGHT 2003 ACS on STN

1

ACCESSION NUMBER:

1998:721494 CAPLUS

DOCUMENT NUMBER:

129:331157

TITLE:

Acrylic or methacrylic acid derivatives and polymers

therefrom useful for resist compositions used in production of semiconductor devices

INVENTOR(S): PATENT ASSIGNEE(S): Sumino, Motoshige; Fukasawa, Kazuhito

Wako Pure Chemical Industries, Ltd, Japan

SOURCE:

Eur. Pat. Appl., 35 pp. CODEN: EPXXDW

DOCUMENT TYPE:

Patent

LANGUAGE:

English

FAMILY ACC. NUM. COUNT: 1

PATENT INFORMATION:

PATENT NO.				KIND		DATE			APPLICATION NO.					DATE				
			<b></b>						-							<b></b>		
EP	875496			A1		19981104			EP 1998-303332				2	19980429				
EP	875496			B1		20011107										,		
	R:	AT,	BE,	CH,	DE,	DK,	ES,	FR,	GB,	GR	, IT	'. I	JI.	LU.	NL,	SE.	MC	DT
		ΙE,	SI,	LT,	LV,	FI,	RO				•	•		_ ,	,	,	,	11,
TW	4918	60		В		2002	0621		Т	W 1:	998-	871	.069	542	1998	0423		
US	5856	521		Α		1999	0105				998-				1998			
AT	2083	67		Ė		2001	1115		А	T 1	998-	303	332		1998			
JP	1101	2325		A2	2	1999	0119		J	P 1	998-	136	128		1998			
PRIORITY	APP	LN.	INFO.	:				ن	JP 1	997.	-126	391		Α	1997			

Title derivs. have a general formula of R6R7C:CR5ZOCOR, wherein R5, R6, R7 AB = independently hydrogen, alkyl, cyano, alkyloxycarbonyl, or carbamoyl; Z = spacer or direct link; and R = hydroxyalkyl having protected terminal hydroxy. Thus, a resist compn. comprising a polymer prepd. from Me methacrylate, 2-(methacryloyloxy)ethyl 3-methoxy-2-butenoate (prepn. given), and 2-(methacryloyloxy)ethyl acetoacetate was spin-coated on a silicon wafer to give a 0.5 mm-thick resist film, covered with patterned mask, and exposed to ArF excimer laser beams (.lambda. = 193 nm, NA = 0.55) to give a line-and-space pattern. ΙT 215051-59-5P

RL: IMF (Industrial manufacture); POF (Polymer in formulation); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses) (prepn. of acrylic or methacrylic acid derivs. and their polymers for resist compns. useful in prodn. of semiconductor devices)

RN 215051-59-5 CAPLUS

2-Butenoic acid, 3-methoxy-, 2-[(2-methyl-1-oxo-2-propenyl)oxy]ethyl CN ester, polymer with [octahydro-5-[[(2-methyl-1-oxo-2-propenyl)oxy]methyl]-4,7-methano-1H-inden-2-yl]methyl 3-oxobutanoate (9CI) (CA INDEX NAME)

CM 1

CRN 215051-58-4 CMF C20 H28 O5

$$^{\text{H}_2\text{C}}_{\text{Me}-\text{C}-\text{C}-\text{O}-\text{CH}_2}$$

CM

CRN 215051-44-8 CMF C11 H16 O5

IC ICM C07C069-734 ICS C07D317-30; C07D319-06; C08F020-18; G03F007-027

35-2 (Chemistry of Synthetic High Polymers) CC Section cross-reference(s): 76

acrylic methacrylic acid deriv prepn; resist semiconductor ST device methacryloyloxyethyl methoxybutenoate copolymer; methyl methacrylate methacryloyloxyethyl acetoacetate methoxybutenoate copolymer

IT Photoresists Resists Semiconductor devices (prepn. of acrylic or methacrylic acid derivs. and their polymers for resist compns. useful in prodn. of semiconductor devices) 173161-66-5P 215051-53-9P 215051-54-0P 215051-58-4P RL: IMF (Industrial manufacture); RCT (Reactant); PREP (Preparation); RACT (Reactant or reagent) (in monomer prepn.; prepn. of acrylic or methacrylic acid derivs. and their polymers for resist compns. useful in prodn. of semiconductor devices) IT 107-21-1, 1,2-Ethanediol, reactions 126-30-7 149-73-5, Methyl orthoformate 920-46-7, Methacryloyl chloride 21282-97-3 28132-01-6, Tricyclo[5.2.1.02.6]decane-4,8-dimethanol 42822-86-6 RL: RCT (Reactant); RACT (Reactant or reagent) (in monomer prepn.; prepn. of acrylic or methacrylic acid derivs. and their polymers for resist compns. useful in prodn. of semiconductor devices) IT 128692-52-4P 215051-44-8P 215051-47-1P 215051-49-3P 215051-51-7P RL: IMF (Industrial manufacture); PREP (Preparation) (monomer; prepn. of acrylic or methacrylic acid derivs. and their polymers for resist compns. useful in prodn. of semiconductor devices) IT 215051-56-2P 215051-59-5P 215051-60-8P RL: IMF (Industrial manufacture); POF (Polymer in formulation); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses) (prepn. of acrylic or methacrylic acid derivs. and their polymers for resist compns. useful in prodn. of semiconductor devices) REFERENCE COUNT: THERE ARE 1 CITED REFERENCES AVAILABLE FOR THIS 1 RECORD. ALL CITATIONS AVAILABLE IN THE RE FORMAT L12 ANSWER 25 OF 34 CAPLUS COPYRIGHT 2003 ACS on STN ACCESSION NUMBER: 1998:631736 CAPLUS DOCUMENT NUMBER: 129:317081 TITLE: Novel (meth)acrylic acid derivatives and curable compositions therefrom with good heat resistance, water resistance, electric insulation properties and adhesion to substrates INVENTOR(S): Morikawa, Toshiyuki; Fujinobu, Takafumi; Kanefuji, Yuji; Mineyama, Shinobu PATENT ASSIGNEE(S): Yasuhara Chemical K. K., Japan SOURCE: Jpn. Kokai Tokkyo Koho, 13 pp. CODEN: JKXXAF DOCUMENT TYPE: Patent LANGUAGE: Japanese FAMILY ACC. NUM. COUNT: 1 PATENT INFORMATION: PATENT NO. KIND DATE APPLICATION NO. DATE ---------------JP 1997-84448 19970318 JP 10259162 A2 19980929 PRIORITY APPLN. INFO.: JP 1997-84448 19970318

Fage 121Lee507

GI

AB The (meth)acrylic acid derivs. (A) have the base backbone consisting of phenolic compds. contg. cyclic terpene backbones and the curable compns. contg. A are useful for resist inks and coatings or printings on plastics, metals, wood, or paper. Thus, 23.2 g I (prepd. by reaction of 1-p-menthene with phenol) was reacted with 9.1 g acryloyl chloride to give II, 40.0 parts of which were kneaded with 2-hydroxyethyl acrylate 5.0, trimethylolpropane triacrylate 40.0, and 2-ethylanthraquinone 1.0 part to give a solder resist ink. The resist ink was printed onto a flexible Cu-clad laminate and cured by exposure to a high-pressure Hg lamp at 1000 mJ/cm2 to give a laminate showing elec. resistance (JIS Z 3197) 4 .times. 1014 .OMEGA. and water absorption 1.6% after 100 h in boiling water.

IT 214763-47-0P

RL: IMF (Industrial manufacture); PRP (Properties); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

(resist ink; novel (meth)acrylic acid derivs. and curable compns. therefrom with good heat resistance, water resistance, elec. insulation properties and adhesion to substrates)

RN 214763-47-0 CAPLUS

CN 2-Propenoic acid, 2-ethyl-2-[[(1-oxo-2-propenyl)oxy]methyl]-1,3-propanediyl ester, polymer with 2-hydroxyethyl 2-propenoate and rel-2-[4-[(1R,2R,4S)-1,7,7-trimethylbicyclo[2.2.1]hept-2-yl]phenoxy]ethyl 2-propenoate (9CI) (CA INDEX NAME)

CM 1

CRN 214763-46-9 CMF C21 H28 O3

Relative stereochemistry.

CM 2

CRN 15625-89-5 CMF C15 H20 O6

CM 3

CRN 818-61-1 CMF C5 H8 O3

$$\begin{array}{c} \text{O} \\ || \\ \text{HO-CH}_2\text{-CH}_2\text{-O-C-CH} \end{array}$$

IC ICM C07C069-54

. ICS C07C069-54; C07C067-08; C08F020-18; C08F020-20

CC 37-6 (Plastics Manufacture and Processing) Section cross-reference(s): 35, 42, 74, 76

st menthylphenyl acrylate copolymer resist heat resistance; isobornylphenyl ethoxyacrylate copolymer resist heat resistance; water resistance methylphenyl acrylate copolymer; ink resist menthylphenyl acrylate copolymer; circuit board resit menthylphenyl acrylate copolymer; cyclic terpene acrylate copolymer elec insulator; coating cyclic terpene acrylate copolymer; printing ink cyclic terpene acrylate copolymer

```
ŦΤ
      Polyurethanes, preparation
      RL: IMF (Industrial manufacture); PRP (Properties); TEM (Technical or
      engineered material use); PREP (Preparation); USES (Uses)
         (acrylates, resist inks; novel (meth)acrylic acid derivs. and
         curable compns. therefrom with good heat resistance, water resistance,
         elec. insulation properties and adhesion to substrates)
 IT
      Polyurethanes, preparation
      Polyurethanes, preparation
     RL: IMF (Industrial manufacture); PRP (Properties); TEM (Technical or
      engineered material use); PREP (Preparation); USES (Uses)
         (epoxy, resist inks; novel (meth)acrylic acid derivs. and
         curable compns. therefrom with good heat resistance, water resistance,
         elec. insulation properties and adhesion to substrates)
     Water-resistant materials
 IT
     Water-resistant materials
         (heat-resistant; novel (meth)acrylic acid derivs. and curable compns.
        therefrom with good heat resistance, water resistance, elec. insulation
        properties and adhesion to substrates)
TΤ
     Coating materials
     Electric insulators
     Printed circuit boards
     Solder resists
         (novel (meth)acrylic acid derivs. and curable compns. therefrom with
        good heat resistance, water resistance, elec. insulation properties and
        adhesion to substrates)
IT
     Epoxy resins, preparation
     Epoxy resins, preparation
     RL: IMF (Industrial manufacture); PRP (Properties); TEM (Technical or
     engineered material use); PREP (Preparation); USES (Uses)
        (polyurethane-, resist inks; novel (meth)acrylic acid derivs.
        and curable compns. therefrom with good heat resistance, water
        resistance, elec. insulation properties and adhesion to substrates)
IT
     Inks
        (printing; novel (meth)acrylic acid derivs. and curable compns.
        therefrom with good heat resistance, water resistance, elec. insulation
        properties and adhesion to substrates)
IT
     Heat-resistant materials
     Heat-resistant materials
        (water-resistant; novel (meth)acrylic acid derivs. and curable compns.
        therefrom with good heat resistance, water resistance, elec. insulation
        properties and adhesion to substrates)
IT
     4488-58-8P
                  13150-01-1P
    RL: IMF (Industrial manufacture); RCT (Reactant); PREP (Preparation); RACT
     (Reactant or reagent)
        (intermediate; novel (meth)acrylic acid derivs. and curable compns.
        therefrom with good heat resistance, water resistance, elec. insulation
       properties and adhesion to substrates)
    50-00-0, Formaldehyde, reactions 75-21-8, Oxirane, reactions
    2-Propenoic acid, reactions
                                  79-92-5, Camphene
                                                       108-95-2, Phenol,
                 814-68-6, Acryloyl chloride
                                               5502-88-5, 1-p-Menthene
    RL: RCT (Reactant); RACT (Reactant or reagent)
        (intermediate; novel (meth) acrylic acid derivs. and curable compns.
```

therefrom with good heat resistance, water resistance, elec. insulation properties and adhesion to substrates)

IT 214763-44-7P 214763-46-9P

RL: IMF (Industrial manufacture); PREP (Preparation)
 (novel (meth)acrylic acid derivs. and curable compns. therefrom with
 good heat resistance, water resistance, elec. insulation properties and
 adhesion to substrates)

IT 101-68-8DP, reaction products with 2-hydroxyethyl acrylate and cyclic terpene-based phenolic compds., copolymers with acrylates 214763-45-8P 214763-47-0P

RL: IMF (Industrial manufacture); PRP (Properties); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

(resist ink; novel (meth)acrylic acid derivs. and curable compns. therefrom with good heat resistance, water resistance, elec. insulation properties and adhesion to substrates)

IT 106-89-8DP, reaction products with acrylic acid and cyclic terpene-based phenolic compds., polymers with acrylates 818-61-1DP, reaction products with MDI and cyclic terpene-based phenolic compds., polymers with acrylates 15625-89-5DP, Trimethylolpropane triacrylate, copolymers with acrylates

RL: IMF (Industrial manufacture); PRP (Properties); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)
 (resist inks; novel (meth)acrylic acid derivs. and curable

compns. therefrom with good heat resistance, water resistance, elec. insulation properties and adhesion to substrates)

L12 ANSWER 26 OF 34 CAPLUS COPYRIGHT 2003 ACS on STN

ACCESSION NUMBER: 1998:298164 CAPLUS

DOCUMENT NUMBER: 129:60665

TITLE: Color filter materials having high transparency and

low reflectance and high-definition color filters for

liquid crystal displays

INVENTOR(S): Kazama, Shingo; Toki, Koichi; Teramoto, Takeo

PATENT ASSIGNEE(S): Nippon Steel Chemical Co., Ltd., Japan; Nippon Steel

Corp.

SOURCE: Jpn. Kokai Tokkyo Koho, 12 pp.

CODEN: JKXXAF

DOCUMENT TYPE:

LANGUAGE:

Patent Japanese

FAMILY ACC. NUM. COUNT: 1

PATENT INFORMATION:

PATENT NO. KIND DATE APPLICATION NO. DATE

JP 10123311 A2 19980515 JP 1996-274867 19961017

PRIORITY APPLN. INFO.: JP 1996-274867 19961017

AB Title materials, useful for protective films, color inks, and black resists for color filters, contain alkali-sol resins (Mw >1000) comprising aliph. polycyclic compds. H2C:CRXA [R = H, Me; X = divalent group, direct bond; A = (un)substituted aliph. polycyclic hydrocarbonyl] 15-70, (meth)acrylic acid 15-70, and comonomers 0-45 mol%. Thus, 2 g 40:40:20 mol% isobornyl methacrylate-methacrylic acid-hydroxyethyl

methacrylate copolymer oligomer (Mw 9000) were mixed with Et cellosolve 12, Kayarad DPHA 1, Kayarad PET 30 1, Sila-Ace S 510 0.04, Celloxide 2021P 0.359, and Irgacure 907 0.06 g to give a compn, which formed coating films showing light transmittance 98% at 400 nm.

IT 208471-84-5P

RL: DEV (Device component use); IMF (Industrial manufacture); PRP (Properties); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

(photosensitive resin materials having high transparency and low reflectance for color filters of liq. crystal displays)

RN 208471-84-5 CAPLUS

2-Propenoic acid, 2-methyl-, polymer with 2-hydroxyethyl
2-methyl-2-propenoate, 2-(hydroxymethyl)-2-[[(1-oxo-2-propenyl)oxy]methyl]1,3-propanediyl di-2-propenoate, 2,2'-[oxybis(methylene)]bis[2(hydroxymethyl)-1,3-propanediol] 2-propenoate and rel-(1R,2R,4R)-1,7,7trimethylbicyclo[2.2.1]hept-2-yl 2-propenoate (9CI) (CA INDEX NAME)

CM 1

CN

CRN 5888-33-5 CMF C13 H20 O2

Relative stereochemistry.

CM 2

CRN 3524-68-3 CMF C14 H18 O7

CM 3

CRN 868-77-9

Page 126Lee507

CMF C6 H10 O3

. CM 4

CRN 79-41-4 CMF C4 H6 O2

CM 5

CRN 77641-99-7 CMF C10 H22 O7 . x C3 H4 O2

CM 6

CRN 126-58-9 CMF C10 H22 O7

CM 7

CRN 79-10-7 CMF C3 H4 O2

IC ICM G02B005-20

KOROMA EIC1700

```
ICS C08L033-02; C08L033-04; G03F007-027; G03F007-028; G03F007-033
       74-13 (Radiation Chemistry, Photochemistry, and Photographic and Other
  CC
       Reprographic Processes)
      Section cross-reference(s): 42
      liq crystal display color filter transparency; reflectance acrylic resin
  ST
      color filter; acrylic resin color filter transparency
  IT
      Coating materials
      Inks
      Liquid crystal displays
      Optical filters
         (photosensitive resin materials having high transparency and low
         reflectance for color filters of liq. crystal displays)
 IT
      Acrylic polymers, properties
      RL: IMF (Industrial manufacture); PRP (Properties); TEM (Technical or
      engineered material use); PREP (Preparation); USES (Uses)
         (photosensitive resin materials having high transparency and low
         reflectance for color filters of liq. crystal displays)
 ΙT
      208471-83-4P 208471-84-5P
                                 208471-85-6P
                                                208471-86-7P
      RL: DEV (Device component use); IMF (Industrial manufacture); PRP
      (Properties); TEM (Technical or engineered material use); PREP
      (Preparation); USES (Uses)
         (photosensitive resin materials having high transparency and low
         reflectance for color filters of liq. crystal displays)
 IT
      28136-81-4P
                   31693-08-0P, Hydroxyethyl methacrylate-methacrylic acid
      copolymer
                184640-97-9P
                                199105-60-7P
     RL: IMF (Industrial manufacture); PREP (Preparation)
         (photosensitive resin materials having high transparency and low
        reflectance for color filters of liq. crystal displays)
L12 ANSWER 27 OF 34 CAPLUS COPYRIGHT 2003 ACS on STN
ACCESSION NUMBER:
                         1996:631745 CAPLUS
DOCUMENT NUMBER:
                         125:278139
TITLE:
                         Manufacture of phenolic resins and epoxy resins for
                         laminates, sealants, and solder resists and
                         photocurable compositions
INVENTOR (S):
                         Ootsuki, Yutaka; Yuasa, Hitoshi; Oshimi, Fumiaki;
                         Enomoto, Masami
PATENT ASSIGNEE(S):
                        Nippon Oil Co Ltd, Japan
SOURCE:
                        Jpn. Kokai Tokkyo Koho, 22 pp.
                        CODEN: JKXXAF
DOCUMENT TYPE:
                        Patent
LANGUAGE:
                        Japanese
FAMILY ACC. NUM. COUNT:
PATENT INFORMATION:
     PATENT NO.
                    KIND DATE
                                        APPLICATION NO. DATE
     -----
                                         -----
     JP 08208812
                     . A2
                         19960813
                                         JP 1995-20666
                                                          19950208
     JP 3292616
                     B2 20020617
     JP 2002265561
                    A2 20020918
                                         JP 2002-12561 19950208
PRIORITY APPLN. INFO.:
                                       JP 1995-20666
                                                     A3 19950208
    Epoxy resin compns. are obtained from epihalohydrins and phenolic resins
```

prepd. by treating (A) olefins comprising 10-90% C4-5 conjugated diene polymers and 10-90% C4-15 hydrocarbon dienes with (B) phenols in the presence of acid catalysts. Photocurable compns. contain photocurable polymers obtained from the epoxy resins, (meth)acrylic acids, and .alpha.,.beta.-dicarboxylic acid anhydrides and photopolymn. initiators. Thus, 100 parts copolymer obtained from PhOH, Nisseki B 700, and dicyclopentadiene and 12 parts hexamethylenetetramine were mixed with glass fibers 145, wollastonite 90, Mg stearate 1, and carbon black 5 parts, melt kneaded, and pressed to give a test piece showing good heat resistance and low water absorption.

IT 182508-76-5P 182508-77-6P 182508-78-7P

RL: IMF (Industrial manufacture); PRP (Properties); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

(manuf. of phenolic resins and epoxy resins for laminates, sealants, and photocurable solder resists)

RN 182508-76-5 CAPLUS

2-Propenoic acid, 2-[[3-[(1-oxo-2-propenyl)oxy]-2,2-bis[[(1-oxo-2-propenyl)oxy]methyl]propoxy]methyl]-2-[[(1-oxo-2-propenyl)oxy]methyl]-1,3-propanediyl ester, polymer with 1,3-butadiene, (chloromethyl)oxirane, Epo Tohto YDCN 702 2-propenoate, hexahydro-1,3-isobenzofurandione, phenol and 3a,4,7,7a-tetrahydro-4,7-methano-1H-indene (9CI) (CA INDEX NAME)

CM 1

CN

CRN 29570-58-9 CMF C28 H34 O13

CM 2

CRN 108-95-2 CMF C6 H6 O

CM 3

CRN 106-99-0 CMF C4 H6

н₂с= сн- сн= сн₂

CM 4

CRN 106-89-8 CMF C3 H5 Cl O

CM 5

CRN 85-42-7 CMF C8 H10 O3

CM 6

CRN 77-73-6 CMF C10 H12

CM 7

CRN 126040-06-0

CMF C3 H4 O2 . x Unspecified

CM 8

CRN 109190-39-8

CMF Unspecified

CCI PMS, MAN

# \*\*\* STRUCTURE DIAGRAM IS NOT AVAILABLE \*\*\*

CM 9

CRN 79-10-7

CMF C3 H4 O2

RN 182508-77-6 CAPLUS

CN 2-Propenoic acid, 2-[[3-[(1-oxo-2-propenyl)oxy]-2,2-bis[[(1-oxo-2-propenyl)oxy]methyl]propoxy]methyl]-2-[[(1-oxo-2-propenyl)oxy]methyl]-1,3-propanediyl ester, polymer with 1,3-butadiene, (chloromethyl)oxirane, Epo Tohto YDCN 702 2-propenoate, hexahydro-1,3-isobenzofurandione, 2-methylphenol and 3a,4,7,7a-tetrahydro-4,7-methano-1H-indene (9CI) (CA INDEX NAME)

CM 1

CRN 29570-58-9 CMF C28 H34 O13

CM 2

Page 131Lee507

CRN 106-99-0 CMF C4 H6

 $H_2C = CH - CH = CH_2$ 

CM 3

CRN 106-89-8 CMF C3 H5 Cl O

CH<sub>2</sub>-Cl

CM 4

CRN 95-48-7 CMF C7 H8 O

CM 5

CRN 85-42-7 CMF C8 H10 O3

CM 6

CRN 77-73-6 CMF C10 H12

KOROMA EIC1700

CM 7

CRN 126040-06-0

CMF C3 H4 O2 . x Unspecified

CM 8

CRN 109190-39-8

CMF Unspecified

CCI PMS, MAN

\*\*\* STRUCTURE DIAGRAM IS NOT AVAILABLE \*\*\*

CM 9

CRN 79-10-7 CMF C3 H4 O2

O || || HO- C- CH---- CH2

RN 182508-78-7 CAPLUS

CN 2-Propenoic acid, 2-[[3-[(1-oxo-2-propenyl)oxy]-2,2-bis[[(1-oxo-2-propenyl)oxy]methyl]propoxy]methyl]-2-[[(1-oxo-2-propenyl)oxy]methyl]-1,3-propanediyl ester, polymer with 1,3-butadiene polymer with (chloromethyl)oxirane, phenol and 3a,4,7,7a-tetrahydro-4,7-methano-1H-indene 2-propenoate, dihydro-2,5-furandione and Epo Tohto YDCN 704 (9CI) (CA INDEX NAME)

CM 1

CRN 94362-50-2

CMF Unspecified

CCI MAN

\*\*\* STRUCTURE DIAGRAM IS NOT AVAILABLE \*\*\*

CM 2

CRN 29570-58-9

CMF C28 H34 O13

Page 133Lee507

CM 3

CRN 108-30-5 CMF C4 H4 O3

CM 4

CRN 182508-72-1 CMF (C10 H12 . C6 H6 O . C4 H6 . C3 H5 Cl O)x . x C3 H4 O2

CM 5

CRN 79-10-7 CMF C3 H4 O2

CM 6

CRN 182281-41-0

CMF (C10 H12 . C6 H6 O . C4 H6 . C3 H5 Cl O)  $\times$ 

CCI PMS

CM 7

## Page 134Lee507

CRN 108-95-2 CMF C6 H6 O

CM 8

CRN 106-99-0 CMF C4 H6

 $H_2C = CH - CH = CH_2$ 

CM 9

CRN 106-89-8 CMF C3 H5 Cl O

CM 10

CRN 77-73-6 CMF C10 H12



IC ICM C08G061-00

ICS C08G059-06; C08G059-14; C08G059-18; C08K005-00; C08L063-00;
C08L065-00; G03F007-027; G03F007-028; G03F007-038; H01L023-29;
H01L023-31; H05K003-18; H05K003-28

CC 38-3 (Plastics Fabrication and Uses)

Section cross-reference(s): 42, 74

ST butadiene phenolic resin heat resistance; water resistance butadiene phenolic resin; epoxy resin laminate heat resistance; sealant epoxy resin

```
heat resistance; solder resist epoxy resin photocurable
 IT
      Chemically resistant materials
      Crosslinking agents
      Heat-resistant materials
      Sealing compositions
      Water-resistant materials
         (manuf. of phenolic resins and epoxy resins for laminates, sealants,
         and photocurable solder resists)
 IT
      Epoxy resins, uses
      Phenolic resins, uses
      RL: IMF (Industrial manufacture); TEM (Technical or engineered material
      use); PREP (Preparation); USES (Uses)
         (manuf. of phenolic resins and epoxy resins for laminates, sealants,
         and photocurable solder resists)
 IT
     Crosslinking
         (photochem., manuf. of phenolic resins and epoxy resins for laminates,
         sealants, and photocurable solder resists)
 TT
     Resists
         (solder, manuf. of phenolic resins and epoxy resins for laminates,
         sealants, and photocurable solder resists)
 ΙT
     182281-48-7P 182281-49-8P 182281-50-1P 182281-51-2P
                                                                 182281-52-3P
     182281-53-4P 182281-54-5P 182281-55-6P 182281-56-7P
                                                                 182281-57-8P
     182281-59-0P 182281-61-4P 182281-64-7P 182281-67-0P
                                                                 182281-70-5P
     182281-73-8P 182282-17-3P 182282-18-4P 182508-76-5P
     182508-77-6P 182508-78-7P
     RL: IMF (Industrial manufacture); PRP (Properties); TEM (Technical or
     engineered material use); PREP (Preparation); USES (Uses)
         (manuf. of phenolic resins and epoxy resins for laminates, sealants,
        and photocurable solder resists)
     163149-15-3P, Butadiene-dicyclopentadiene-phenol copolymer 182281-41-0P,
IT
     Butadiene-dicyclopentadiene-epichlorohydrin-phenol copolymer
     182281-42-1P, Butadiene-o-cresol-dicyclopentadiene copolymer
                  182281-44-3P, Butadiene-phenol-vinylcyclohexene copolymer
     182281-43-2P
     182281-45-4P 182281-46-5P
                                   182281-47-6P
                                                 182508-73-2P
                                                                 182508-75-4P,
     YDCN 702 acrylate-hexahydrophthalic anhydride copolymer
     RL: IMF (Industrial manufacture); TEM (Technical or engineered material
     use); PREP (Preparation); USES (Uses)
        (manuf. of phenolic resins and epoxy resins for laminates, sealants,
        and photocurable solder resists)
L12 ANSWER 28 OF 34 CAPLUS COPYRIGHT 2003 ACS on STN
ACCESSION NUMBER:
                         1995:586359 CAPLUS
DOCUMENT NUMBER:
                         122:315354
TITLE:
                         Photopolymerization initiators for photocurable
                         compositions
INVENTOR(S):
                        Lin, Samuel Q.; Humphreys, Robert W. R.
PATENT ASSIGNEE(S):
                        Loctite Corp., USA
SOURCE:
                         Jpn. Kokai Tokkyo Koho, 12 pp.
                         CODEN: JKXXAF
DOCUMENT TYPE:
                        Patent
LANGUAGE:
                        Japanese
FAMILY ACC. NUM. COUNT: 1
```

### Page 136Lee507

### PATENT INFORMATION:

PATENT NO. KIND DATE APPLICATION NO. DATE

JP 06293803 A2 19941021 JP 1993-321272 19931126

PRIORITY APPLN. INFO.: JP 1993-321272 19931126

The compns. consist of photocurable compds. and polymers having initiator end groups QR8R5- [QR8 = branched arom.-aliph. ketone residue; R8 = alkylene, alkenylene, alkyleneoxy, oxy; R5 = Si(R6)2[OSi(R6)2]n; R6 = org. group, halo; n = 0, integer].

IT 163518-27-2P

RL: IMF (Industrial manufacture); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)
(polymeric photoinitiators for manuf. of)

RN 163518-27-2 CAPLUS

CN 2-Propenoic acid, 2-methyl-, cyclohexyl ester, polymer with 1,3-butadiene, 2-(hydroxymethyl)-2-[[(1-oxo-2-propenyl)oxy]methyl]-1,3-propanediyl di-2-propenoate and exo-1,7,7-trimethylbicyclo[2.2.1]hept-2-yl 2-methyl-2-propenoate, graft (9CI) (CA INDEX NAME)

CM 1

CRN 7534-94-3 CMF C14 H22 O2

Relative stereochemistry.

CM 2

CRN 3524-68-3 CMF C14 H18 O7

```
Page 137Lee507
     CM
          3
     CRN 106-99-0
     CMF C4 H6
H_2C = CH - CH = CH_2
     CM
     CRN 101-43-9
     CMF C10 H16 O2
            CH<sub>2</sub>
       O- C- C- Me
IC
     ICM C08F002-50
ICA C08F008-42; C08F299-08; C08G077-42
CC
     35-3 (Chemistry of Synthetic High Polymers)
ST
     photopolymn initiator photocurable compn
IT
     Adhesives
     Coating materials
        (UV-curable, contg. polymeric photopolymn. initiators)
IT
     Polymerization catalysts
        (graft, photochem., prepn. of polymeric photopolymn. initiators)
IT
     Rubber, synthetic
     RL: CAT (Catalyst use); SPN (Synthetic preparation); PREP (Preparation);
     USES (Uses)
        (isoprene-styrene, block, triblock, reaction products, with
        siloxane-contg. benzoin derivs.; prepn. of polymeric photopolymn.
        initiators)
ΙŤ
     Rubber, butadiene, preparation
     RL: CAT (Catalyst use); SPN (Synthetic preparation); PREP (Preparation);
    USES (Uses)
        (of cis-1,4-configuration, reaction products, with siloxane-contg.
        benzoin derivs.; prepn. of polymeric photopolymn. initiators)
IT
    Resists
        (photo-, UV, contg. polymeric photopolymn. initiators)
IT
     Polymerization catalysts
        (photochem., prepn. of polymeric photopolymn. initiators)
ΙT
    Polymerization catalysts
        (polyfunctional, prepn. of polymeric photopolymn. initiators)
IT
    Siloxanes and Silicones, preparation
    RL: CAT (Catalyst use); SPN (Synthetic preparation); PREP (Preparation);
```

USES (Uses)

```
(reaction products, with siloxane-contg. benzoin derivs.; prepn. of
        polymeric photopolymn. initiators)
IT
     107439-29-2P, Butadiene-methyl methacrylate graft copolymer
     163518-27-2P
     RL: IMF (Industrial manufacture); TEM (Technical or engineered material
     use); PREP (Preparation); USES (Uses)
        (polymeric photoinitiators for manuf. of)
ΙŤ
     9003-17-2DP, Butarez NF, reaction products with siloxane-contg. benzoin
               121698-02-0DP, reaction products with siloxane-contq. benzoin
              155665-02-4DP, Dimethylsilanediol-methylvinylsilanediol
     copolymer, reaction products with siloxane-contq. benzoin derivs.
     RL: CAT (Catalyst use); SPN (Synthetic preparation); PREP (Preparation);
        (prepn. of polymeric photopolymn. initiators)
IT
     98-86-2, Acetophenone, reactions 106-95-6, Allyl bromide, reactions
     108-94-1, Cyclohexanone, reactions 574-09-4, Benzoin ethyl ether
     1066-35-9, Chlorodimethylsilane 3524-62-7, Benzoin methyl ether
     7677-24-9, Trimethylsilyl cyanide 40663-68-1, p-(Allyloxy)benzaldehyde
     RL: RCT (Reactant); RACT (Reactant or reagent)
        (prepn. of polymeric photopolymn. initiators)
IT
     26595-39-1P, .alpha.-Allylbenzoin ethyl ether
                                                    27984-20-9P,
     4-Penten-1-one, 2-methoxy-1,2-diphenyl- 104120-96-9P 104120-97-0P
     104120-98-1P 104140-50-3P
                                  104140-51-4P
                                                 104140-52-5P
                                                               104140-53-6P
     104140-54-7P 114450-99-6P
                                  163518-28-3P
     RL: RCT (Reactant); SPN (Synthetic preparation); PREP (Preparation); RACT
     (Reactant or reagent)
        (prepn. of polymeric photopolymn. initiators)
IT
     104140-55-8DP, reaction products with polybutadiene
     RL: SPN (Synthetic preparation); PREP (Preparation)
        (prepn. of polymeric photopolymn. initiators)
ΙŤ
     9003-17-2P
     RL: CAT (Catalyst use); SPN (Synthetic preparation); PREP (Preparation);
     USES (Uses)
        (rubber, of cis-1,4-configuration, reaction products, with
        siloxane-contg. benzoin derivs.; prepn. of polymeric photopolymn.
L12 ANSWER 29 OF 34 CAPLUS COPYRIGHT 2003 ACS on STN
ACCESSION NUMBER:
                        1994:166897 CAPLUS
DOCUMENT NUMBER:
                        120:166897
TITLE:
                        UV-curable resin compositions for electrically
                         insulating coatings and colorant compositions
                         containing them
INVENTOR (S):
                        Aratama, Nobuo
PATENT ASSIGNEE(S):
                        Za Inku Tetsuku Kk, Japan
SOURCE:
                        Jpn. Kokai Tokkyo Koho, 6 pp.
                         CODEN: JKXXAF
DOCUMENT TYPE:
                        Patent
                         Japanese
LANGUAGE:
FAMILY ACC. NUM. COUNT: 1
PATENT INFORMATION:
```

The UV-curable resin compns. with good adhesion to metals, useful as resist inks, insulating coatings, etc., comprise phosphate-modified epoxy (meth)acrylates 10-70, phosphate-modified (meth)acrylates 0-20, monofunctional (meth)acrylates 10-70, polyfunctional (meth)acrylates 5-20, photoinitiators 1-15, and polymn. inhibitors 0-1%. The compns. optionally contain 0.01-50% pigments as coloring and thickening agents. A mixt. of Ripoxy SP 6000 (phosphate-modified epoxy acrylate) 45, Light Ester PA 3, SR 506 45, Kayarad TMPTA 10, Irgacure 184 7, and hydroquinone 0.01 part showed viscosity 500 cP and gave a cured coating showing pencil hardness 3H, cross-cut adhesion 100/100, and elec. resistance 3.0 .times. 1012 .OMEGA..

IT 153515-81-2

RL: USES (Uses)

(photocurable, for elec. insulating coatings and inks with adhesion to metal)

RN 153515-81-2 CAPLUS

CN 2-Propenoic acid, 2-ethyl-2-[[(1-oxo-2-propenyl)oxy]methyl]-1,3propanediyl ester, polymer with 2-(phosphonooxy)ethyl 2-propenoate,
exo-1,7,7-trimethylbicyclo[2.2.1]hept-2-yl 2-propenoate and Ripoxy SP 6000
(9CI) (CA INDEX NAME)

CM 1

CRN 153302-21-7 CMF Unspecified CCI PMS, MAN

\*\*\* STRUCTURE DIAGRAM IS NOT AVAILABLE \*\*\*

CM 2

CRN 32120-16-4 CMF C5 H9 O6 P

O || H<sub>2</sub>O<sub>3</sub>PO-CH<sub>2</sub>-CH<sub>2</sub>-O-C-CH<del>----</del>CH<sub>2</sub>

CM 3

CRN 15625-89-5 CMF C15 H20 O6

CM 4

CRN 5888-33-5 CMF C13 H20 O2

Relative stereochemistry.

IC ICM C08F299-02 ICS C08F002-50

CC 42-7 (Coatings, Inks, and Related Products) Section cross-reference(s): 38, 74

ST elec insulator coating acrylate photocuring; epoxy acrylate coating elec insulator; metal acrylate coating photocuring insulator; phosphate epoxy acrylate coating insulator; colorant acrylate coating photocuring insulator; adhesion acrylate photocuring coating insulator

IT Polymerization inhibitors

(UV-curable epoxy acrylate compns. contg., for elec. insulating coatings and inks)

IT Carbon black, uses

RL: USES (Uses)

(pigments, UV-curable acrylate compns. contg., for elec. insulating coatings and inks)

IT Coating materials

(UV-curable, epoxy acrylate-based, with adhesion to metals)

IT Epoxy resins, compounds

RL: USES (Uses)

(acrylates, UV-curable, for elec. insulating coatings and inks with adhesion to metals)

IT Electric insulators and Dielectrics

(coatings, UV-curable acrylate compns., with adhesion to metals)

IT Polymerization catalysts

(photochem., UV-curable epoxy acrylate compns. contg., for elec.

insulating coatings and inks)

IT Crosslinking

(photochem., epoxy acrylate compns. for, for elec. insulating coatings and inks)

IT Inks

(printing, UV-curable, epoxy acrylate-based, elec. insulating, with adhesion to metals)

IT 39362-79-3, 42 Alloy

RL: USES (Uses)

(coatings and inks for, UV-curable acrylate compns. as, adherent)

IT 153218-49-6 153452-24-5 153515-81-2

RL: USES (Uses)

(photocurable, for elec. insulating coatings and inks with adhesion to metal)

IT 947-19-3, Irgacure 184

RL: USES (Uses)

(photoinitiators, in epoxy acrylate compns. for elec. insulating coatings and inks)

IT 7727-43-7, Barium sulfate

RL: USES (Uses)

(pigments, in photocurable acrylate compns. for elec. insulating coatings and inks)

IT 123-31-9, Hydroquinone, uses

RL: USES (Uses)

(polymn. inhibitors, in photocurable acrylate compns. for elec. insulating coatings and inks)

L12 ANSWER 30 OF 34 CAPLUS COPYRIGHT 2003 ACS on STN

ACCESSION NUMBER: 1993:136238 CAPLUS

DOCUMENT NUMBER: 118:136238

TITLE: Patterning of gold film

INVENTOR(S): Kushi, Kenji; Inukai, Kenichi; Izeki, Takayuki;

Fujimoto, Yasuyuki; Koyanagi, Seiya

PATENT ASSIGNEE(S): Mitsubishi Rayon Co., Ltd., Japan SOURCE: Jpn. Kokai Tokkyo Koho, 11 pp.

CODEN: JKXXAF

DOCUMENT TYPE: Patent LANGUAGE: Japanese

FAMILY ACC. NUM. COUNT: 1

PATENT INFORMATION:

PATENT NO. KIND DATE APPLICATION NO. DATE

JP 04039664 A2 19920210 JP 1990-146086 19900606

PRIORITY APPLN. INFO.: JP 1990-146086 19900606

AB The title patterning has the steps of: (1) forming an alkali-developable photosensitive resin interlayer on a metal substrate; (2) laminating an alkali-developable dry-resist film; (3) effecting imagewise exposure of the aforementioned 2 films to harden them, and developing them with an alkali developer to remove an unexposed region; and (4) effecting electroplating of Au. This patterning is characterized by use of said photosensitive resin interlayer which with an acid value 10-100, contains

#### Page 142Lee507

(a) a copolymer which as a thermoplastic binder and with glass transition temp. 60-100.degree., is made up of (1) Ph-C(R):CH2 [R = H, Cl-6 alkyl, halo] 3-30%, (2) .gtoreq.1 compd. 15-45% selected from Cl-6 alkyl acrylate and C2-6 hydroxy alkyl acrylate, (3) .gtoreq.1 compd. 25-60% selected from Cl-6 alkyl methacrylate, and (3) C2-6 hydroxy methacrylate, C3-15 .alpha., .beta.-unsatd. COOH-bearing monomer(s) 15-35%, (b) a monomer 25-50% contg. .gtoreq.1 OH and .gtoreq.2 ethylenic unsatd. moieties, and (c) a photopolymn. initiator 0-10%. This patterning can be used in fabrication of a printed circuit board.

IT 146057-34-3

RL: USES (Uses)

(alkali-developable photosensitive resin film, patterning of gold film by)

RN 146057-34-3 CAPLUS

CN 2-Propenoic acid, polymer with 2,2-dimethyl-1,3-propanediyl di-2-propenoate, 2,5-furandione, 2,2'-[(1-methylethylidene)bis(4,1-phenyleneoxymethylene)]bis[oxirane] and 2-(3a,4,7,7a-tetrahydro-4,7-methano-1H-indenyl)ethyl 2-propenoate (9CI) (CA INDEX NAME)

CM 1

CRN 130725-08-5 CMF C15 H18 O2 CCI IDS

$$0 \\ || \\ D1-CH_2-CH_2-O-C-CH == CH_2$$

CM 2

CRN 2223-82-7 CMF C11 H16 O4

Page 143Lee507

CM 3

CRN 1675-54-3 CMF C21 H24 O4

$$\begin{array}{c|c} O & \\ \hline \\ CH_2 - O \\ \hline \\ Me \end{array} \begin{array}{c} Me \\ \hline \\ CH_2 \\ \hline \\ O - CH_2 \\ \hline \\ \\ Me \end{array}$$

CM 4

CRN 108-31-6 CMF C4 H2 O3

CM 5

CRN 79-10-7 CMF C3 H4 O2

IC ICM G03F007-027

ICS G03F007-26; G03F007-40; H01L021-027; H05K003-24

ICA H05K003-18

CC 74-5 (Radiation Chemistry, Photochemistry, and Photographic and Other Reprographic Processes) Section cross-reference(s): 76

ST patterning gold film photosensitive resin

IT Epoxy resins, uses

RL: USES (Uses)

(novolak-type, acrylated, alkali-developable photosensitive resin film, patterning of gold film by)

IT Resists

(photo-, patterning of gold film by)

TT 79-10-7D, 2-Propenoic acid, acrylated, reaction product with succinic anhydride 108-30-5D, Succinic anhydride, acrylated, reaction product

#### Page 144Lee507

with acrylic acid 2223-82-7D, Neopentyl glycol diacrylate, reaction product with epoxy resin 16969-10-1D, 3-Phenoxy-2-hydroxypropy1 acrylate, reaction product with epoxy resin 130725-08-5D, reaction product with epoxy resin 146057-30-9 146057-31-0 146057-32-1 146057-33-2 146057-34-3 146057-35-4

RL: USES (Uses)

(alkali-developable photosensitive resin film, patterning of gold film by)

IT 146057-25-2 146057-26-3 146057-27-4 146057-28-5 146057-29-6 146332-21-0

RL: USES (Uses)

(dry-resist film, patterning of gold film by)

IT 7440-57-5, Gold, uses

RL: USES (Uses)

(film, patterning of, by using photoresist film)

L12 ANSWER 31 OF 34 CAPLUS COPYRIGHT 2003 ACS on STN

ACCESSION NUMBER:

1992:532488 CAPLUS

DOCUMENT NUMBER:

117:132488

TITLE:

Light-transmitting material and its manufacture, and

resin compositions for claddings for

light-transmitting materials

INVENTOR(S):

Hashimoto, Yutaka; Shiraga, Jun; Kamei, Masayuki

PATENT ASSIGNEE(S):

Dainippon Ink and Chemicals, Inc., Japan

SOURCE:

Jpn. Kokai Tokkyo Koho, 40 pp.

CODEN: JKXXAF

DOCUMENT TYPE:

Patent

LANGUAGE:

Japanese

FAMILY ACC. NUM. COUNT: 1

PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO. DATE
JP 03289605	A2	19911219	JP 1990-255998 19900926
JP 3044767	B2	20000522	
ORITY APPLN. INFO.	:		JP 1989-251026 A1 19890927

PRI JP 1990-71220 A1 19900320

AΒ Title materials, e.g., optical fibers, showing good transmission characteristics and high-resoln. image transmission comprise a no. of cores embedded in a light-diffusing cladding with lower refractive index than the core. A light-transmitting material was prepd. by the photolithog. method from a photocurable core compn. [giving cured product with refractive index 1.526 and transmission loss 0.13 dB/cm (633 nm)] comprising dicyclopentadienediol-phthalic acid copolymer diacrylate 70, dicyclopentanyl acrylate 10, neopentyl glycol diacrylate 20, and 1-hydroxycyclohexyl Ph ketone 2 parts and clad with a photocurable compn. (giving cured product with light transmittance 85% and refractive index 1.401) comprising CH2:CHCO2CH2CH2C8F17 75.6, trimethylolpropane triacrylate 11.4, dipentaerythritol hexaacrylate 10.0, 3-mercaptopropyltrimethoxysilane 2.0, and 1-hydroxycyclohexyl Ph ketone 1.0 part to give a product with resoln. 12/mm and aperture 0.60.

142957-80-0P 142957-83-3P 142957-86-6P IT

## 142957-87-7P 143024-70-8P

RL: IMF (Industrial manufacture); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

(manuf. of, as light-diffusing photocured claddings on plastic optical fibers)

RN 142957-80-0 CAPLUS

CN 2-Propenoic acid, 1,4-butanediyl ester, polymer with 2-ethyl-2-[[(1-oxo-2-propenyl)oxy]methyl]-1,3-propanediyl di-2-propenoate,

3,3,4,4,5,5,6,6,7,7,8,8,9,9,10,10,10-heptadecafluorodecyl 2-propenoate and exo-1,7,7-trimethylbicyclo[2.2.1]hept-2-yl 2-propenoate (9CI) (CA INDEX NAME)

CM 1

CRN 27905-45-9 CMF C13 H7 F17 O2

CM 2

CRN 15625-89-5 CMF C15 H20 O6

CM 3

CRN 5888-33-5 CMF C13 H20 O2

Relative stereochemistry.

•Page 146Lee507

CM 4

CRN 1070-70-8 CMF C10 H14 O4

RN 142957-83-3 CAPLUS

CN 2-Propenoic acid, 2-ethyl-2-[[(1-oxo-2-propenyl)oxy]methyl]-1,3-propanediyl ester, polymer with 3,3,4,4,5,5,6,6,7,7,8,8,9,9,10,10,10-heptadecafluorodecyl 2-propenoate and (octahydro-4,7-methano-1H-indene-5,?-diyl)bis(methylene) di-2-propenoate (9CI) (CA INDEX NAME)

CM 1

CRN 42594-17-2 CMF C18 H24 O4 CCI IDS

$$2 \begin{bmatrix}
0 \\
|| \\
D1-CH_2-O-C-CH-CH_2
\end{bmatrix}$$

CM 2

CRN 27905-45-9 CMF C13 H7 F17 O2 Page 147Lee507

$$\begin{array}{c} \text{O} \\ \parallel \\ \text{F}_3\text{C-- (CF}_2) \text{ }_7\text{-- CH}_2\text{-- CH}_2\text{-- O-- C-- CH} \end{array}$$

CM 3

CRN 15625-89-5 CMF C15 H20 O6

RN 142957-86-6 CAPLUS

CN 2-Propenoic acid, 2-ethyl-2-[[(1-oxo-2-propenyl)oxy]methyl]-1,3-propanediyl ester, polymer with 3,3,4,4,5,5,6,6,7,7,8,8,9,9,10,10,10-heptadecafluorodecyl 2-propenoate and exo-1,7,7-trimethylbicyclo[2.2.1]hept-2-yl 2-propenoate (9CI) (CA INDEX NAME)

CM 1

CRN 27905-45-9 CMF C13 H7 F17 O2

$$\begin{array}{c} \text{O} \\ \parallel \\ \text{F}_{3}\text{C---} (\text{CF}_{2})_{7} - \text{CH}_{2} - \text{CH}_{2} - \text{O---} \text{C---} \text{CH} = \text{CH}_{2} \end{array}$$

CM 2

CRN 15625-89-5 CMF C15 H20 O6 Page 148Lee507

CM 3

CRN 5888-33-5 CMF C13 H20 O2

Relative stereochemistry.

RN 142957-87-7 CAPLUS

2-Propenoic acid, 2-ethyl-2-[[(1-oxo-2-propenyl)oxy]methyl]-1,3-propanediyl ester, polymer with 1,4-butanediyl di-2-propenoate, 3,3,4,4,5,5,6,6,7,7,8,8,9,9,10,10,10-heptadecafluorodecyl 2-propenoate, 2-[[(heptadecafluorooctyl)sulfonyl]propylamino]ethyl 2-propenoate and (octahydro-4,7-methano-1H-indene-5,?-diyl)bis(methylene) di-2-propenoate (9CI) (CA INDEX NAME)

CM 1

CRN 42594-17-2 CMF C18 H24 O4 CCI IDS \*Page 149Lee507

CM 2

CRN 27905-45-9 CMF C13 H7 F17 O2

$$F_3C-(CF_2)_7-CH_2-CH_2-O-C-CH=CH_2$$

CM 3

CRN 15625-89-5 CMF C15 H20 O6

CM 4

CRN 2357-60-0

CMF C16 H14 F17 N O4 S

Page 150Lee507

CM 5

CRN 1070-70-8 CMF C10 H14 O4

RN 143024-70-8 CAPLUS

2-Propenoic acid, 2,2-dimethyl-1,3-propanediyl ester, polymer with butyl 2-propenoate, 3,3,4,4,5,5,6,6,7,7,8,8,9,9,10,10,10-heptadecafluorodecyl 2-propenoate, (1-methyl-1,2-ethanediyl)bis[oxy(methyl-2,1-ethanediyl)] di-2-propenoate, octahydro-4,7-methano-1H-inden-5-yl 2-propenoate and exo-1,7,7-trimethylbicyclo[2.2.1]hept-2-yl 2-propenoate, graft (9CI) (CA INDEX NAME)

CM 1

CRN 42978-66-5 CMF C15 H24 O6 CCI IDS

3 (D1-Me)

CM 2

CRN 27905-45-9 CMF C13 H7 F17 O2 Page 151Lee507

$$F_3C-(CF_2)_7-CH_2-CH_2-O-C-CH=CH_2$$

CM 3

CRN 7398-56-3 CMF C13 H18 O2

CM 4

CRN 5888-33-5 CMF C13 H20 O2

Relative stereochemistry.

CM 5

CRN 2223-82-7 CMF C11 H16 O4

\*Page 152Lee507

CM 6

CRN 141-32-2 CMF C7 H12 O2

$$\begin{array}{c} \text{O} \\ \parallel \\ \text{n-BuO-C-CH} \end{array}$$

IT 143409-33-0P

RL: PREP (Preparation)

(manuf. of, as photocured optical fiber cores with light-diffusing claddings)

RN 143409-33-0 CAPLUS

CN 2-Propenoic acid, 2,2-dimethyl-1,3-propanediyl ester, polymer with octahydro-4,7-methano-1H-inden-5-yl 2-propenoate and .alpha.-[octahydro[(1-oxo-2-propenyl)oxy]-4,7-methano-1H-indenyl]-.omega.-[(1-oxo-2-propenyl)oxy]poly[oxycarbonyl-1,2-phenylenecarbonyloxy(octahydro-4,7-methano-1H-indenediyl)] (9CI) (CA INDEX NAME)

CM 1

CRN 143178-25-0 CMF (C18 H18 O4)n C16 H20 O4 CCI IDS, PMS, MAN

\*\*\* STRUCTURE DIAGRAM IS NOT AVAILABLE \*\*\*

CM 2

CRN 7398-56-3 CMF C13 H18 O2

CM 3

CRN 2223-82-7 CMF C11 H16 O4

```
Me
IC
     ICM G02B006-00
     ICS C08L033-14; G02B006-12; G02B006-16
CC
     38-3 (Plastics Fabrication and Uses)
     Section cross-reference(s): 73
ST
     photocurable acrylic clad optical fiber; fluoropolymer photocurable
     optical fiber; epoxy resin photocurable optical fiber; polyester acrylic
     photocurable optical fiber
IT
     Optical fibers
        (acrylic-polyester, with photocured light-diffusing polymer claddings)
IT
     Epoxy resins, uses
     RL: USES (Uses)
        (plastic optical fiber claddings, photocurable, light-diffusing)
IT
     Polyesters, uses
     RL: USES (Uses)
        (acrylic, optical fiber cores, photocurable, with light-diffusing
        claddings)
IT
     Fluoropolymers
     RL: USES (Uses)
        (acrylic, plastic optical fiber claddings, photocurable,
        light-diffusing)
IT
     Fluoropolymers
     RL: USES (Uses)
        (epoxy, plastic optical fiber claddings, photocurable, light-diffusing)
IT
     Acrylic polymers, uses
     Epoxy resins, uses
     RL: USES (Uses)
        (fluorine-contg., plastic optical fiber claddings, photocurable,
        light-diffusing)
IT
     Acrylic polymers, uses
     RL: USES (Uses)
        (polyester-, optical fiber cores, photocurable, with light-diffusing
        claddings)
     Siloxanes and Silicones, uses
IT
     RL: USES (Uses)
```

(vinyl group-terminated, acrylic copolymers, plastic optical fiber

3-Methacryloyloxypropyltrimethoxysilane, silicone-contg. acrylic copolymer derivs. 4998-38-3DP, silicone-contg. acrylic copolymer derivs. 5888-33-5DP, Isobornyl acrylate, silicone-contg. acrylic copolymer derivs. 15625-89-5DP, Trimethylolpropane triacrylate, silicone-contg. acrylic

117725-57-2P, Methyl methacrylate-trimethylolpropane triacrylate graft

74049-08-4P

2530-85-0DP,

79637-74-4DP,

90571-08-7P

claddings, photocurable, light-diffusing)

79-10-7DP, Acrylic acid, silicones terminated by,

30603-97-5P

silicone-contg. acrylic copolymer derivs.

copolymer derivs.

IT

Page 154Lee507

copolymer 118256-09-0P 120111-54-8P 140127-75-9P 140127-76-0P 140127-77-1P 142957-74-2P 142957-75-3P 142957-76-4P 142957-77-5P 142957-78-6P 142957-79-7P 142957-80-0P 142957-82-2P 142957-83-3P 142957-84-4P 142957-85-5P 142957-86-6P 142957-87-7P 142957-88-8P 142957-89-9P 142987-91-5P 142987-92-6P 142987-97-1P 142987-98-2P 142987-99-3P 142988-00-9P 142988-01-0P 142988-03-2P 143024-70-8P 143434-11-1P RL: IMF (Industrial manufacture); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses) (manuf. of, as light-diffusing photocured claddings on plastic optical fibers)

IT 143409-33-0P

RL: PREP (Preparation)

(manuf. of, as photocured optical fiber cores with light-diffusing claddings)

L12 ANSWER 32 OF 34 CAPLUS COPYRIGHT 2003 ACS on STN

ACCESSION NUMBER: 1990:236501 CAPLUS

DOCUMENT NUMBER: 112:236501

TITLE: Curable polyene-polythiol resin compositions

INVENTOR(S): Takiyama, Eiichiro; Ogura, Tateshi; Harigai, Noriaki

PATENT ASSIGNEE(S): Showa Highpolymer Co., Ltd., Japan

SOURCE: Jpn. Kokai Tokkyo Koho, 10 pp.

CODEN: JKXXAF

DOCUMENT TYPE: Patent LANGUAGE: Japanese

FAMILY ACC. NUM. COUNT: 1

PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
JP 01306424	A2	19891211	JP 1988-136554	19880602
JP 06045697	B4	19940615		
EP 429701	A1	19910605	EP 1989-121983	19891129
	~~			

R: DE, FR, GB

PRIORITY APPLN. INFO.: JP 1988-136554 19880602

The odorless title compns. with good heat resistance, useful for coatings and adhesives, comprise (a) polymers or oligomers (mol. wt. .gtoreq.1000) selected from compds. contg. .gtoreq.2 C:C bonds or .gtoreq.1 C.tplbond.C bond and (b) compds. prepd. by the reaction of alicyclic compds. having .gtoreq.2 unsatd. bond (.gtoreq.1 of which in the ring) and compds. having .gtoreq.2 SH, under SH excess condition. Thus, 132 g dicyclopentadiene was added dropwise to a mixt. of 490 g pentaerythritol tetramercaptopropionate and 0.2 g methyl-p-benzoquinone at .ltoreq.60.degree. and stirred 2 h at 80.degree. to give an odorless adduct (I). Sep., 200 g phenoxy resin (mol. wt. 25,000) was treated with 30 g isocyanatoethyl methacrylate in MEK to give an unsatd. polymer (II). A Cu foil was coated with a mixt. of I 50, II 450, and Darocure 1173 2 parts and irradiated by UV to form a coating with pencil hardness H, crosscut adhesion 100/100, and good solder heat resistance at 260.degree.

IT 127455-59-8P

RL: PREP (Preparation)

Page 155Lee507

(prepn. of, odorless, heat-resistant, for coatings and adhesives)
RN 127455-59-8 CAPLUS
CN 2-Propenoic acid, 2-methyl-, 1,2-ethanediyl ester, polymer with

2-Propenoic acid, 2-methyl-, 1,2-ethanediyl ester, polymer with 2,2-bis[(3-mercapto-1-oxopropoxy)methyl]-1,3-propanediyl bis(3-mercaptopropanoate), 1,2-ethanediol, 1,3-isobenzofurandione, oxiranylmethyl 2-methyl-2-propenoate and 3a,4,7,7a-tetrahydro-4,7-methano-1H-indene (9CI) (CA INDEX NAME)

CM 1

CRN 7575-23-7 CMF C17 H28 O8 S4

CM 2

CRN 107-21-1 CMF C2 H6 O2

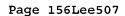
$$^{\rm HO-CH_2-CH_2-OH}$$

CM 3

CRN 106-91-2 CMF C7 H10 O3

CM 4

CRN 97-90-5 CMF C10 H14 O4



CM 5

CRN 85-44-9 CMF C8 H4 O3

CM 6

CRN 77-73-6 CMF C10 H12



IC ICM C08G075-00

CC 37-6 (Plastics Manufacture and Processing) Section cross-reference(s): 38, 42, 76

ST polyene polythiol copolymer curable odorless; coating polyene polythiol copolymer adhesion; adhesive polyene polythiol copolymer; photocurable polyene polythiol copolymer

IT Resists

(curable polyene-polythiol copolymers for, heat-resistant)

IT Adhesives

Coating materials

(curable, heat-resistant, polyene-polythiol copolymers for, odorless)

IT Epoxy resins, uses and miscellaneous

RL: USES (Uses)

(phenoxy, unsatd., solder resist inks contg., photocurable, odorless, heat-resistant)

IT Thiols, polymers

RL: USES (Uses)

(poly-, with polyenes, UV-curable, odorless, heat-resistant, for coatings and adhesives)

Page 157Lee507

IT Electric circuits

(printed, boards, resist inks for manuf. of, contg. curable polyene-polythiol copolymers, heat-resistant)

30674-80-7DP, Isocyanatoethyl methacrylate, reaction products with phenoxy resins, polymers with polyene-polythiols 121602-09-3DP, reaction products with phenoxy resin acrylates 127455-55-4P 127455-58-7P 127455-59-8P

RL: PREP (Preparation)

(prepn. of, odorless, heat-resistant, for coatings and adhesives)
IT 107-19-7D, Propargyl alcohol, isophorone diisocyanate adducts, reaction
products with phenoxy resins 4098-71-9D, Isophorone diisocyanate,
propargyl alc. adducts, reaction products with phenoxy resins
127455-57-6

RL: USES (Uses)

(solder resist inks contg., photocurable, odorless, heat-resistant)

L12 ANSWER 33 OF 34 CAPLUS COPYRIGHT 2003 ACS on STN

ACCESSION NUMBER: 1988:591433 CAPLUS

DOCUMENT NUMBER: 109:191433

TITLE: Polymerizable (meth)allylnorbornene

dicarboximide-(meth)acrylate ester compositions

APPLICATION NO. DATE

INVENTOR(S): Banks, Christopher Paul; Irving, Edward; Renner,

Alfred; Smith, Terence James

PATENT ASSIGNEE(S): Ciba-Geigy A.-G., Switz.

SOURCE: Eur. Pat. Appl., 15 pp.

KIND DATE

CODEN: EPXXDW

DOCUMENT TYPE: Patent LANGUAGE: German

FAMILY ACC. NUM. COUNT: 1

PATENT INFORMATION:

PATENT NO.

	EP 269568	A2 19880601	EP 1987-810663	19871116				
	EP 269568	A3 19890705						
	EP 269568	B1 19910515						
	R: CH, DE,	FR, GB, IT, LI,	NL, SE					
	US 4966923	A 19901030		19871113				
	JP 63150311	A2 19880623	JP 1987-293857	19871120				
]	PRIORITY APPLN. INFO.	. :	GB 1986-28003	19861122				
AB Mixts. of (meth)acrylate esters and (meth)allyl-5-norbornene-2,3-								
dicarboximide derivs. can be photopolymd. to polymers useful in								
fiber-reinforced composites and imaging, which can be thermally cured. A								
mixt. of N,N'-hexamethylenebis(allyl-5-norbornene-2,3-dicarboximide) 35,								
N,-diallyl-5-norbornene-2,3-dicarboximide 5, tetramethylene methacrylate								
8, allyl methacrylate 2, PhCOC(OMe) 2Ph 1, and allyl-N-(benzenesulfonyloxy)-								
	5-norbornene-2,3-dicarboximide 0.2 part was exposed as a 20mu.m film to							
an 80-W/cm Hg lamp at a distance of 20 cm for 30 s and then heated at								
	250 degree for	2 h to give a ha	ard film with glass tem	np. 285-290.degree				
		7181-85-8P 117181		_				
		7181-90-5P 117181						

CN

### Page 158Lee507

# 117181-92-7P 117181-93-8P 117248-17-6P

RL: PREP (Preparation)

(manuf. of, by photochem. polymn.)

RN 117181-84-7 CAPLUS

2-Propenoic acid, 2-methyl-, 2-ethyl-2-[[(2-methyl-1-oxo-2-propenyl)oxy]methyl]-1,3-propanediyl ester, polymer with 2,2'-(1,6-hexanediyl)bis[3a,4,7,7a-tetrahydro(2-propenyl)-4,7-methano-1H-isoindole-1,3(2H)-dione], 2-propenyl 2-methyl-2-propenoate and 3a,4,7,7a-tetrahydro-2,?-di-2-propenyl-4,7-methano-1H-isoindole-1,3(2H)-dione (9CI) (CA INDEX NAME)

CM 1

CRN 91865-52-0 CMF C30 H36 N2 O4 CCI IDS

CM 2

CRN 91865-47-3 CMF C15 H17 N O2 CCI IDS

$$CH_2-CH$$

$$D1-CH_2-CH=CH_2$$

CM 3

•

CM 4

CRN 96-05-9 CMF C7 H10 O2

RN 117181-85-8 CAPLUS

CN 2-Propenoic acid, 2-methyl-, 2-ethyl-2-[[(2-methyl-1-oxo-2-propenyl)oxy]methyl]-1,3-propanediyl ester, polymer with.

2,2'-(1,6-hexanediyl)bis[3a,4,7,7a-tetrahydro(2-propenyl)-4,7-methano-1H-isoindole-1,3(2H)-dione], 2,2'-(methylenedi-4,1-phenylene)bis[3a,4,7,7a-tetrahydro(2-propenyl)-4,7-methano-1H-isoindole-1,3(2H)-dione] and

3a,4,7,7a-tetrahydro-2,?-di-2-propenyl-4,7-methano-1H-isoindole-1,3(2H)-dione (9CI) (CA INDEX NAME)

CM 1

CRN 91865-54-2 CMF C37 H34 N2 O4 CCI IDS

$$2 \left[ D1 - CH_2 - CH = CH_2 \right]$$

CM 2

CRN 91865-52-0 CMF C30 H36 N2 O4

CCI IDS

$$2 \left[ D1-CH_2-CH=-CH_2 \right]$$

CM 3

CRN 91865-47-3

CMF C15 H17 N O2

CCI IDS

$$CH_2-CH$$
  $CH_2$ 

$$D1-CH_2-CH=CH_2$$

CM 4

CRN 3290-92-4 CMF C18 H26 O6 Page 161Lee507

•

RN 117181-87-0 CAPLUS

CN 2-Propenoic acid, 2-[[3-hydroxy-2,2-bis[[(1-oxo-2-propenyl)oxy]methyl]propoxy]methyl]-2-[[(1-oxo-2-propenyl)oxy]methyl]-1,3-propanediyl ester, polymer with 2,2'-(methylenedi-4,1-phenylene)bis[3a,4,7,7a-tetrahydro(2-propenyl)-4,7-methano-1H-isoindole-1,3(2H)-dione] (9CI) (CA INDEX NAME)

CM 1

CRN 91865-54-2 CMF C37 H34 N2 O4 CCI IDS

CM 2

CRN 60506-81-2 CMF C25 H32 O12

À

RN 117181-88-1 CAPLUS

CN 2-Propenoic acid, 2-methyl-, 1,4-butanediyl ester, polymer with 2,2'-(methylenedi-4,1-phenylene)bis[3a,4,7,7a-tetrahydro(2-propenyl)-4,7-methano-1H-isoindole-1,3(2H)-dione] (9CI) (CA INDEX NAME)

CM 1

CRN 91865-54-2 . CMF C37 H34 N2 O4 CCI IDS

CM 2

CRN 2082-81-7 CMF C12 H18 O4

RN 117181-90-5 CAPLUS

CN 2-Propenoic acid, 1,4-butanediyl ester, polymer with 2,2'-(methylenedi-4,1-phenylene)bis[3a,4,7,7a-tetrahydro(2-propenyl)-4,7-methano-1H-isoindole-1,3(2H)-dione] (9CI) (CA INDEX NAME)

CM 1

CRN 91865-54-2 CMF C37 H34 N2 O4 CCI IDS Page 163Lee507

i.

$$2 \left[ D1-CH_2-CH=CH_2 \right]$$

CM 2

CRN 1070-70-8 CMF C10 H14 O4

RN 117181-91-6 CAPLUS

CN 2-Propenoic acid, 2,2-dimethyl-1,3-propanediyl ester, polymer with 2,2'-(methylenedi-4,1-phenylene)bis[3a,4,7,7a-tetrahydro(2-propenyl)-4,7-methano-1H-isoindole-1,3(2H)-dione] (9CI) (CA INDEX NAME)

CM 1

CRN 91865-54-2 CMF C37 H34 N2 O4 CCI IDS

$$2 \left[ D1-CH_2-CH=CH_2 \right]$$

CM 2

Page 164Lee507

F

CRN 2223-82-7 CMF C11 H16 O4

RN 117181-92-7 CAPLUS

CN 2-Propenoic acid, 1,6-hexanediyl ester, polymer with 2,2'-(methylenedi-4,1-phenylene)bis[3a,4,7,7a-tetrahydro(2-propenyl)-4,7-methano-1H-isoindole-1,3(2H)-dione] (9CI) (CA INDEX NAME)

CM 1

CRN 91865-54-2 CMF C37 H34 N2 O4 CCI IDS

CM 2

CRN 13048-33-4 CMF C12 H18 O4

RN 117181-93-8 CAPLUS

CN 2-Propenoic acid, 2-methyl-, 1,6-hexanediyl ester, polymer with 2,2'-(methylenedi-4,1-phenylene)bis[3a,4,7,7a-tetrahydro(2-propenyl)-4,7-methano-1H-isoindole-1,3(2H)-dione] (9CI) (CA INDEX NAME)

## Page 165Lee507

CM 1

CRN 91865-54-2 CMF C37 H34 N2 O4 CCI IDS

CM 2

CRN 6606-59-3 CMF C14 H22 O4

RN 117248-17-6 CAPLUS

CN 2-Propenoic acid, 2,2-bis[[(1-oxo-2-propenyl)oxy]methyl]-1,3-propanediyl ester, polymer with 2,2'-(methylenedi-4,1-phenylene)bis[3a,4,7,7a-tetrahydro(2-propenyl)-4,7-methano-1H-isoindole-1,3(2H)-dione] (9CI) (CA INDEX NAME)

CM 1

CRN 91865-54-2 CMF C37 H34 N2 O4 CCI IDS Page 166Lee507

÷

CM 2

CRN 4986-89-4 CMF C17 H20 O8

IC ICM C08F226-06

ICS C08F222-40; C08J005-24

CC 37-3 (Plastics Manufacture and Processing)
 Section cross-reference(s): 27, 74

allylnorbornenedicarboximide deriv polymer; norbornenedicarboximide allyl deriv polymer; allyl methacrylate copolymer photopolymn; polymn photochem allylimide methacrylate; catalyst polymn photochem cationic

IT Carbon fibers, uses and miscellaneous

RL: USES (Uses)

(allylnorbornenedicarboximide deriv. copolymers reinforced by, manuf. of)

IT Resists

(photo-, allylnorbornenedicarboximide deriv. copolymers, manuf. of)

IT Polymerization catalysts

(photochem., allyl[(benzenesulfonyl)oxy]norbornenedicarboximide, for allylnorbornenedicarboximide derivs. with (meth)acrylate esters)

IT Polymerization

(photochem., of allylnorbornenedicarboximide derivs. with (meth)acrylate esters)

IT 7440-44-0P

RL: PREP (Preparation)

(carbon fibers, allylnorbornenedicarboximide deriv. copolymers

Page 167Lee507

2

reinforced by, manuf. of) IT 101483-20-9 RL: CAT (Catalyst use); USES (Uses) (catalysts, for photochem. polymn. of allylnorbornene dicarboximide derivs. with (meth)acrylate esters) TΤ 117181-84-7P 117181-85-8P 117181-86-9P 117181-87-0P 117181-88-1P 117181-89-2P 117181-90-5P 117181-91-6P 117181-92-7P 117181-93-8P 117181-94-9P 117181-95-0P 117181-96-1P 117181-97-2P 117182-91-9P 117248-17-6P RL: PREP (Preparation) (manuf. of, by photochem. polymn.) IT 101483-19-6P RL: PREP (Preparation) (prepn. of) 5470-11-1, Hydroxylaminehydrochloride IT RL: RCT (Reactant); RACT (Reactant or reagent) (reaction of, with allylnorbornene dicarboxylic anhydride) IT 50984-57-1 RL: RCT (Reactant); RACT (Reactant or reagent) (reaction of, with hydroxylamine) L12 ANSWER 34 OF 34 CAPLUS COPYRIGHT 2003 ACS on STN 1987:68851 CAPLUS ACCESSION NUMBER: DOCUMENT NUMBER: 106:68851 TITLE: Photocurable flexible inks INVENTOR(S): Nagahara, Shigenori; Abe, Shunzo; Miyake, Hideo PATENT ASSIGNEE(S): Toyobo Co., Ltd., Japan SOURCE: Jpn. Kokai Tokkyo Koho, 9 pp. CODEN: JKXXAF DOCUMENT TYPE: Patent LANGUAGE: Japanese FAMILY ACC. NUM. COUNT: 1 PATENT INFORMATION: PATENT NO. KIND DATE APPLICATION NO. DATE -----JP 1985-42471 JP 61203108 A2 19860909 19850304 PRIORITY APPLN. INFO.: JP 1985-42471 19850304 A photocurable solder-resistant ink, useful in manuf. of a flexible printed circuit board, comprises a photocurable prepolymer, a bornyl acrylate deriv.-based photocurable compd., and a photoinitiator. Thus, a flexible polyimide-Cu foil laminate was printed with an ink compn. comprising Ripoxy SP 5003 (bisphenol A-type epoxy acrylate) 29.9, isobornyl methacrylate (I) 20.0, 2-hydroxyethyl methacrylate 7.5, trimethylolpropane triacrylate 7.5, triallyl isocyanurate 10.0, 2-ethylanthraquinone 1.0, talc 20.0, powd. silica 0.1, phthalocyanine green 1.0, a silicone defoamer 1.0, and a leveling agent 2.0 parts and UV-cured to form a resist layer exhibiting crosscut adhesion

test 100/100, max. no. of flexion before crack formation (diam. 4 mm) 100, solder resistance (at 260.degree.) .gtoreq.60 s, and resistance 2 .times. 1014 .OMEGA.. An ink not contg. I gave a layer withstanding solder test

### Page 168Lee507

.ltoreq.10 s.

IT 106671-00-5 106671-01-6 106671-02-7

106679-65-6 106686-47-9

RL: USES (Uses)

(inks, photocurable, flexible, solder-resistant, in manuf. of printed circuit boards)

RN 106671-00-5 CAPLUS

CN 2-Propenoic acid, 2-methyl-, 2-hydroxyethyl ester, polymer with

2-ethyl-2-[[(1-oxo-2-propenyl)oxy]methyl]-1,3-propanediyl di-2-propenoate,

2-hydroxyethyl 2-propenoate, 5-isocyanato-1-(isocyanatomethyl)-1,3,3-

trimethylcyclohexane, exo-1,7,7-trimethylbicyclo[2.2.1]hept-2-yl

2-methyl-2-propenoate and 1,3,5-tri-2-propenyl-1,3,5-triazine-

2,4,6(1H,3H,5H)-trione (9CI) (CA INDEX NAME)

CM 1

CRN 15625-89-5

CMF C15 H20 O6

CM 2

CRN 7534-94-3 CMF C14 H22 O2

Relative stereochemistry.

CM 3

CRN 4098-71-9

CMF C12 H18 N2 O2

Page 169Lee507

CM 4

CRN 1025-15-6 CMF C12 H15 N3 O3

$$H_2C = CH - CH_2$$
 $CH_2 - CH = CH_2$ 
 $H_2C = CH - CH_2$ 

CM 5

CRN 868-77-9 CMF C6 H10 O3

$$^{\rm H_2C}$$
 O  $^{\rm H_2}$   $^{\rm H_$ 

CM 6

CRN 818-61-1 CMF C5 H8 O3

$$\begin{array}{c} \text{O} \\ \parallel \\ \text{HO-CH$_2$-CH$_2$-O-C-CH$== CH$_2} \end{array}$$

RN 106671-01-6 CAPLUS

CN 2-Propenoic acid, 2-methyl-, 2-hydroxyethyl ester, polymer with

#### Page 170Lee507

CM 1

CRN 90780-31-7 CMF C21 H32 O8

CM 2

CRN 15625-89-5 CMF C15 H20 O6

CM 3

CRN 7534-94-3 CMF C14 H22 O2

Relative stereochemistry.

Page 171Lee507

CM 4

CRN 4098-71-9 CMF C12 H18 N2 O2

CM 5

CRN 868-77-9 CMF C6 H10 O3

CM 6

CRN 818-61-1 CMF C5 H8 O3

$$\begin{array}{c} & \text{O} \\ || \\ \text{HO-} \ \text{CH}_2 - \ \text{CH}_2 - \ \text{O-} \ \text{C-} \ \text{CH} \\ \end{array}$$

CM 7

Page 172Lee507

CRN 53814-24-7 CMF (C15 H16 O2 . C3 H5 Cl O)x . 2 C3 H4 O2

CM 8

CRN 79-10-7 CMF C3 H4 O2

CM 9

CRN 25068-38-6

CMF (C15 H16 O2 . C3 H5 Cl O) x

CCI PMS

CM 10

CRN 106-89-8 CMF C3 H5 Cl O

CM 11

CRN 80-05-7 CMF C15 H16 O2

RN 106671-02-7 CAPLUS

CN 2-Propenoic acid, 2-methyl-, 2-hydroxyethyl ester, polymer with 2-ethyl-2-[[(1-oxo-2-propenyl)oxy]methyl]-1,3-propanediyl di-2-propenoate, 2-hydroxyethyl 2-propenoate, 5-isocyanato-1-(isocyanatomethyl)-1,3,3-trimethylcyclohexane, (1-methylethylidene)bis[(2,6-dibromo-4,1-phenylene)oxy(2-hydroxy-3,1-propanediyl)] di-2-propenoate,

Page 173Lee507

exo-1,7,7-trimethylbicyclo[2.2.1]hept-2-yl 2-methyl-2-propenoate and 1,3,5-tri-2-propenyl-1,3,5-triazine-2,4,6(1H,3H,5H)-trione (9CI) (CAINDEX NAME)

CM 1

CRN 66696-45-5 CMF C27 H28 Br4 O8

PAGE 1-A

PAGE 1-B

CM 2

CRN 15625-89-5 CMF C15 H20 O6

CM 3

CRN 7534-94-3 CMF C14 H22 O2

Relative stereochemistry.

7

CM 4

CRN 4098-71-9 CMF C12 H18 N2 O2

CM 5

CRN 1025-15-6 CMF C12 H15 N3 O3

$$H_2C = CH - CH_2$$
 $CH_2 - CH = CH_2$ 
 $CH_2 - CH = CH_2$ 
 $CH_2 - CH = CH_2$ 

CM 6

CRN 868-77-9 CMF C6 H10 O3 Page 175Lee507

CM 7

CRN 818-61-1 CMF C5 H8 O3

RN 106679-65-6 CAPLUS

CN 2-Propenoic acid, 2-methyl-, 2-hydroxyethyl ester, polymer with (chloromethyl)oxirane polymer with 4,4'-(1-methylethylidene)bis[phenol] di-2-propenoate, 2-ethyl-2-[[(1-oxo-2-propenyl)oxy]methyl]-1,3-propanediyl di-2-propenoate, exo-1,7,7-trimethylbicyclo[2.2.1]hept-2-yl 2-methyl-2-propenoate and 1,3,5-tri-2-propenyl-1,3,5-triazine-2,4,6(1H,3H,5H)-trione (9CI) (CA INDEX NAME)

CM 1

CRN 15625-89-5 CMF C15 H20 O6

CM 2

CRN 7534-94-3 CMF C14 H22 O2

Relative stereochemistry.

Page 176Lee507

CM 3

CRN 1025-15-6 CMF C12 H15 N3 O3

CM 4

CRN 868-77-9 CMF C6 H10 O3

CM 5

CRN 53814-24-7

CMF (C15 H16 O2 . C3 H5 Cl O) x . 2 C3 H4 O2

CM 6

CRN 79-10-7 CMF C3 H4 O2 Page 177Lee507

CM 7

CRN 25068-38-6 CMF (C15 H16 O2 . C3 H5 Cl O)x CCI PMS

CM 8

CRN 106-89-8 CMF C3 H5 Cl O

CM 9

CRN 80-05-7 CMF C15 H16 O2

RN 106686-47-9 CAPLUS

CN 2-Propenoic acid, 2-methyl-, 2-hydroxyethyl ester, polymer with (chloromethyl)oxirane polymer with 4,4'-(1-methylethylidene)bis[phenol] di-2-propenoate, 2-ethyl-2-[[(1-oxo-2-propenyl)oxy]methyl]-1,3-propanediyl di-2-propenoate, 2-hydroxyethyl 2-propenoate, 5-isocyanato-1-(isocyanatomethyl)-1,3,3-trimethylcyclohexane, exo-1,7,7-trimethylbicyclo[2.2.1]hept-2-yl 2-methyl-2-propenoate and 1,3,5-tri-2-propenyl-1,3,5-triazine-2,4,6(1H,3H,5H)-trione (9CI) (CA INDEX NAME)

CM 1

CRN 15625-89-5 CMF C15 H20 O6 Page 178Lee507

CM 2

CRN 7534-94-3 CMF C14 H22 O2

Relative stereochemistry.

CM 3

CRN 4098-71-9 CMF C12 H18 N2 O2

CM 4

CRN 1025-15-6 CMF C12 H15 N3 O3 Page 179Lee507

CM 5

CRN 868-77-9 CMF C6 H10 O3

CM 6

CRN 818-61-1 CMF C5 H8 O3

CM 7

CRN 53814-24-7 CMF (C15 H16 O2 . C3 H5 Cl O)  $\times$  . 2 C3 H4 O2

CM 8

CRN 79-10-7 CMF C3 H4 O2

CM 9

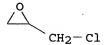
CRN 25068-38-6

CMF (C15 H16 O2 . C3 H5 Cl O)x

CCI PMS

CM 10

CRN 106-89-8 CMF C3 H5 Cl O



CM 11

CRN 80-05-7 CMF C15 H16 O2

IC ICM C08F220-10

ICS C08F002-48; C08F220-18; C09D011-10; H05K003-28

CC 42-10 (Coatings, Inks, and Related Products)
 Section cross-reference(s): 76

ST epoxy acrylate photocurable ink; isobornyl methacrylate photocurable ink; hydroxyethyl methacrylate photocurable ink; methylolpropane triacrylate photocurable ink; allyl isocyanurate photocurable ink; copper flexible printed circuit board; polyimide flexible printed circuit board; solder resistant photocurable ink

IT Polyimides, uses and miscellaneous

RL: USES (Uses)

(films, copper foil laminates, solder-resistant inks for, in manuf. of flexible printed circuit boards)

IT Soldering

(resistance to, of inks contg. epoxy or urethane acrylate and isobornyl acrylate, UV-curable)

IT Inks

(photocurable, epoxy or methane acrylates contg. isobornyl acrylate, flexible, solder-resistant)

IT Electric circuits

## Page 181Lee507

(printed, flexible, inks for, epoxy or urethane acrylates contg. isobornyl acrylate as, solder-resistant)

IT 7440-50-8, Copper, uses and miscellaneous

RL: USES (Uses)

(foil, polyimide film laminates, solder-resistant inks for, in manuf. of flexible printed circuit boards)

IT 106671-00-5 106671-01-6 106671-02-7

106679-65-6 106686-47-9

RL: USES (Uses)

(inks, photocurable, flexible, solder-resistant, in manuf. of printed circuit boards)